
SEMICONDUCTOR GENERAL CATALOG

半導体製品総覧表2018年7月版

MOSFETs / Junction FETs

MOSFET / 接合形FET

Low Voltage MOSFETs / 低耐压MOSFET

Mid-High Voltage MOSFETs / 中高耐压MOSFET

Automotive MOSFETs / 車載MOSFET

Junction FETs / 接合形FET

SiC MOSFETs / SiC MOSFET

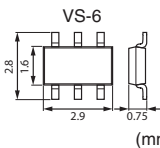
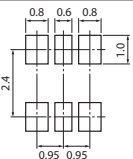
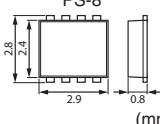
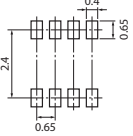
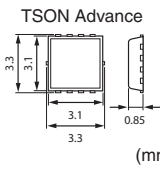
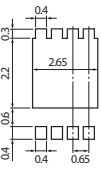
Radio-Frequency MOSFETs / 高周波MOSFET

Low Voltage MOSFETs / 低耐圧MOSFET

High-Speed Switching Series / 高速スイッチングシリーズ

(Single N-Channel) / (シングルNチャンネル)

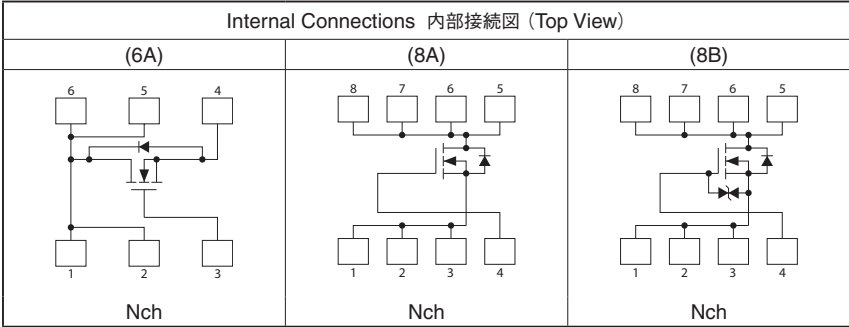
(1/5)

Package	Part Number	Absolute Maximum Ratings				R _{DS(ON)} max (mΩ)		Ciss typ. (pF)	Crss typ. (pF)	Coss typ. (pF)	Qg typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)	V _{GS} = 10 V	V _{GS} = 4.5 V							
 (mm)	TPC6008-H	30	±20	5.9	2.2 (2)	60	74	232	16	68	4.8	U-MOSVI-H	(6A)	
	TPC6009-H	40	±20	5.3	2.2 (2)	81	98	225	13	54	4.7	U-MOSVI-H		
	TPC6010-H	60	±20	6.1	2.2 (2)	59	63	640	24	95	12	U-MOSVI-H		
 (mm)	TPCP8007-H	60	±20	5	1.68 (2)	57	64	640	25	90	11	U-MOSVI-H	(8A)	
 (mm)	TPCC8067-H	30	±20	9	15	25	33	690	28	120	9.5	U-MOSVII-H	(8A)	
	TPCC8066-H		±20	11	17	15	19	1100	49	190	15	U-MOSVII-H		
	TPCC8065-H		±20	13	18	11.4	14.5	1350	63	240	20	U-MOSVII-H		
	TPCC8068-H		±20	13	17	11.6	16	980	57	210	14	U-MOSVII-H		
	TPCC8064-H		±20	19	30	8.2	10.6	1600	78	290	23	U-MOSVII-H		
	TPCC8062-H		±20	27	39	5.6	7.1	2400	120	430	34	U-MOSVII-H		
	TPN11003NL		±20	31 (1)	19	11	16	510	18	300	7.5	U-MOSVIII-H		
	TPN8R903NL		±20	37 (1)	22	8.9	12.7	630	21	350	9.8	U-MOSVIII-H		
	TPN6R003NL		±20	56 (1)	32	6	8.3	1050	37	600	17	U-MOSVIII-H		
	TPN4R303NL		±20	63 (1)	34	4.3	6.3	1110	39	640	14.8	U-MOSVIII-H		
	TPN5R203PL		±20	76 (1)	61	5.2	6.4	1520	55	515	22	U-MOSIX-H		
	TPN2R703NL		±20	90 (1)	42	2.7	4.1	1600	53	890	21	U-MOSVIII-H		
	TPN2R903PL		±20	122 (1)	75	2.9	4.1	1780	60	620	26	U-MOSIX-H		
	TPN1R603PL		±20	188 (1)	104	1.6	2.5	2970	110	850	41	U-MOSIX-H		
	TPN7R504PL	40	±20	68 (1)	61	7.5	10	1570	35	380	24	U-MOSIX-H		
	TPN3R704PL		±20	92 (1)	86	3.7	6	1910	41	470	27	U-MOSIX-H		
	TPN2R304PL		±20	100 (1)	104	2.3	4	2750	66	650	41	U-MOSIX-H		
	TPN2R805PL	45	±20	139 (1)	104	2.8	5	2450	56	610	39	U-MOSIX-H		
	TPN22006NH	60	±20	21 (1)	18	22	—	710	14	235	12	U-MOSVIII-H		
	TPN14006NH		±20	33 (1)	30	14	—	1000	25	310	15	U-MOSVIII-H		
	TPN11006NL		±20	37 (1)	30	11.4	17	1500	23	350	23	U-MOSVIII-H		
	TPN7R506NH		±20	53 (1)	42	7.5	—	1410	28	480	22	U-MOSVIII-H		
	TPN11006PL		±20	54 (1)	61	11.4	18.1	1250	25	225	17	U-MOSIX-H		
	TPN7R006PL		±20	76 (1)	75	7	13.5	1440	35	300	20	U-MOSIX-H		
	TPN4R806PL	80	±20	105 (1)	104	4.8	9.1	2130	45	360	29	U-MOSIX-H		
	TPN30008NH		±20	22 (1)	27	30	—	710	10	170	11	U-MOSVIII-H		
	TPN13008NH		±20	40 (1)	42	13.3	—	1230	20	290	18	U-MOSVIII-H		
	TPN3300ANH		±20	21 (1)	27	33	—	680	8.8	130	11	U-MOSVIII-H		
	TPN1600ANH	100	±20	36 (1)	42	16	—	1230	18	220	19	U-MOSVIII-H		
	TPN1200APL *		±20	66 (1)	104	11.5	20	1425	15	205	24	U-MOSIX-H	(8B)	
	TPN5900CNH	150	±20	18 (1)	39	59	—	460	3	80	7	U-MOSVIII-H	(8A)	
	TPN1110ENH	200	±20	13 (1)	39	114	—	460	3	55	7	U-MOSVIII-H		
	TPN2010FNH	250	±20	9.9 (1)	39	198	—	460	3	45	7	U-MOSVIII-H		

Note (1): I_D (DC) (Silicon Limit)

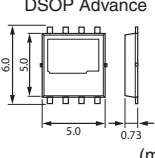
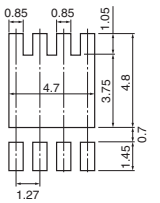
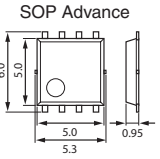
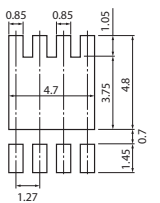
(2): Device mounted on a glass board. t = 5 seconds. / ガラスエポキシ基板。t = 5 秒。

*: New Product / 新製品



・ The internal connection diagrams only show the general configurations of the circuits.

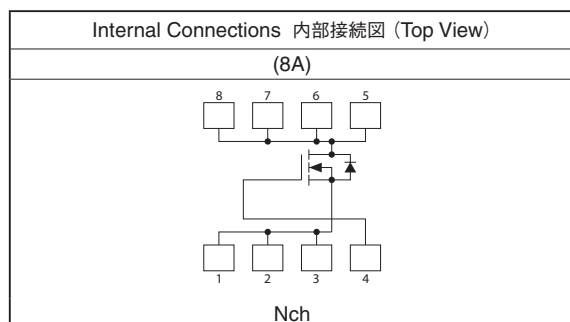
・ 内部接続図はイメージ図です。

Package	Part Number	Absolute Maximum Ratings				R _{DS(ON)} max (mΩ)		Ciss typ. (pF)	Crss typ. (pF)	Coss typ. (pF)	Qg typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)	V _{GSl} = 10 V	V _{GSl} = 4.5 V							
 (mm)	TPWR8503NL	30	±20	300 ⁽¹⁾	142	0.85	1.3	5300	130	2700	74	U-MOSVIII-H	(8A)	
	TPWR6003PL		±20	412 ⁽¹⁾	170	0.6	0.84	7700	220	2720	110	U-MOSIX-H		
	TPWR8004PL	40	±20	340 ⁽¹⁾	170	0.8	1.35	7370	58	1930	103	U-MOSIX-H		
	TPW1R005PL	45	±20	300 ⁽¹⁾	170	0.99	1.65	7700	76	1860	122	U-MOSIX-H		
	TPW1R306PL	60	±20	260 ⁽¹⁾	170	1.29	2.3	6250	80	1160	91	U-MOSIX-H		
	TPW2R508NH	75	±20	170 ⁽¹⁾	142	2.5	—	4600	50	1100	72	U-MOSVIII-H		
	TPW4R008NH	80	±20	116	142	4	—	4100	32	890	59	U-MOSVIII-H		
	TPW4R50ANH	100	±20	92	142	4.5	—	4000	31	700	58	U-MOSVIII-H		
	TPW3R70APL *		±20	150 ⁽¹⁾	170	3.7	6.2	4850	29	640	67	U-MOSIX-H		
	TPW1500CNH	150	±20	50 ⁽¹⁾	142	15.4	—	1700	7	280	22	U-MOSVIII-H		
	TPW2900ENH	200	±20	36 ⁽¹⁾	142	29	—	1700	7	180	22	U-MOSVIII-H		
	TPW5200FNH	250	±20	27 ⁽¹⁾	142	52	—	1700	7	140	22	U-MOSVIII-H		
 (mm)	TPCA8068-H	30	±20	15	21	11.6	16	980	57	210	14	U-MOSVII-H	(8A)	
	TPCA8065-H		±20	16	25	11.4	14.5	1350	63	240	20	U-MOSVII-H		
	TPCA8064-H		±20	20	32	8.2	10.6	1600	78	290	23	U-MOSVII-H		
	TPCA8063-H		±20	22	35	6.8	8.7	1900	93	340	27	U-MOSVII-H		
	TPCA8062-H		±20	28	42	5.6	7.1	2400	120	430	34	U-MOSVII-H		
	TPCA8059-H		±20	32	45	3.8	4.8	2900	150	530	41	U-MOSVII-H		
	TPH11003NL		±20	32 ⁽¹⁾	21	11	16	510	18	300	7.5	U-MOSVIII-H		
	TPCA8091-H		±20	35	25	6	8.4	1410	110	280	20	U-MOSVII-H		
	TPCA8058-H		±20	38	52	3	3.8	3600	200	680	51	U-MOSVII-H		
	TPH8R903NL		±20	38 ⁽¹⁾	24	8.9	12.7	630	21	350	9.8	U-MOSVIII-H		
	TPCA8057-H		±20	42	57	2.6	3.2	4300	240	810	61	U-MOSVII-H		
	TPCA8056-H		±20	48	63	2.2	2.7	5200	290	1000	74	U-MOSVII-H		
	TPCA8055-H		±20	56	70	1.9	2.3	6400	360	1200	91	U-MOSVII-H		
	TPH6R003NL		±20	57 ⁽¹⁾	34	6	8.3	1050	37	600	17	U-MOSVIII-H		
	TPH4R003NL		±20	68 ⁽¹⁾	36	4	6.2	1110	39	640	14.8	U-MOSVIII-H		
	TPH3R203NL		±20	84 ⁽¹⁾	44	3.2	4.7	1600	53	890	21	U-MOSVIII-H		
	TPH4R803PL *		±20	90 ⁽¹⁾	69	4.8	6.2	1520	55	515	22	U-MOSIX-H		
	TPH2R903PL		±20	124 ⁽¹⁾	81	2.9	4.1	1780	60	620	26	U-MOSIX-H		
	TPH3R003PL		±20	134 ⁽¹⁾	90	3	4.2	2940	88	850	50	U-MOSIX-H		
	TPH1R403NL		±20	150 ⁽¹⁾	64	1.4	2.1	3400	93	1800	46	U-MOSVIII-H		
	TPH2R003PL		±20	180 ⁽¹⁾	116	2	2.6	4930	135	1455	86	U-MOSIX-H		
	TPHR9003NL		±20	220 ⁽¹⁾	78	0.9	1.4	5300	130	2700	74	U-MOSVIII-H		
	TPHR9203PL		±20	280 ⁽¹⁾	132	0.92	1.29	5800	190	1750	81	U-MOSIX-H		
	TPHR6503PL		±20	393 ⁽¹⁾	170	0.65	0.89	7700	220	2720	110	U-MOSIX-H		
	TPCA8052-H	40	±20	20	30	11.3	13.1	1620	85	280	25	U-MOSVI-H		
	TPCA8047-H		±20	32	45	7.3	8.5	2590	135	440	43	U-MOSVI-H		
	TPCA8046-H		±20	38	45	5.4	6.3	3545	185	600	55	U-MOSVI-H		
	TPCA8045-H		±20	46	45	3.6	4.1	5800	305	950	90	U-MOSVI-H		
	TPH7R204PL		±20	72 ⁽¹⁾	69	7.2	9.7	1570	35	380	24	U-MOSIX-H		
	TPH6R004PL		±20	87 ⁽¹⁾	81	6	8.4	2100	50	470	30	U-MOSIX-H		
	TPH3R704PL		±20	92	81	3.7	6	1910	41	470	27	U-MOSIX-H		
	TPH3R704PC		±20	118 ⁽¹⁾	90	3.7	5.8	2780	60	640	47	U-MOSIX-H		
	TPH2R104PL		±20	180 ⁽¹⁾	116	2.1	3.1	4790	70	1050	78	U-MOSIX-H		
	TPH1R204PB		±20	240 ⁽¹⁾	132	1.2	—	4400	55	1300	62	U-MOSIX-H		
	TPH1R204PL		±20	246 ⁽¹⁾	132	1.24	2.1	5500	93	1300	74	U-MOSIX-H		
	TPHR8504PL		±20	340 ⁽¹⁾	170	0.85	1.4	7370	58	1930	103	U-MOSIX-H		

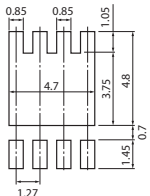
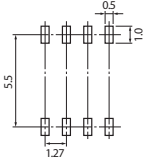
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Note (1): I_D (DC) (Silicon Limit)

*: New Product / 新製品

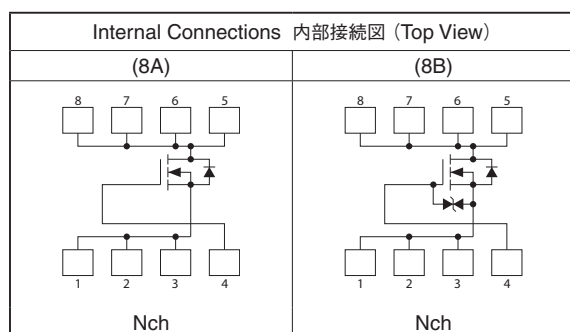


- The internal connection diagrams only show the general configurations of the circuits.
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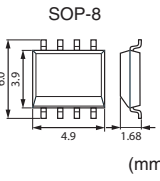
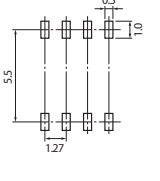
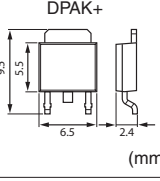
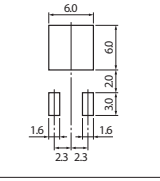
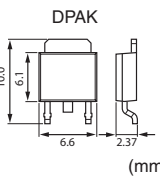
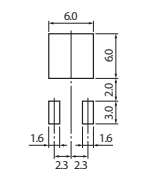
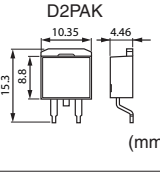
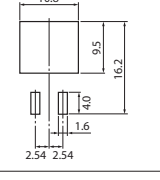
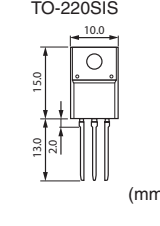
Package	Part Number	Absolute Maximum Ratings				R _{DS(ON)} max (mΩ)		Ciss typ. (pF)	Crss typ. (pF)	Coss typ. (pF)	Qg typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)	
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)	V _{GS} = 10 V	V _{GS} = 4.5 V								
(Continued from previous page)	TPH2R805PL	45	±20	150 ⁽¹⁾	116	2.8	3.9	3980	45	980	73	U-MOSIX-H	(8A)		
	TPH1R405PL		±20	232 ⁽¹⁾	132	1.4	2.3	4830	66	1210	74	U-MOSIX-H			
	TPH1R005PL		±20	280 ⁽¹⁾	170	1.04	1.7	7700	76	1860	122	U-MOSIX-H			
	TPCA8053-H		60	±20	15	30	22.3	24	1620	60	200	25			U-MOSVI-H
	TPCA8049-H			±20	28	45	10.4	11.2	3545	130	420	55			U-MOSVI-H
	TPH14006NH			±20	34 ⁽¹⁾	32	14	—	1000	25	310	16			U-MOSVIII-H
	TPCA8048-H	±20		35	45	6.6	7.1	5800	210	650	90	U-MOSVI-H			
	TPH11006NL	±20		40 ⁽¹⁾	34	11.4	17	1500	23	350	23	U-MOSVIII-H			
	TPH7R506NH	±20		55 ⁽¹⁾	45	7.5	—	1785	40	575	31	U-MOSVIII-H			
	TPH9R506PL	±20		68 ⁽¹⁾	81	9.5	15	1470	30	270	21	U-MOSIX-H			
	TPH5R906NH	±20		71 ⁽¹⁾	57	5.9	—	2340	50	745	38	U-MOSVIII-H			
	TPH7R006PL	±20		79 ⁽¹⁾	81	7	13.5	1440	35	300	22	U-MOSIX-H			
	TPH4R606NH	±20		85 ⁽¹⁾	63	4.6	—	3050	60	990	49	U-MOSVIII-H			
	TPH2R306NH	±20		130 ⁽¹⁾	78	2.3	—	4700	55	1500	72	U-MOSVIII-H			
	TPH3R506PL	±20	135 ⁽¹⁾	116	3.5	6.7	3400	50	600	55	U-MOSIX-H				
	TPH2R506PL	±20	160 ⁽¹⁾	132	2.5	4.4	4180	60	770	60	U-MOSIX-H				
	TPH1R306PL	±20	260 ⁽¹⁾	170	1.34	2.3	6250	80	1160	91	U-MOSIX-H				
	TPH1R306P1 *	75	±20	260 ⁽¹⁾	170	1.28	2.3	6250	80	1160	91	U-MOSIX-H			
	TPH2R608NH		±20	168 ⁽¹⁾	142	2.6	—	4600	50	1100	72	U-MOSVIII-H			
	TPCA8051-H		80	±20	28	45	9.4	9.8	5800	150	520	91			U-MOSVI-H
	TPH12008NH			±20	44 ⁽¹⁾	48	12.3	—	1490	16	330	22			U-MOSVIII-H
	TPH8R008NH	±20		63 ⁽¹⁾	61	8	—	2300	23	520	35	U-MOSVIII-H			
	TPH4R008NH	±20		100 ⁽¹⁾	78	4	—	4100	32	890	59	U-MOSVIII-H			
	TPH1400ANH	100	±20	42 ⁽¹⁾	48	13.6	—	1440	15	260	22	U-MOSVIII-H			
	TPH8R80ANH		±20	59 ⁽¹⁾	61	8.8	—	2180	21	410	33	U-MOSVIII-H			
	TPH6R30ANL		±20	66 ⁽¹⁾	54	6.3	10.3	3300	27	410	55	U-MOSVIII-H			
	TPH4R10ANL		±20	92 ⁽¹⁾	67	4.1	6.6	4850	29	640	75	U-MOSVIII-H			
	TPH4R50ANH	150	±20	93 ⁽¹⁾	78	4.5	—	4000	31	700	58	U-MOSVIII-H			
	TPH5R60APL *		±20	106 ⁽¹⁾	132	5.6	9.5	3300	27	410	52	U-MOSIX-H			
	TPH3R70APL *		±20	150 ⁽¹⁾	170	3.7	6.2	4850	29	640	67	U-MOSIX-H			
	TPH5900CNH		±20	18 ⁽¹⁾	42	59	—	460	3	80	7	U-MOSVIII-H			
	TPH3300CNH	200	±20	29 ⁽¹⁾	57	33	—	810	3	140	10.6	U-MOSVIII-H			
	TPH1500CNH		±20	50 ⁽¹⁾	78	15.4	—	1700	7	280	22	U-MOSVIII-H			
	TPH1110ENH		±20	13 ⁽¹⁾	42	114	—	460	3	55	7	U-MOSVIII-H			
	TPH6400ENH		±20	21 ⁽¹⁾	57	64	—	810	3	90	11.2	U-MOSVIII-H			
	TPH2900ENH	250	±20	36 ⁽¹⁾	78	29	—	1700	7	180	22	U-MOSVIII-H			
	TPH2010FNH		±20	10 ⁽¹⁾	42	198	—	460	3	45	7	U-MOSVIII-H			
	TPH1110FNH		±20	15 ⁽¹⁾	57	112	—	810	3	75	11	U-MOSVIII-H			
	TPH5200FNH		±20	27 ⁽¹⁾	78	52	—	1700	7	140	22	U-MOSVIII-H			
SOP-8	TPC8067-H	30	±20	9	1.9	25	33	690	28	120	9.5	U-MOSVII-H	(8A)		
	TPC8066-H		±20	11	1.9	16	19	1100	49	190	15	U-MOSVII-H			
	TPC8065-H		±20	13	1.9	11.6	14.7	1350	63	240	20	U-MOSVII-H			
	TP89R103NL		±20	15	1.9	9.1	12.9	630	21	350	9.8	U-MOSVIII-H			
	TPC8064-H		±20	16	1.9	8.4	10.8	1600	78	290	23	U-MOSVII-H			
	TPC8063-H		±20	17	1.9	7	8.9	1900	93	340	27	U-MOSVII-H			
	TPC8055-H		±20	18	1.9	2.1	2.5	6400	360	1200	91	U-MOSVII-H			
	TPC8056-H		±20	18	1.9	2.4	2.9	5200	290	1000	74	U-MOSVII-H			
	TPC8057-H		±20	18	1.9	2.8	3.4	4300	240	810	61	U-MOSVII-H			
	TPC8058-H		±20	18	1.9	3.2	4	3600	200	680	51	U-MOSVII-H			
	TPC8059-H		±20	18	1.9	4	5	2900	150	530	41	U-MOSVII-H			
	(Continued on next page)		TPC8062-H	±20	18	1.9	5.8	7.3	2400	120	430	34			U-MOSVII-H

Note (1): I_D (DC) (Silicon Limit)

*: New Product / 新製品

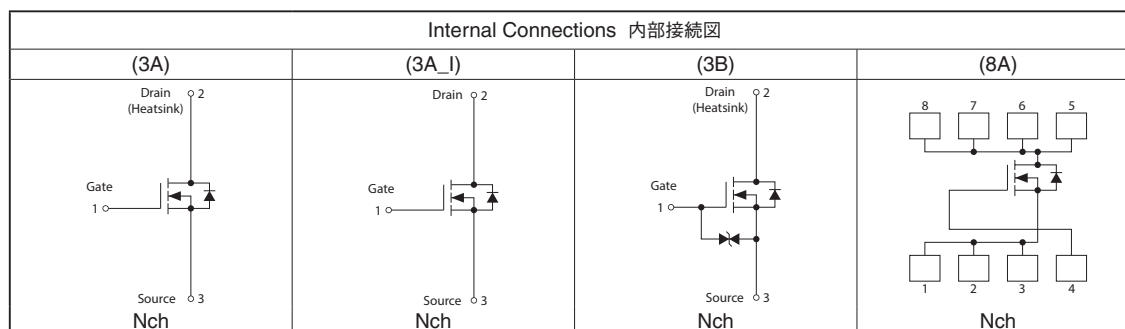


- The internal connection diagrams only show the general configurations of the circuits.
- 内部接続図はイメージ図です。

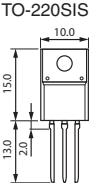
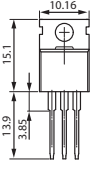
Package	Part Number	Absolute Maximum Ratings				R _{DS(ON)} max (mΩ)		Ciss typ. (pF)	Crss typ. (pF)	Coss typ. (pF)	Qg typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)	V _{GSL} = 10 V	V _{GSL} = 4.5 V							
(Continued from previous page)  (mm)	TP86R203NL	30	±20	19 ⁽¹⁾	1.9	6.2	8.5	1050	37	600	17	U-MOSVIII-H	(8A)	
	TPC8089-H		±20	7.2	1.9	32	36	850	40	145	14	U-MOSVI-H		
	TPC8052-H		±20	12	1.9	11.5	13.3	1620	85	280	25	U-MOSVI-H		
	TPC8047-H	40	±20	16	1.9	7.6	8.8	2590	135	440	43	U-MOSVI-H		
	TPC8045-H		±20	18	1.9	3.9	4.4	5800	305	950	90	U-MOSVI-H		
	TPC8046-H		±20	18	1.9	5.7	6.6	3545	185	600	57	U-MOSVI-H		
	TPC8053-H		±20	9	1.9	22.5	24.2	1620	60	200	25	U-MOSVI-H		
	TPC8050-H		±20	11	1.9	14.5	15.6	2590	95	300	41	U-MOSVI-H		
	TPC8049-H	60	±20	13	1.9	10.7	11.5	3545	130	420	56	U-MOSVI-H		
	TPC8048-H		±20	16	1.9	6.9	7.4	5800	210	650	87	U-MOSVI-H		
	TPC8051-H	80	±20	13	1.9	9.7	10.1	5800	150	520	85	U-MOSVI-H		
 (mm)	TK33S10N1H	100	±20	33	125	9.7	—	2050	140	1070	28	U-MOSVIII-H	(3B)	
 (mm)	TK40P03M1	30	±20	40	33	10.8	14.4	1150	85	260	17.5	U-MOSVI-H	(3A)	
	TK45P03M1		±20	45	39	9.7	12	1500	100	320	25	U-MOSVI-H		
	TK50P03M1		±20	50	47	7.5	9.8	1700	125	380	25.3	U-MOSVI-H		
	TK20P04M1	40	±20	20	27	29	34	985	37	159	15	U-MOSVI-H		
	TK40P04M1		±20	40	47	11	13.4	1920	90	310	29	U-MOSVI-H		
	TK50P04M1		±20	50	60	8.7	10.2	2600	110	420	38	U-MOSVI-H		
	TK3R1P04PL *	60	±20	130 ⁽¹⁾	87	3.1	4.3	4670	70	1000	60	U-MOSIX-H		
	TK6R7P06PL *		±20	74 ⁽¹⁾	66	6.7	11.1	1990	45	350	26	U-MOSIX-H		
	TK4R4P06PL *		±20	106 ⁽¹⁾	87	4.4	7.1	3280	60	600	48.2	U-MOSIX-H		
	TK110P10PL *	100	±20	60 ⁽¹⁾	75	10.6	16	2040	22	310	33	U-MOSIX-H		
	TK7R7P10PL *		±20	79 ⁽¹⁾	93	7.7	11.5	2800	25	450	44	U-MOSIX-H		
 (mm)	TK65G10N1	100	±20	136 ⁽¹⁾	156	4.5	—	5400	42	950	81	U-MOSVIII-H	(3A)	
 (mm)	TK3R1A04PL	40	±20	82	36	3.1	3.8	4670	70	1000	63.4	U-MOSIX-H	(3A_I)	
	TK30A06N1	60	±20	43 ⁽¹⁾	25	15	—	1050	33	400	16	U-MOSVIII-H		
	TK8R2A06PL		±20	50	36	8.2	11.4	1990	45	350	28	U-MOSIX-H		
	TK40A06N1		±20	60 ⁽¹⁾	30	10.4	—	1700	40	580	23	U-MOSVIII-H		
	TK5R3A06PL *		±20	62 ⁽¹⁾	36	5.3	9.3	2380	50	470	36	U-MOSIX-H		
	TK4R3A06PL		±20	68	36	4.3	7.2	3280	60	600	48.2	U-MOSIX-H		
	TK3R3A06PL *		±20	88 ⁽¹⁾	42	3.3	4.9	5000	55	950	71	U-MOSIX-H		
	TK58A06N1		±20	105 ⁽¹⁾	35	5.4	—	3400	45	1120	46	U-MOSVIII-H		
	TK100A06N1		±20	263 ⁽¹⁾	45	2.7	—	10500	50	3500	140	U-MOSVIII-H		
(Continued on next page)	TK35A08N1	80	±20	55 ⁽¹⁾	30	12.2	—	1700	18	440	25	U-MOSVIII-H		

Note (1): I_D (DC) (Silicon Limit)

*: New Product / 新製品

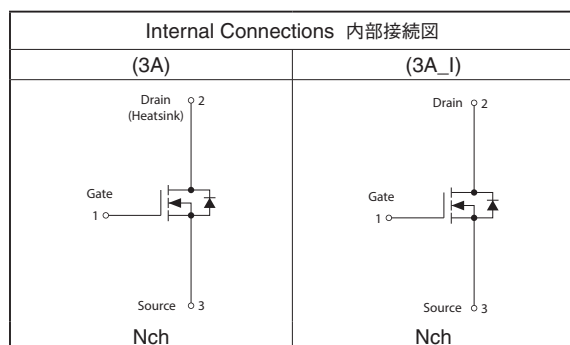


- The internal connection diagrams only show the general configurations of the circuits.
- 内部接続図はイメージ図です。

Package	Part Number	Absolute Maximum Ratings				R _{DS(ON)} max (mΩ)		Ciss typ. (pF)	Crss typ. (pF)	Coss typ. (pF)	Qg typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)		
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)	V _{GS} = 10 V	V _{GS} = 4.5 V									
(Continued from previous page)  TO-220SIS (mm)	TK46A08N1	80	±20	80 ⁽¹⁾	35	8.4	—	2500	22	620	37	U-MOSVIII-H	(3A_I)			
	TK72A08N1		±20	157 ⁽¹⁾	45	4.5	—	5500	38	1300	81	U-MOSVIII-H				
	TK100A08N1		±20	214 ⁽¹⁾	45	3.2	—	9000	52	2100	130	U-MOSVIII-H				
	TK110A10PL *	100	±20	41 ⁽¹⁾	36	10.8	16	2040	22	310	33	U-MOSIX-H				
	TK7R4A10PL *		±20	50	42	7.4	11.2	2800	25	450	44	U-MOSIX-H				
	TK22A10N1		±20	52 ⁽¹⁾	30	13.8	—	1800	18	310	28	U-MOSVIII-H				
	TK6R7A10PL *		±20	56	42	6.7	10.1	3455	30	520	58	U-MOSIX-H				
	TK34A10N1		±20	75 ⁽¹⁾	35	9.5	—	2600	23	450	38	U-MOSVIII-H				
	TK4R1A10PL *		±20	85 ⁽¹⁾	54	4.1	5.9	6320	45	950	104	U-MOSIX-H				
	TK40A10N1		±20	90 ⁽¹⁾	35	8.2	—	3000	29	520	49	U-MOSVIII-H				
	TK3R2A10PL *		±20	106 ⁽¹⁾	54	3.2	4.3	9500	65	1500	161	U-MOSIX-H				
	TK65A10N1		±20	148 ⁽¹⁾	45	4.8	—	5400	42	950	81	U-MOSVIII-H				
	TK100A10N1		±20	207 ⁽¹⁾	45	3.8	—	8800	63	1500	140	U-MOSVIII-H				
	TK32A12N1	120	±20	60 ⁽¹⁾	30	13.8	—	2000	13	330	34	U-MOSVIII-H				
	TK42A12N1		±20	88 ⁽¹⁾	35	9.4	—	3100	16	490	52	U-MOSVIII-H				
	TK56A12N1		±20	112 ⁽¹⁾	45	7.5	—	4200	19	650	69	U-MOSVIII-H				
	TK72A12N1		±20	179 ⁽¹⁾	45	4.5	—	8100	30	1200	130	U-MOSVIII-H				
 TO-220 (mm)	TK3R3E03GL	30	±20	147 ⁽¹⁾	104	3.3	4.1	4350	260	710	67	U-MOSVII-H	(3A)			
	TK3R1E04PL	40	±20	128 ⁽¹⁾	87	3.1	3.8	4670	70	1000	63.4	U-MOSIX-H				
	TK30E06N1	60	±20	43 ⁽¹⁾	53	15	—	1050	33	400	16	U-MOSVIII-H			(3A_I)	
	TK40E06N1		±20	60 ⁽¹⁾	67	10.4	—	1700	40	580	23	U-MOSVIII-H				
	TK3R2E06PL *		±20	160 ⁽¹⁾	168	3.2	4.7	5000	55	950	71	U-MOSIX-H				
	TK8R2E06PL		±20	75 ⁽¹⁾	81	8.2	11.4	1990	45	350	28	U-MOSIX-H				
	TK5R1E06PL *		±20	98 ⁽¹⁾	87	5.1	8.8	2380	50	470	36	U-MOSIX-H				
	TK58E06N1		±20	105 ⁽¹⁾	110	5.4	—	3400	45	1120	46	U-MOSVIII-H				
	TK4R3E06PL	80	±20	106 ⁽¹⁾	87	4.3	7.2	3280	60	600	48.2	U-MOSIX-H	(3A)			
	TK100E06N1		±20	263 ⁽¹⁾	255	2.3	—	10500	50	3500	140	U-MOSVIII-H				
	TK35E08N1		±20	55	72	12.2	—	1700	18	440	25	U-MOSVIII-H				
	TK46E08N1		±20	80	103	8.4	—	2500	22	620	37	U-MOSVIII-H				
	TK72E08N1		±20	157 ⁽¹⁾	192	4.3	—	5500	38	1300	81	U-MOSVIII-H				
	TK100E08N1		±20	214 ⁽¹⁾	255	3.2	—	9000	52	2100	130	U-MOSVIII-H				
	TK22E10N1		100	±20	52	72	13.8	—	1800	18	310	28			U-MOSVIII-H	(3A_I)
	TK110E10PL *			±20	64 ⁽¹⁾	87	10.7	16	2040	22	310	33			U-MOSIX-H	
	TK34E10N1			±20	75	103	9.5	—	2600	23	450	38			U-MOSVIII-H	
	TK40E10N1			±20	90	126	8.2	—	3000	29	520	49			U-MOSVIII-H	
	TK7R2E10PL *	±20		94 ⁽¹⁾	123	7.2	11	2800	25	450	44	U-MOSIX-H				
	TK6R4E10PL *	±20		112	152	6.4	9.7	3455	30	520	58	U-MOSIX-H				
	TK65E10N1	±20		148 ⁽¹⁾	192	4.8	—	5400	42	950	81	U-MOSVIII-H				
	TK3R9E10PL *	±20		180 ⁽¹⁾	230	3.9	5.8	6320	45	950	96	U-MOSIX-H				
	TK100E10N1	±20		207 ⁽¹⁾	255	3.4	—	8800	63	1500	140	U-MOSVIII-H				
	TK2R9A10PL *	±20		240 ⁽¹⁾	300	2.9	4.1	9500	65	1500	161	U-MOSIX-H				
	TK32E12N1	120		±20	60	98	13.8	—	2000	13	330	34	U-MOSVIII-H		(3A)	
	TK42E12N1		±20	88	140	9.4	—	3100	16	490	52	U-MOSVIII-H				
	TK56E12N1		±20	112 ⁽¹⁾	168	7	—	4200	19	650	69	U-MOSVIII-H				
	TK72E12N1		±20	179 ⁽¹⁾	255	4.4	—	8100	30	1200	130	U-MOSVIII-H				

Note (1): I_D (DC) (Silicon Limit)

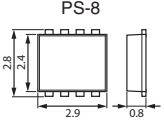
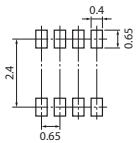
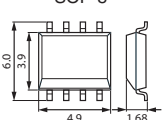
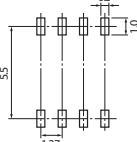
*: New Product / 新製品



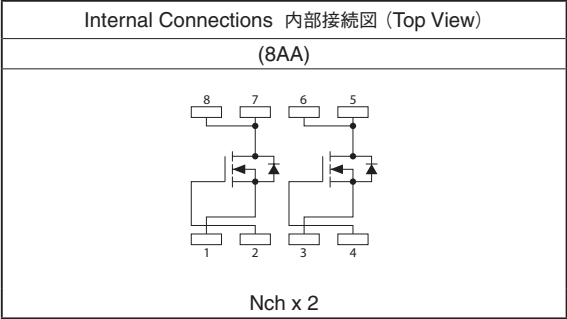
• The internal connection diagrams only show the general configurations of the circuits.

• 内部接続図はイメージ図です。

(Dual Channel) / (デュアルチャネル)

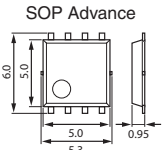
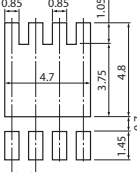
Package	Part Number	Absolute Maximum Ratings				R _{DS(ON)} max (mΩ)		C _{iss} typ. (pF)	C _{rss} typ. (pF)	C _{oss} typ. (pF)	Q _g typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)	V _{GS} = 10 V	V _{GS} = 4.5 V							
 (mm)	TPCP8205-H	30	±20	6.5	1.48 (1)	26	29	830	53	177	13.8	U-MOSVI-H	(8AA)	
 (mm)	TPC8224-H	30	±20	8	1.5	26	34	690	28	120	9.5	U-MOSVII-H	(8AA)	
	TPC8223-H		±20	9	1.5	17	21	1190	55	210	17	U-MOSVII-H		
	TPC8227-H	40	±20	5.1	1.5	33	40	640	35	115	10	U-MOSVI-H		
	TPC8228-H	60	±20	3.8	1.5	57	64	640	25	90	11	U-MOSVI-H		
	TPC8229-H	80	±20	3.2	1.5	80	87	640	17	75	11	U-MOSVI-H		

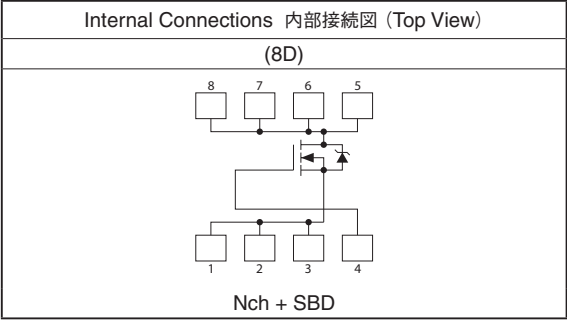
Note (1): Device mounted on a glass board. t = 5 seconds. / ガラスエポキシ基板。t = 5 秒。



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- 内部接続図はイメージ図です。

(Built-in schottky Barrier Diode) / (SBD 混載品)

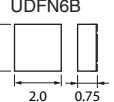
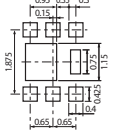
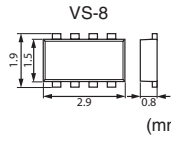
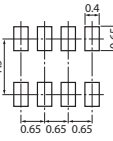
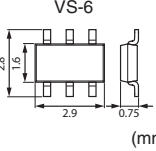
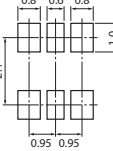
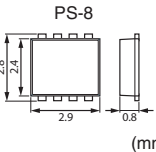
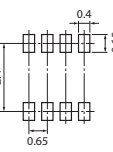
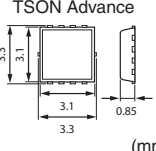
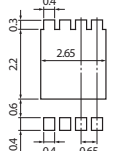
Package	Part Number	Absolute Maximum Ratings				R _{DS(ON)} max (mΩ)		C _{iss} typ. (pF)	C _{rss} typ. (pF)	C _{oss} typ. (pF)	Q _g typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)	V _{GS} = 10 V	V _{GS} = 4.5 V							
 (mm)	TPCA8A11-H	30	±20	35	52	3.6	4.6	3200	170	600	46	U-MOSVII-H	(8D)	
	TPCA8A10-H		±20	40	58	3	3.8	4000	200	810	57	U-MOSVII-H		
	TPCA8A09-H		±20	51	70	2.3	2.8	5900	250	1100	82	U-MOSVII-H		



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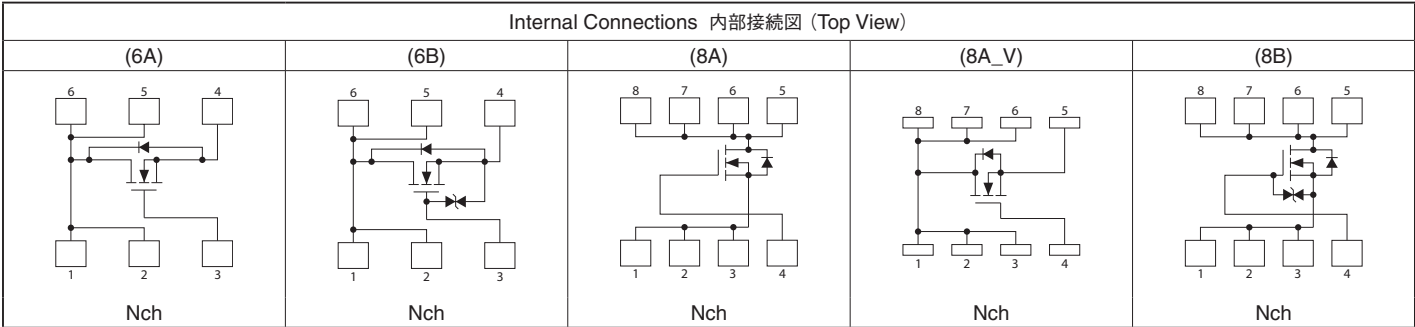
Low On-Resistance Series / 低オン抵抗シリーズ
(Single N-Channel) / (シングルNチャネル)

(1/4)

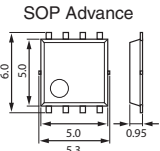
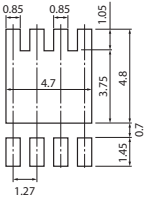
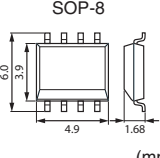
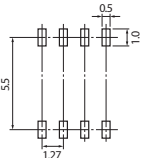
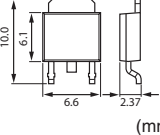
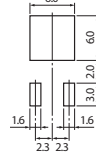
Package	Part Number	Absolute Maximum Ratings				R _{DS(ON)} max (mΩ)					C _{iss} typ. (pF)	C _{rss} typ. (pF)	C _{oss} typ. (pF)	Q _g typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)	
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)	V _{GS} = 10 V	V _{GS} = 6 V	V _{GS} = 4.5 V	V _{GS} = 2.5 V	V _{GS} = 1.8 V								
 (mm)	SSM6K504NU	30	±20	9	1.25	19.5	—	26	—	—	620	42	110	4.8	U-MOSVII-H	(6B)		
	SSM6K513NU		*	±20	15	1.25	8.9	—	12	—	—	1130	52	350	7.5			U-MOSIX-H
	SSM6K514NU	*	40	±20	12	1.25	11.6	—	17.3	—	—	1110	26	245	7.5	U-MOSIX-H		(6A)
	SSM6K341NU	*	60	±20	6	1.25	36	—	51	—	—	550	35	300	9.3	U-MOSVIII-H		
	SSM6K361NU	*	100	±20	3.5	1.25	69	—	92	—	—	430	22	160	3.2	U-MOSVIII-H		(6B)
 (mm)	TPCF8003	20	±12	7	2.5 (1)	—	—	18	34	—	500	155	215	9.5	U-MOSIV	(8A_V)		
	TPCF8004	30	±20	7	2.5 (1)	24	—	30	—	—	610	34	130	9	U-MOSVII			
 (mm)	TPC6012	20	±12	6	2.2 (1)	—	—	20	38	—	630	150	180	9	U-MOSIV	(6A)		
	TPC6067	30	±20	6	2.2 (1)	23	—	29	—	—	610	34	130	8	U-MOSVII			
 (mm)	TPCP8011	40	±20	5	1.96 (1)	31.8	51.2	—	—	—	505	66	115	11.8	U-MOSIV	(8B)		
	TPCP8010		±20	6	1.96 (1)	23.8	38.4	—	—	—	600	75	132	13.1	U-MOSIV			
	TPCP8009		±20	10	2.01 (1)	11.8	19.5	—	—	—	1250	165	265	25.1	U-MOSIV			
	TPCP8013	60	±20	4	1.96 (1)	51.8	77.9	—	—	—	515	48	86	12	U-MOSIV			
	TPCP8012		±20	8	2.01 (1)	20.2	29.1	—	—	—	1160	120	200	26.6	U-MOSIV			
 (mm)	TPCC8093	20	±12	21	30	—	—	5.8	9.5	—	1860	140	365	16	U-MOSVII	(8A)		
	TPCC8074	30	±20	20	30	6.3	—	8.5	—	—	1800	88	330	25	U-MOSVII			
	TPCC8073		±20	27	39	4.5	—	5.9	—	—	2600	130	470	37	U-MOSVII			
	TPN6R303NC		±20	43 (2)	19	6.3	—	8.4	—	—	1370	110	420	24	U-MOSVIII			
	TPN4R203NC		±20	53 (2)	22	4.2	—	6.4	—	—	1370	110	420	24	U-MOSVIII			
	TPN2R503NC		±20	85 (2)	35	2.5	—	4.1	—	—	2230	160	650	40	U-MOSVIII			
	TPN2R203NC		±20	100 (2)	42	2.2	—	3.6	—	—	2230	160	650	34	U-MOSVIII			
	TPCC8084	33	±20	21	32	6.7	—	9	—	—	1900	98	300	27	U-MOSVII	(8B)		
	TPCC8076		±20	27	39	4.6	—	6.2	—	—	2500	120	430	34	U-MOSVII			

Note (1): Device mounted on a glass board. t = 5 seconds. / ガラスエポキシ基板。t = 5 秒。
(2): I_D (DC) (Silicon Limit)

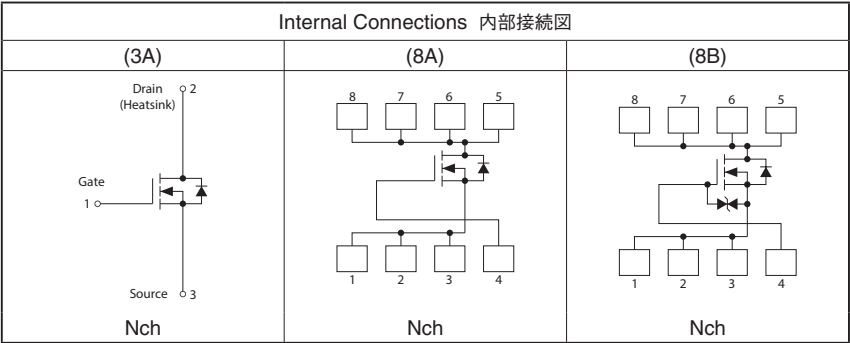
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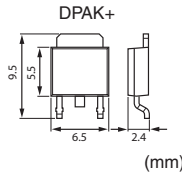
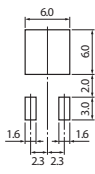
• The internal connection diagrams only show the general configurations of the circuits.
• 内部接続図はイメージ図です。

Package	Part Number	Absolute Maximum Ratings				RDS(ON) max (mΩ)					Ciss typ. (pF)	Crss typ. (pF)	Coss typ. (pF)	Qg typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)
		Vbss (V)	Vgss (V)	Id (A)	Pd (W)	Vgs1 = 10 V	Vgs1 = 6 V	Vgs1 = 4.5 V	Vgs1 = 2.5 V	Vgs1 = 1.8 V							
 (mm)	TPCA8082	30	±20	32	45	3.8	—	4.8	—	—	2900	150	530	41	U-MOSVII	(8A)	
	TPCA8081		±20	38	52	3	—	3.8	—	—	3600	200	680	51	U-MOSVII		
	TPCA8080		±20	42	57	2.6	—	3.2	—	—	4300	240	810	61	U-MOSVII		
	TPCA8088		±20	48	63	2.2	—	2.7	—	—	5200	290	1000	74	U-MOSVII		
	TPCA8087		±20	56	70	1.9	—	2.3	—	—	6400	360	1200	91	U-MOSVII		
	TPHR9003NC		±20	220 (1)	78	0.9	—	1.4	—	—	5300	130	2700	75	U-MOSVIII		
	TPCA8075	33	±20	48	63	2.4	—	3.1	—	—	5200	300	970	70	U-MOSVII		
	TPCA8078		±20	54	70	2.1	—	2.6	—	—	6400	370	1200	90	U-MOSVII		
 (mm)	TPC8092	30	±20	15	1.9	9	—	11.1	—	—	1800	88	330	25	U-MOSVII	(8A)	
	TPC8074		±20	17	1.9	6.5	—	8.7	—	—	1800	88	330	25	U-MOSVII	(8B)	
	TPC8086		±20	17	1.9	6.4	—	8.5	—	—	1900	90	330	26	U-MOSVII	(8A)	
	TPC8073		±20	18	1.9	4.7	—	6.1	—	—	2600	130	470	37	U-MOSVII	(8B)	
	TPC8080	30	±20	18	1.9	2.8	—	3.4	—	—	4300	240	810	61	U-MOSVII	(8A)	
	TPC8081		±20	18	1.9	3.2	—	4	—	—	3600	200	680	51	U-MOSVII	(8B)	
	TPC8082		±20	18	1.9	4	—	5	—	—	2900	150	530	41	U-MOSVII	(8A)	
	TPC8085		±20	18	1.9	4.7	—	6.1	—	—	2600	130	470	37	U-MOSVII	(8B)	
	TPC8087	33	±20	18	1.9	2.1	—	2.5	—	—	6400	360	1200	91	U-MOSVII	(8A)	
	TPC8088		±20	18	1.9	2.4	—	2.9	—	—	5200	290	1000	74	U-MOSVII	(8B)	
	TPC8084		±20	17	1.9	6.9	—	9.2	—	—	1900	98	300	27	U-MOSVII	(8A)	
	TPC8075		±20	18	1.9	2.6	—	3.3	—	—	5200	300	970	70	U-MOSVII	(8B)	
	TPC8076	33	±20	18	1.9	4.9	—	6.5	—	—	2500	120	430	34	U-MOSVII	(8A)	
	TPC8078		±20	18	1.9	2.3	—	2.8	—	—	6400	370	1200	90	U-MOSVII	(8A)	
 (mm)	TK8P25DA	250	±20	7.5	55	500	—	—	—	—	550	5.1	40	16	π-MOSVII	(3A)	
	TK13P25D		±20	13	96	250	—	—	—	—	1100	8	66	25	π-MOSVII		

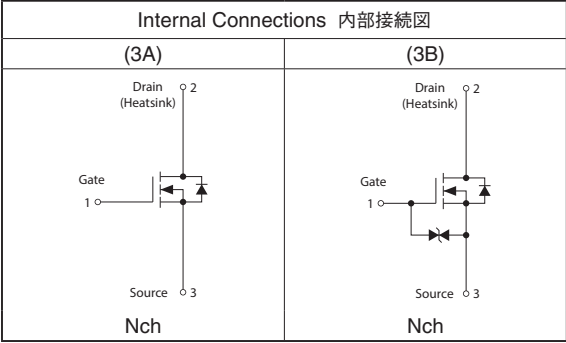
Note (1): Id (DC) (Silicon Limit)



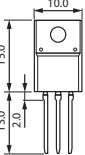
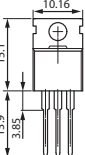
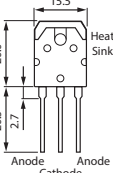
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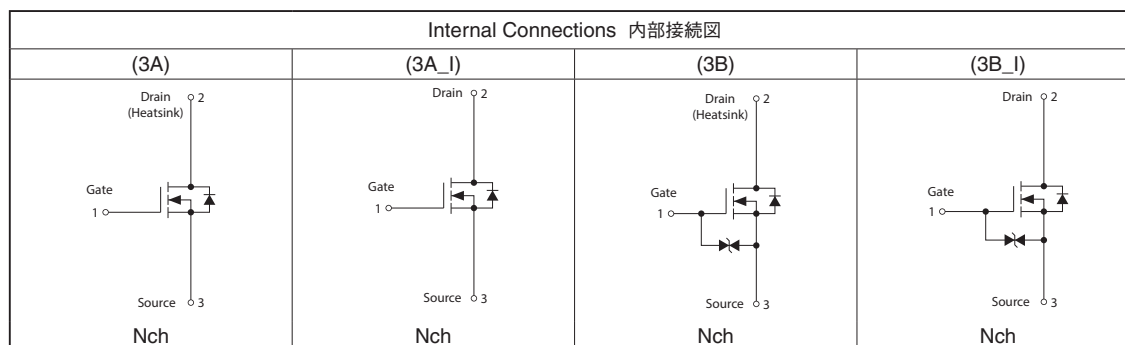
Package	Part Number	Absolute Maximum Ratings				R _{DS(ON)} max (mΩ)					C _{iss} typ. (pF)	C _{rss} typ. (pF)	C _{oss} typ. (pF)	Q _g typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)	
		V _{DS} (V)	V _{GS} (V)	I _D (A)	P _D (W)	V _{GS} = 10 V	V _{GS} = 6 V	V _{GS} = 4.5 V	V _{GS} = 2.5 V	V _{GS} = 1.8 V								
 (mm)	TK10S04K3L	40	±20	10	25	28	54	—	—	—	410	55	100	10	U-MOSIV	(3B)		
	TK15S04N1L		±20	15	46	17.8	—	37	—	—	610	50	390	10	U-MOSVIII-H			
	TK20S04K3L		±20	20	38	14	26	—	—	—	820	110	190	18	U-MOSIV			
	TK35S04K3L		±20	35	58	10.3	15	—	—	—	1370	180	320	28	U-MOSIV			
	TK50S04K3L		±20	50	68	5.4	10	—	—	—	2010	255	435	42	U-MOSIV			
	TK65S04K3L		±20	65	88	4.5	7.9	—	—	—	2800	440	680	63	U-MOSIV			
	TK65S04N1L		±20	65	107	4.3	—	7.8	—	—	2550	130	1430	39	U-MOSVIII-H			
	TK80S04K3L		±20	80	100	3.1	4.8	—	—	—	4340	570	910	87	U-MOSIV			
	TK100S04N1L		±20	100	180	2.3	—	4.5	—	—	5490	220	3000	76	U-MOSVIII-H			
	TK1R4S04PB		±20	120	180	1.35	1.9	—	—	—	5500	490	3400	103	U-MOSIX-H			
	TK8S06K3L	60	±20	8	25	54	80	—	—	—	400	40	80	10	U-MOSIV	(3B)		
	TK20S06K3L		±20	20	38	29	40	—	—	—	780	75	136	18	U-MOSIV			
	TK25S06N1L		±20	25	57	18.5	—	36.8	—	—	855	69	490	15	U-MOSVIII-H			
	TK30S06K3L		±20	30	58	18	30	—	—	—	1350	130	230	28	U-MOSIV			
	TK40S06N1L		±20	40	88.2	10.5	—	18	—	—	1650	107	835	26	U-MOSVIII-H			
	TK45S06K3L		±20	45	68	10.5	16.4	—	—	—	1950	185	315	41	U-MOSIV			
	TK60S06K3L		±20	60	88	8	12.3	—	—	—	2900	280	460	60	U-MOSIV			
	TK80S06K3L		±20	80	100	5.5	7.8	—	—	—	4200	400	650	85	U-MOSIV			
	TK90S06N1L		±20	90	157	3.3	—	5.2	—	—	5400	350	2630	81	U-MOSVIII-H			
	TK7S10N1Z		100	±20	7	50	48	—	—	—	—	470	36	260	7.1			U-MOSVIII-H
	TK11S10N1L	*		±20	11	65	28	—	50	—	—	850	67	370	15	U-MOSVIII-H		
	TK33S10N1L	±20		33	125	9.7	—	16.2	—	—	2250	145	1010	33	U-MOSVIII-H			
	TK33S10N1Z	±20		33	125	9.7	—	—	—	—	2050	140	1070	28	U-MOSVIII-H			
	TK40S10K3Z	±20		40	93	18	—	—	—	—	3110	245	400	61	U-MOSIV			
	TK55S10N1	±20		55	157	6.5	—	—	—	—	3280	210	1520	49	U-MOSVIII-H			
															(3A)			

*: New Product / 新製品



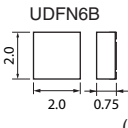
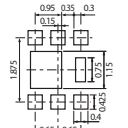
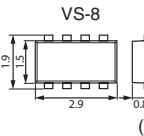
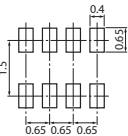
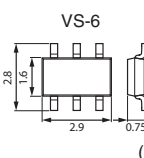
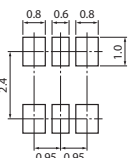
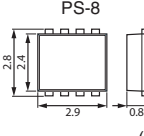
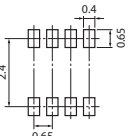
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Package	Part Number	Absolute Maximum Ratings				R _{DS(ON)} max (mΩ)					C _{iss} typ. (pF)	C _{rss} typ. (pF)	C _{oss} typ. (pF)	Q _g typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)	V _{GSL} = 10 V	V _{GSL} = 6 V	V _{GSL} = 4.5 V	V _{GSL} = 2.5 V	V _{GSL} = 1.8 V							
TO-220SIS  (mm)	TK50A04K3	40	±20	50	42	3.5	—	—	—	—	4500	900	1100	102	U-MOSIV	(3A_I)	
	TK80A04K3L		±20	80	48	2.4	3.5	—	—	—	—	9400	1200	1900	190	U-MOSIV	
	TK80A08K3	75	±20	80	40	4.5	—	—	—	—	8200	770	1140	175	U-MOSIV	(3A_I)	
	TK9A20DA	200	±20	8.5	30	400	—	—	—	—	550	5.6	40	14	π-MOSVII		
	TK15A20D		±20	15	35	180	—	—	—	—	1050	9	80	26	π-MOSVII		
	TK20A20D		±20	20	45	109	—	—	—	—	1650	14	120	43	π-MOSVII		
	TK25A20D		±20	25	45	70	—	—	—	—	2550	21	180	60	π-MOSVII		
	TK8A25DA	250	±20	7.5	30	500	—	—	—	—	550	5.1	40	16	π-MOSVII		
	TK13A25D		±20	13	35	250	—	—	—	—	1100	8	66	25	π-MOSVII		
	TK17A25D		±20	17	45	150	—	—	—	—	1650	12	110	43	π-MOSVII		
	TK20A25D		±20	20	45	100	—	—	—	—	2550	14	150	55	π-MOSVII		
	TK18A30D	300	±20	18	45	139	—	—	—	—	2600	17	140	60	π-MOSVII		
TO-220  (mm)	TK18E10K3	100	±20	18	71	42	—	—	—	—	1580	135	200	33	U-MOSIV	(3A)	
	TK13E25D	250	±20	13	102	250	—	—	—	—	1100	8	66	25	π-MOSVII		
TO-3P(N)  (mm)	TK70J04K3Z	40	±20	70	125	4.1	—	—	—	—	4500	800	1150	100	U-MOSIV	(3B)	
	TK75J04K3Z		±20	75	150	3	—	—	—	—	—	8450	1480	2060	190		
	2SK2313	60	±20	60	150	11	—	—	—	—	5400	920	2600	170	L ² -π-MOSV	(3A)	
	TK70J06K3		±20	70	125	6	—	—	—	—	4500	600	800	98	U-MOSIV		
	TK40J20D	200	±20	40	260	44	—	—	—	—	4300	30	280	100	π-MOSVII		
	TK70J20D		±20	70	410	27	—	—	—	—	6950	50	450	160	π-MOSVII		
	TK30J25D	250	±20	30	260	60	—	—	—	—	4300	30	250	100	π-MOSVII		
	TK60J25D		±20	60	410	38	—	—	—	—	7000	44	400	160	π-MOSVII		
TK50J30D	300	±20	50	410	52	—	—	—	—	7000	50	345	160	π-MOSVII			

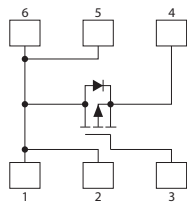
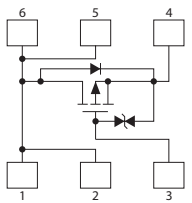
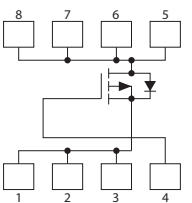
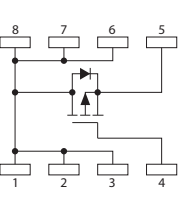
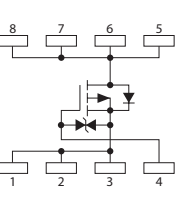


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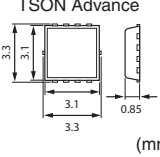
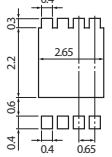
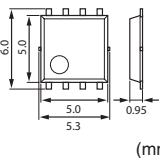
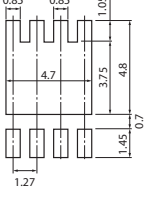
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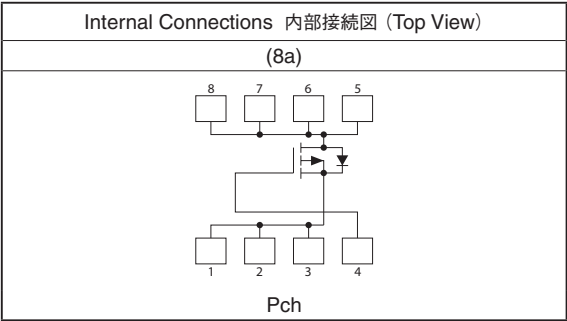
Package	Part Number	Absolute Maximum Ratings				R _{DS(ON)} max (mΩ)					C _{iss} typ. (pF)	C _{rss} typ. (pF)	C _{oss} typ. (pF)	Q _g typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)	
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)	V _{GSL} = 10 V	V _{GSL} = 6 V	V _{GSL} = 4.5 V	V _{GSL} = 2.5 V	V _{GSL} = 1.8 V								
 (mm)	SSM6J512NU *	-12	±10	-10	1.25	—	—	18.7	25.7	40.1	1400	225	250	19.5	U-MOSVII	(6b)		
	SSM6J505NU		±6	-12	1.25	—	—	12	16	21	2700	800	800	37.6	U-MOSVI			
	SSM6J511NU *		±10	-14	1.25	—	—	10	13.5	19.2	3350	570	590	47	U-MOSVII			
	SSM6J502NU	-20	±8	-6	1	—	—	23.1	28.3	38.4	1800	190	205	24.8	U-MOSVI			
	SSM6J503NU		±8	-6	1	—	—	32.4	41.7	57.9	840	99	118	12.8	U-MOSVI			
	SSM6J501NU		±8	-10	1	—	—	15.3	19	26.5	2600	280	290	29.9	U-MOSVI			
	SSM6J507NU *	-30	+20/-25	-10	1.25	20	—	28	—	—	1150	185	210	13.6	U-MOSVI			
 (mm)	TPCF8105	-20	±12	-6	2.5 (1)	—	—	30	41	100	1100	160	190	17	U-MOSVI	(8a_V)		
	TPCF8108		±12	-7	2.5 (1)	—	—	26	37	95	1320	180	210	19	U-MOSVI			
	TPCF8107	-30	+20/-25	-6	2.5 (1)	28	—	38	—	—	970	170	200	22	U-MOSVI			
 (mm)	TPC6130	-20	±12	-2.8	2.2 (1)	—	—	106	164	—	360	47	63	5.1	U-MOSVI	(6a)		
	TPC6113		±12	-5	2.2 (1)	—	—	55	85	—	690	93	117	10	U-MOSVI			
	TPC6111		±8	-5.5	2.2 (1)	—	—	40	57	80	700	100	140	10	U-MOSV	(6b)		
	TPC6110	-30	+20/-25	-4.5	2.2 (1)	56	—	77	—	—	510	85	110	14	U-MOSVI	(6a)		
 (mm)	TPCP8105	-20	±12	-7.2	1.68 (1)	—	—	17	23	60	2280	296	340	28	U-MOSVI	(8b)		
	TPCP8106	-30	+20/-25	-5.2	1.68 (1)	33	—	44	—	—	870	150	190	19	U-MOSVI	(8a)		
	TPCP8109	-40	+10/-20	-4.5	1.96 (1)	52.3	76.8	—	—	—	810	85	130	18	U-MOSVI	(8b)		
	TPCP8107		+10/-20	-8	2.01 (1)	18	26.8	—	—	—	2160	238	292	44.6	U-MOSVI			
	TPCP8111	-60	+10/-20	-3	1.96 (1)	117	158.4	—	—	—	760	60	90	17	U-MOSVI			
	TPCP8110		+10/-20	-5	2.01 (1)	39.5	53.2	—	—	—	2075	150	205	45	U-MOSVI			

Note (1): Device mounted on a glass board. t = 5 seconds. / ガラスエポキシ基板。t = 5 秒。 *: New Product / 新製品

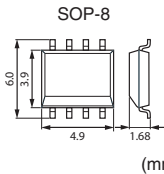
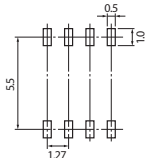
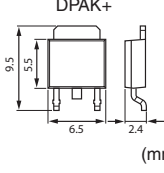
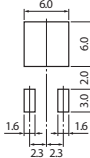
Internal Connections 内部接続図 (Top View)				
(6a)	(6b)	(8a)	(8a_V)	(8b)
 Pch	 Pch	 Pch	 Pch	 Pch

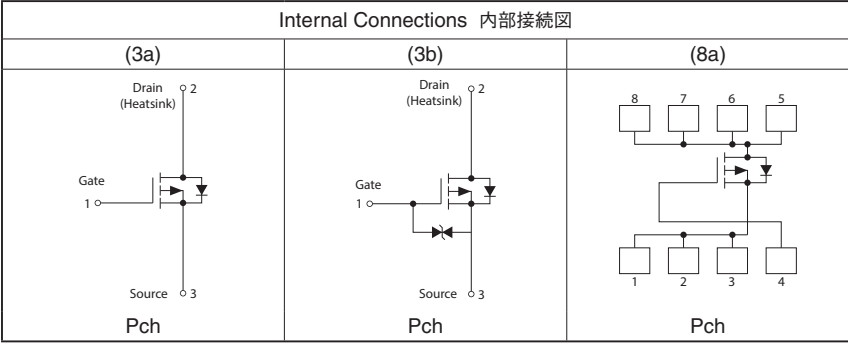
- The internal connection diagrams only show the general configurations of the circuits.
- 内部接続図はイメージ図です。

Package	Part Number	Absolute Maximum Ratings				R _{DS(ON)} max (mΩ)					C _{iss} typ. (pF)	C _{rss} typ. (pF)	C _{oss} typ. (pF)	Q _g typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)
		V _{DS} (V)	V _{GS} (V)	I _D (A)	P _D (W)	V _{GS} = 10 V	V _{GS} = 6 V	V _{GS} = 4.5 V	V _{GS} = 2.5 V	V _{GS} = 1.8 V							
 (mm)	TPCC8136	-20	±12	-9.4	18	—	—	16	22	60	2350	330	360	36	U-MOSVI	(8a)	
	TPCC8137		±12	-13	30	—	—	10	16	52	2990	400	435	43	U-MOSVI		
	TPCC8138		±12	-18	39	—	—	7.5	11	42	4165	575	620	63	U-MOSVI		
	TPN4R712MD		±12	-36	42	—	—	4.7	8.1	—	4300	640	700	65	U-MOSVI		
	TPCC8131	-30	+20/-25	-10	20	17.6	—	23	—	—	1700	280	320	40	U-MOSVI		
	TPCC8103		±20	-18	27	12	—	—	—	—	1600	340	490	38	U-MOSV		
	TPCC8104		+20/-25	-20	27	8.8	—	12.4	—	—	2260	430	485	58	U-MOSVI		
	TPCC8105		+20/-25	-23	30	7.8	—	10.4	—	—	3240	520	580	76	U-MOSVI		
 (mm)	TPH1R712MD	-20	±12	-60	78	—	—	1.7	2.7	—	1090	1550	2010	182	U-MOSVI	(8a)	
	TPCA8131	-30	+20/-25	-13	27	17	—	22	—	—	1700	280	320	40	U-MOSVI		
	TPCA8109		+20/-25	-24	30	9	—	13	—	—	2400	400	460	56	U-MOSVI		
	TPCA8128		+20/-25	-34	45	4.8	—	6.7	—	—	4800	800	900	115	U-MOSVI		
	TPCA8120		+20/-25	-45	45	3	—	4	—	—	7420	1180	1440	190	U-MOSVI		

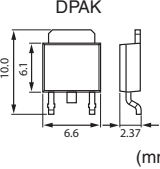
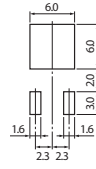
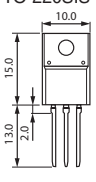


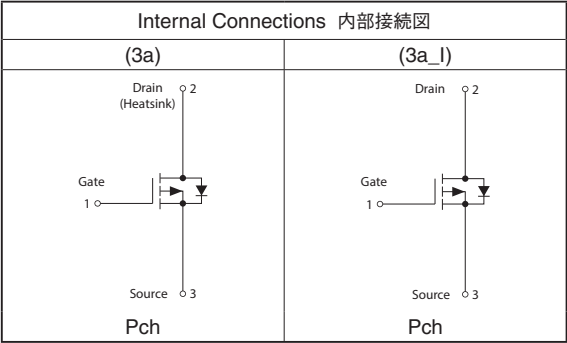
- The internal connection diagrams only show the general configurations of the circuits.
- 内部接続図はイメージ図です。

Package	Part Number	Absolute Maximum Ratings				RDS(ON) max (mΩ)					Ciss typ. (pF)	Crss typ. (pF)	Coss typ. (pF)	Qg typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)
		VDS (V)	VGS (V)	ID (A)	PD (W)	VGS = 10 V	VGS = 6 V	VGS = 4.5 V	VGS = 2.5 V	VGS = 1.8 V							
 SOP-8 (mm)	TPC8129	-30	+20/-25	-9	1.9	22	—	28	—	—	1650	260	300	39	U-MOSVI	(8a)	
	TPC8125		+20/-25	-10	1.9	13	—	17	—	—	2580	430	490	64	U-MOSVI		
	TPC8123		+20/-25	-11	1.9	9	—	12.5	—	—	2940	460	520	68	U-MOSVI		
	TPC8126		+20/-25	-11	1.9	10	—	14	—	—	2400	400	460	56	U-MOSVI		
	TPC8127		+20/-25	-13	1.9	6.5	—	8.9	—	—	3800	620	710	92	U-MOSVI		
	TPC8128		+20/-25	-16	1.9	5	—	6.9	—	—	4800	800	900	115	U-MOSVI		
	TPC8120		+20/-25	-18	1.9	3.2	—	4.2	—	—	7420	1180	1440	180	U-MOSVI		
	TPC8134	-40	+20/-25	-5	1.9	52	—	66	—	—	890	100	130	20	U-MOSVI		
	TPC8132		+20/-25	-7	1.9	25	—	33	—	—	1580	190	230	34	U-MOSVI		
	TPC8133		+20/-25	-9	1.9	15	—	18	—	—	2900	350	410	64	U-MOSVI		
	TPC8124		+20/-25	-12	1.9	8	—	10	—	—	4750	540	620	104	U-MOSVI		
 DPAK+ (mm)	TJ10S04M3L	-40	+10/-20	-10	27	44	62	—	—	—	930	90	140	19	U-MOSVI	(3b)	
	TJ20S04M3L		+10/-20	-20	41	22.2	32	—	—	—	1850	180	250	37	U-MOSVI		
	TJ40S04M3L		+10/-20	-40	68	9.1	13	—	—	—	4140	410	510	83	U-MOSVI		
	TJ60S04M3L		+10/-20	-60	90	6.3	9.4	—	—	—	6510	570	780	125	U-MOSVI		
	TJ80S04M3L		+10/-20	-80	100	5.2	7.9	—	—	—	7770	740	970	158	U-MOSVI		
	TJ8S06M3L	-60	+10/-20	-8	27	104	130	—	—	—	890	60	100	19	U-MOSVI		
	TJ15S06M3L		+10/-20	-15	41	50	63	—	—	—	1770	130	180	36	U-MOSVI		
	TJ30S06M3L		+10/-20	-30	68	21.8	28	—	—	—	3950	270	360	80	U-MOSVI		
	TJ50S06M3L		+10/-20	-50	90	13.8	17.4	—	—	—	6290	410	560	124	U-MOSVI		
	TJ60S06M3L		+10/-20	-60	100	11.2	14.5	—	—	—	7760	530	690	156	U-MOSVI		
	TJ15S10M3	-100	+10/-20	-15	75	130	—	—	—	—	3200	135	190	69	U-MOSVI	(3a)	



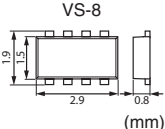
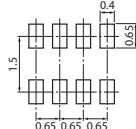
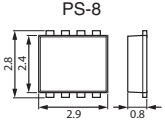
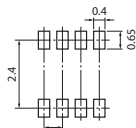
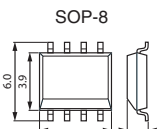
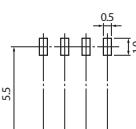
• The internal connection diagrams only show the general configurations of the circuits.
• 内部接続図はイメージ図です。

Package	Part Number	Absolute Maximum Ratings				R _{DS(ON)} max (mΩ)					C _{iss} typ. (pF)	C _{rss} typ. (pF)	C _{oss} typ. (pF)	Q _g typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)	V _{GS} = 10 V	V _{GS} = 6 V	V _{GS} = 4.5 V	V _{GS} = 2.5 V	V _{GS} = 1.8 V							
 (mm)	TJ15P04M3	-40	±20	-15	29	36	—	48	—	—	1100	130	170	26	U-MOSVI	(3a)	
 (mm)	TJ9A10M3	-100	±20	-9	19	170	—	—	—	—	2900	120	150	47	U-MOSVI	(3a_l)	
	TJ11A10M3		±20	-11	24	130	—	—	—	—	3200	135	190	69	U-MOSVI		

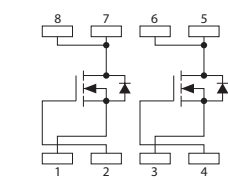
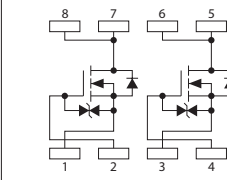
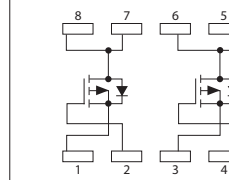
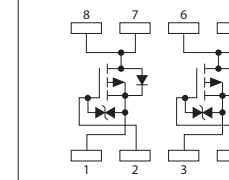
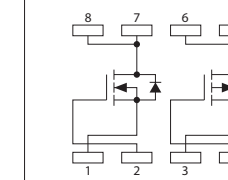
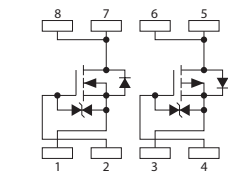


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- 内部接続図はイメージ図です。

(Dual Channel / Complementary) / (デュアルチャネル / コンプリメンタリ)

Package	Polarity	Part Number	Absolute Maximum Ratings				Rds(ON) max (mΩ)					Ciss typ. (pF)	Crss typ. (pF)	Coss typ. (pF)	Qg typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)		
			V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)	V _{GS} = 10 V	V _{GS} = 6 V	V _{GS} = 4.5 V	V _{GS} = 2.5 V	V _{GS} = 1.8 V									
 (mm)	P-ch x 2	TPCF8305	-20	±12	-4	1.35	—	—	58	83	265	680	85	108	9.2	U-MOSVI	(8aa)			
		TPCF8306	-30	+20/-25	-3.2	1.35	72	—	120	—	—	390	65	85	10	U-MOSVI				
 (mm)	N-ch x 2	TPCP8206	20	±12	6	1.48 (1)	—	—	24	35	—	630	47	144	5.8	U-MOSVII	(8AA)			
		TPCP8204	30	±20	4.2	1.48 (1)	50	—	77	—	—	190	45	65	4.6	U-MOSIV				
		TPCP8207	40	±20	5	1.77 (1)	36.3	62.8	—	—	—	505	66	115	11.8	U-MOSIV				
	P-ch x 2	TPCP8303	—	±8	-3.8	1.48 (1)	—	—	46	60	90	640	100	140	10	U-MOSV	(8bb)			
		TPCP8306	-20	±12	-4	1.48 (1)	—	—	58	83	265	680	85	108	9.2	U-MOSVI			(8aa)	
		TPCP8305	—	±12	-6	1.48 (1)	—	—	30	42	—	1500	215	250	21.5	U-MOSVI				
	N-ch + P-ch	TPCP8404	30	±20	4	1.48 (1)	50	—	80	—	—	190	45	60	4.6	U-MOSIV	(8Aa)			
			-30	±20	-4	1.48 (1)	50	—	80	—	—	510	110	170	13	U-MOSV				
		TPCP8405	30	±20	6.5	1.48 (1)	26	—	29	—	—	830	53	177	13.8	U-MOSVI-H	(8Aa)			
			-30	±20	-6	1.48 (1)	31.3	—	42	—	—	1075	190	234	24.1	U-MOSVI				
		TPCP8407	40	±20	5	1.77 (1)	36.3	62.8	—	—	—	505	66	115	11.8	U-MOSIV	(8Bb)			
			-40	+10/-20	-4	1.77 (1)	56.8	82.2	—	—	—	810	85	130	18	U-MOSVI				
TPCP8406	40	±20	6	1.48 (1)	32	—	36	—	—	850	40	142	13.7	U-MOSVI-H	(8Aa)					
	-40	±20	-5	1.48 (1)	43.2	—	53.4	—	—	1105	133	166	24.2	U-MOSVI						
 (mm)	N-ch + P-ch	TPC8407	30	±20	9	1.5	17	—	21	—	—	1190	55	210	17	U-MOSVII-H	(8Aa)			
			-30	±20	-7.4	1.5	23	—	29	—	—	1650	260	300	39	U-MOSVI				
		TPC8408	40	±20	6.1	1.5	32	—	36	—	—	850	40	145	14	U-MOSVI-H				
			-40	±20	-5.3	1.5	43	—	53	—	—	1105	135	165	24	U-MOSVI				

Note (1): Device mounted on a glass board. t = 5 seconds. / ガラスエポキシ基板。t = 5 秒。

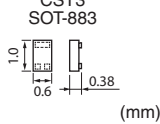
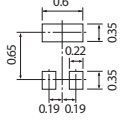
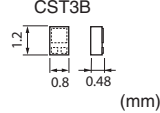
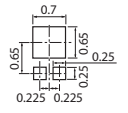
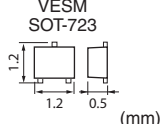
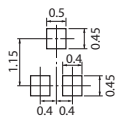
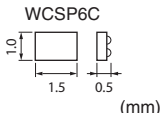
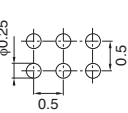
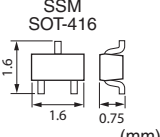
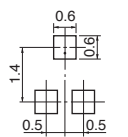
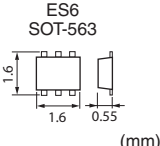
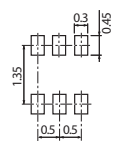
Internal Connections 内部接続図 (Top View)				
(8AA)	(8BB)	(8aa)	(8bb)	(8Aa)
 Nch x 2	 Nch x 2	 Pch x 2	 Pch x 2	 Nch + Pch
 Nch + Pch				

- The internal connection diagrams only show the general configurations of the circuits.
- 内部接続図はイメージ図です。

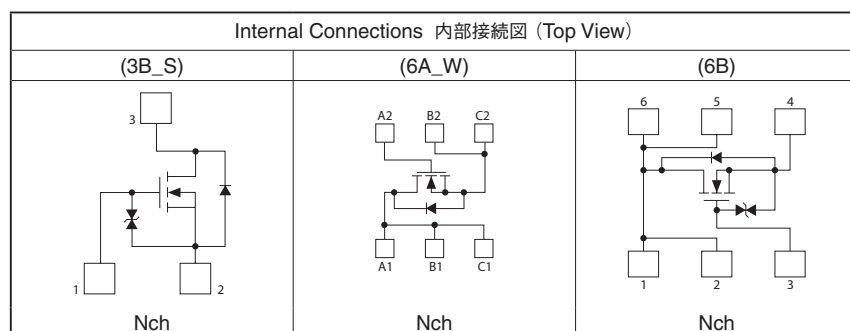
Small-Package Series / 小型パッケージシリーズ

(Semi-Power Type : Single N-Channel) / (セミパワータイプ : シングルNチャネル)

(1/2)

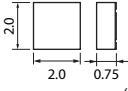
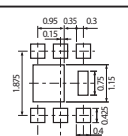
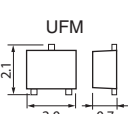
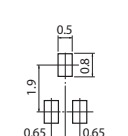
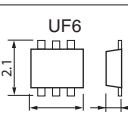
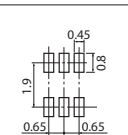
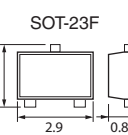
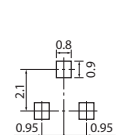
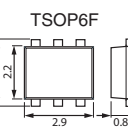
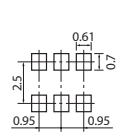
Package	Part Number	Absolute Maximum Ratings				R _{DS(ON)} max (mΩ)						C _{iss} typ. (pF)	C _{rss} typ. (pF)	C _{oss} typ. (pF)	Q _g typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)	V _{GS} = 10 V	V _{GS} = 4.5 V	V _{GS} = 4 V	V _{GS} = 2.5 V	V _{GS} = 1.8 V	V _{GS} = 1.5 V							
 (mm)	SSM3K56CT	20	±8	0.8	0.5	—	235	—	300	480	840	55	6	16	1	U-MOSVII-H	(3B_S)	 (mm)
	SSM3K56ACT		±8	1.4	0.5	—	235	—	300	480	840	55	6	16	1	U-MOSVII-H		
 (mm)	SSM3K59CTB *	40	±12	2	1	—	228	—	268	420	—	130	7.5	26	1.1	U-MOSVII-H	(3B_S)	 (mm)
 (mm)	SSM3K56MFV	20	±8	0.8	0.5	—	235	—	300	480	840	55	6	16	1	U-MOSVII-H	(3B_S)	 (mm)
 (mm)	SSM6K781G *	12	±8	7	1.6	—	18	—	23.2	47.4	124	600	120	250	5.4	U-MOSVII-H	(6A_W)	 (mm)
 (mm)	SSM3K56FS *	20	±8	0.8	0.5	—	235	—	300	480	840	55	6	16	1	U-MOSVII-H	(3B_S)	 (mm)
 (mm)	SSM6K204FE	20	±10	2	0.5	—	—	126	164	214	307	195	29	35	3.4	U-MOSIII	(6B)	 (mm)
	SSM6K211FE		±10	3.2	0.5	—	47	—	59	82	118	510	85	98	10.8	U-MOSIII		
	SSM6K208FE	30	±12	1.9	0.5	—	—	133	177	296	—	123	18	43	1.9	U-MOSIII		
	SSM6K202FE		±12	2.3	0.5	—	—	85	101	145	—	270	47	56	—	U-MOSIII		
	SSM6K217FE	40	±12	1.8	0.5	—	208	—	248	400	—	130	7.5	26	1.1	U-MOSVII-H		

*: New Product / 新製品



• The internal connection diagrams only show the general configurations of the circuits.

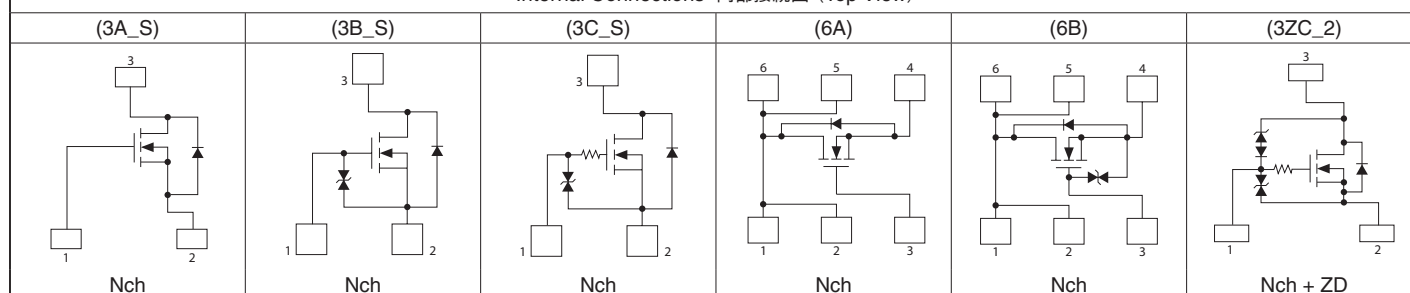
• 内部接続図はイメージ図です。

Package	Part Number	Absolute Maximum Ratings				R _{DS(ON)} max (mΩ)						C _{iss} typ. (pF)	C _{rss} typ. (pF)	C _{oss} typ. (pF)	Q _g typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)	V _{GS} = 10 V	V _{GS} = 4.5 V	V _{GS} = 4 V	V _{GS} = 2.5 V	V _{GS} = 1.8 V	V _{GS} = 1.5 V							
 UDFN6B (mm)	SSM6K504NU	30	±20	9	1.25	19.5	26	—	—	—	—	620	42	110	4.8	U-MOSVII-H	(6B)	
	SSM6K513NU *		±20	15	1.25	8.9	12	—	—	—	—	1130	52	350	7.5	U-MOSIX-H	(6A)	
	SSM6K514NU *	40	±20	12	1.25	11.6	17.3	—	—	—	—	1110	26	245	7.5	U-MOSIX-H	(6B)	
	SSM6K341NU *	60	±20	6	1.25	36	51	69	—	—	—	550	35	300	9.3	U-MOSVIII-H	(6B)	
	SSM6K361NU *	100	±20	3.5	1.25	69	92	—	—	—	—	430	22	160	3.2	U-MOSVIII-H	(6B)	
 UFM (mm)	SSM3K62TU *	20	±8	0.8	0.5	—	57	—	68	89	139	177	17	52	2	U-MOSVII-H	(3C_S)	
	SSM3K122TU		±10	2	0.5	—	—	123	161	211	304	195	29	35	3.4	U-MOSIII	(3B_S)	
	SSM3K121TU		±10	3.2	0.5	—	—	48	63	93	140	400	60	68	5.9	U-MOSIII	(3B_S)	
	SSM3K123TU		±10	4.2	0.5	—	—	28	32	43	66	1010	150	162	13.6	U-MOSIII	(3B_S)	
	SSM3K127TU	30	±12	2	0.5	—	—	123	167	286	—	123	18	43	1.5	U-MOSIII	(3A_S)	
	SSM3K116TU		±12	2.2	0.5	—	100	—	135	—	—	245	33	41	—	U-MOSIII	(3A_S)	
	SSM3K119TU		±12	2.5	0.5	—	—	74	90	134	—	270	47	56	—	U-MOSIII	(3A_S)	
	SSM3K131TU	60	±20	6	0.5	27.6	41.5	—	—	—	—	450	77	120	10.1	U-MOSIV	(3A_S)	
	SSM3K2615TU *		±20	2	0.8	300	—	440	—	—	—	150	25	70	6	π-MOSV	(3C_S)	
	SSM3K341TU *		±20	6	1	36	51	69	—	—	—	550	35	300	9.3	U-MOSVIII-H	(3B_S)	
 UF6 (mm)	SSM6K403TU	20	±10	4.2	0.5	—	—	28	32	43	66	1050	160	175	16.8	U-MOSIII	(6B)	
	SSM6K404TU		±10	3	0.5	—	—	55	70	100	147	400	60	68	5.9	U-MOSIII	(6B)	
	SSM6K405TU		±10	2	0.5	—	—	126	164	214	307	195	29	35	3.4	U-MOSIII	(6B)	
	SSM6K406TU	30	±20	4.4	0.5	25	38.5	—	—	—	—	490	105	143	12.4	U-MOSIV	(6B)	
	SSM6K407TU	60	±20	2	0.5	300	—	440	—	—	—	150	25	70	6	π-MOSV	(6B)	
 SOT-23F (mm)	SSM3K344R *	20	±8	3	1	—	71	—	91	139	232	153	15	37	2	U-MOSVII-H	(3B_S)	
	SSM3K345R *		±8	4	1	—	33	—	45	74	108	410	40	85	3.6	U-MOSVI	(3B_S)	
	SSM3K336R *	30	±20	3	1	95	140	—	—	—	—	126	8	26	1.7	U-MOSVII-H	(3B_S)	
	SSM3K329R		±12	3.5	1	—	—	126	170	289	—	123	18	43	1.5	U-MOSIII	(3B_S)	
	SSM3K324R		±12	4	1	—	56	—	72	109	—	200	13	40	2.2	U-MOSVII-H	(3B_S)	
	SSM3K333R		±20	6	1	28	42	—	—	—	—	436	28	77	3.4	U-MOSVII-H	(3A_S)	
	SSM3K335R	38	±20	6	1	38	56	—	—	—	—	340	20	60	2.7	U-MOSVII-H	(3B_S)	
	SSM3K337R *		±20	2	1	150	176	200	—	—	—	120	7.2	33	3	U-MOSIV	(3ZC_2)	
	SSM3K339R *	40	±12	2	1	—	198	—	238	390	—	130	7.5	26	1.1	U-MOSVII-H	(3B_S)	
	SSM3K2615R	60	±20	2	1	300	—	440	—	—	—	150	25	70	6	π-MOSV	(3C_S)	
	SSM3K318R		±20	2.5	1	107	145	—	—	—	—	235	23	31	7	U-MOSIV	(3B_S)	
	SSM3K341R *		±20	6	1.2	36	51	69	—	—	—	550	35	300	9.3	U-MOSVIII-H	(3B_S)	
 TSOP6F (mm)	SSM6K809R **	60	±20	6	1.5	36	51	69	—	—	—	550	35	300	9.3	U-MOSVIII-H	(6B)	
	SSM6K810R **	100	±20	3.5	1.5	69	92	—	—	—	—	430	22	160	3.2	U-MOSVIII-H	(6B)	

*: New Product / 新製品

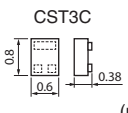
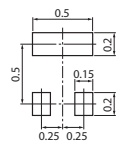
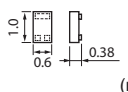
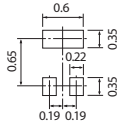
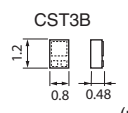
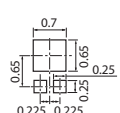
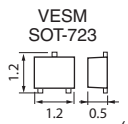
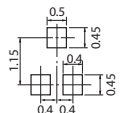
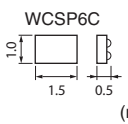
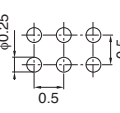
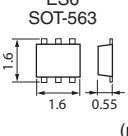
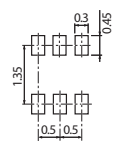
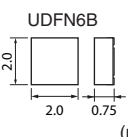
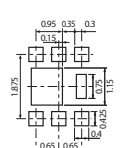
**: Under Development / 開発中

Internal Connections 内部接続図 (Top View)

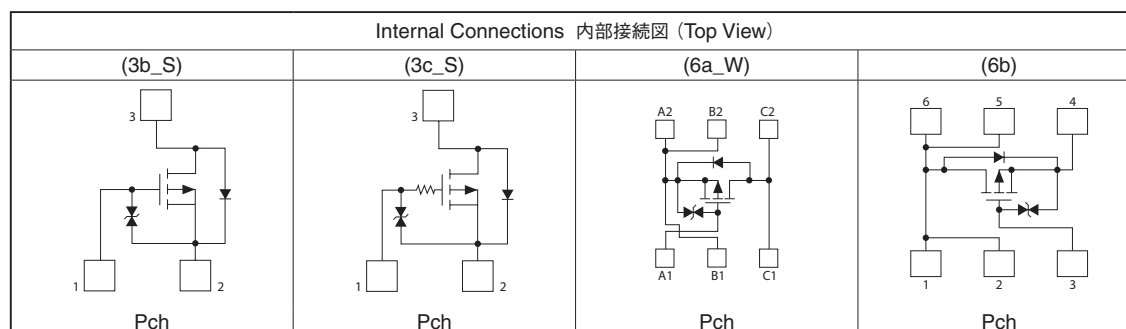


• The internal connection diagrams only show the general configurations of the circuits.

• 内部接続図はイメージ図です。

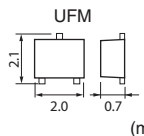
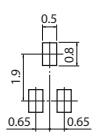
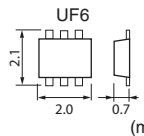
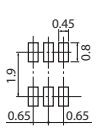
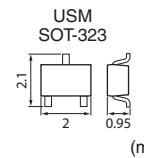
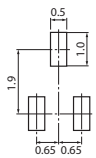
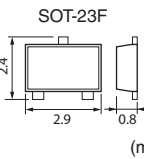
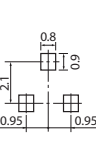
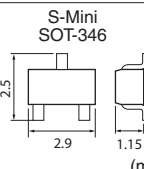
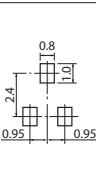
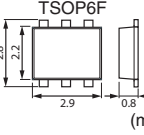
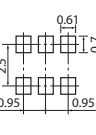
Package	Part Number	Absolute Maximum Ratings				R _{DS(ON)} max (mΩ)					C _{iss} typ. (pF)	C _{rss} typ. (pF)	C _{oss} typ. (pF)	Q _g typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)	V _{GS} = 4.5 V	V _{GS} = 4 V	V _{GS} = 2.5 V	V _{GS} = 1.8 V	V _{GS} = 1.5 V							
 CST3C (mm)	SSM3J64CTC *	-12	±10	-1	0.5	370	—	560	890	1310	50	7.5	12	—	U-MOSVII	(3c_S)	
	SSM3J65CTC *	-20	±10	-0.7	0.5	500	—	700	1070	1550	48	4.6	8.9	—	U-MOSVII		
 CST3 SOT-883 (mm)	SSM3J56ACT	-20	±8	-1.4	0.5	390	—	480	660	900	100	10	16	1.6	U-MOSVI	(3c_S)	
 CST3B (mm)	SSM3J46CTB	-20	±8	-2	1	103	—	133	178	250	290	32	44	4.7	U-MOSVI	(3b_S)	
 VESM SOT-723 (mm)	SSM3J56MFV	-20	±8	-0.8	0.5	390	—	480	660	900	100	10	16	1.6	U-MOSVI	(3b_S)	
 WCSP6C (mm)	SSM6J771G	-20	±12	-5	1.6	35	—	47.5	—	—	870	120	150	9.8	U-MOSVI	(6a_W)	
 ES6 SOT-563 (mm)	SSM6J216FE	-12	±8	-4.8	0.5	32	—	39.3	56	88.1	1040	180	200	12.7	U-MOSVI	(6b)	
	SSM6J213FE	—	±8	-2.6	0.5	103	—	133	178	250	290	32	44	4.7	U-MOSVI		
	SSM6J215FE	-20	±8	-3.4	0.5	59	—	79	104	154	630	60	75	10.4	U-MOSVI		
	SSM6J212FE	—	±8	-4	0.5	40.7	—	49	65.4	94	970	109	127	14.1	U-MOSVI		
	SSM6J207FE	—	±20	-1.4	0.5	—	491	—	—	—	137	20	39	—	U-MOSII		
 UDFN6B (mm)	SSM6J214FE	-30	±12	-3.6	0.5	57	—	77.6	149.6	—	560	65	80	7.9	U-MOSVI	(6b)	
	SSM6J512NU *	—	±10	-10	1.25	18.7	—	25.7	40.1	—	1400	225	250	19.5	U-MOSVII		
	SSM6J505NU	-12	±6	-12	1.25	12	—	16	21	30	2700	800	800	37.6	U-MOSVI		
	SSM6J511NU *	—	±10	-14	1.25	10	—	13.5	19.2	—	3350	570	590	47	U-MOSVII		
	SSM6J502NU	—	±8	-6	1	23.1	—	28.3	38.4	60.5	1800	190	205	24.8	U-MOSVI		
	SSM6J503NU	-20	±8	-6	1	32.4	—	41.7	57.9	89.6	840	99	118	12.8	U-MOSVI		
	SSM6J501NU	—	±8	-10	1	15.3	—	19	26.5	43	2600	280	290	29.9	U-MOSVI		
	SSM6J507NU *	-30	+20/-25	-10	1.25	28	32	—	—	—	1150	185	210	13.6	U-MOSVI		

*: New Product / 新製品



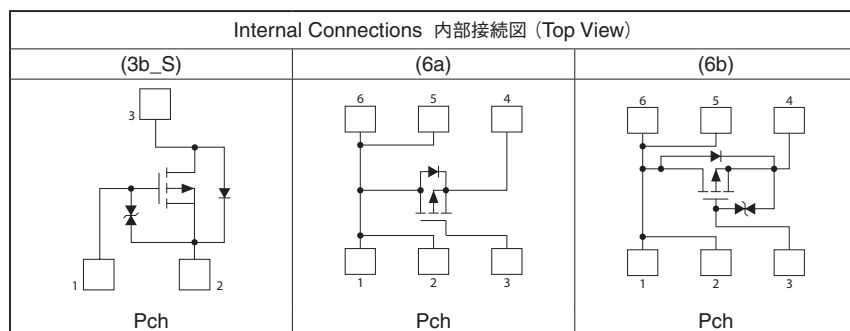
• The internal connection diagrams only show the general configurations of the circuits.

• 内部接続図はイメージ図です。

Package	Part Number	Absolute Maximum Ratings				R _{DS(ON)} max (mΩ)					C _{iss} typ. (pF)	C _{rss} typ. (pF)	C _{oss} typ. (pF)	Q _g typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)	V _{GS} = 4.5 V	V _{GS} = 4 V	V _{GS} = 2.5 V	V _{GS} = 1.8 V	V _{GS} = 1.5 V							
 (mm)	SSM3J132TU	-12	±6	-5.4	0.5	17	—	21	29	39	2700	525	525	33	U-MOSVI	(3b_S)	
	SSM3J135TU	—	±8	-3	0.5	103	—	132	180	260	270	32	40	4.6	U-MOSVI		
	SSM3J134TU	—	±8	-3.2	0.5	93	—	123	168	240	290	32	44	4.7	U-MOSVI		
	SSM3J130TU	—	±8	-4.4	0.5	25.8	—	31	41.1	63.2	1800	190	205	24.8	U-MOSVI		
	SSM3J133TU	—	±8	-5.5	0.5	29.8	—	39.7	56	88.4	840	99	118	12.8	U-MOSVI		
 (mm)	SSM6J50TU	—	±10	-2.5	0.5	64	—	100	—	—	800	120	160	—	U-MOSIV	(6b)	
	SSM6J412TU	-20	±8	-4	1	42.7	—	51.4	67.8	99.6	840	99	118	12.8	U-MOSVI		
	SSM6J414TU	—	±8	-6	1	22.5	—	26	36	54	1650	90	220	23.1	U-MOSVI		
	SSM6J402TU	—	±20	-2	0.5	—	225	—	—	—	280	45	80	5.3	U-MOSII		
	SSM6J410TU	-30	±20	-2.1	0.5	—	393	—	—	—	120	21	32	2.9	U-MOSIII		
	SSM6J401TU	—	±20	-2.5	0.5	—	145	—	—	—	730	90	110	16	U-MOSIII		
 (mm)	SSM3J112TU	—	±20	-1.1	0.5	—	790	—	—	—	86	14	25	—	U-MOSII	(3b_S)	
	SSM3J118TU	-30	±20	-1.4	0.5	—	480	—	—	—	137	20	39	—	U-MOSII		
	SSM3J117TU	—	±20	-2	0.5	—	225	—	—	—	280	45	80	—	U-MOSII		
 (mm)	SSM3J338R	-12	±10	-6	1	20.2	—	27.9	45.3	—	1400	225	250	19.5	U-MOSVII	(3b_S)	
	SSM3J327R	—	±8	-3.9	1	93	—	123	168	240	290	32	44	4.6	U-MOSVI		
	SSM3J331R	—	±8	-4	1	55	—	75	100	150	630	60	75	10.4	U-MOSVI		
	SSM3J328R	-20	±8	-6	1	29.8	—	39.7	56	88.4	840	99	118	12.8	U-MOSVI		
	SSM3J355R	*	±10	-6	1	30.1	—	38.8	52.3	—	1030	94	113	16.6	U-MOSVII		
	SSM3J358R	*	±10	-6	1	25.3	—	32.8	49.3	—	1331	118	135	38.5	U-MOSVII		
	SSM3J334R	—	±20	-4	1	105	136	—	—	—	280	40	55	5.9	U-MOSVI		
	SSM3J340R	-30	+20/-25	-4	1	73	86	—	—	—	492	75	97	6.2	U-MOSVI		
	SSM3J332R	—	±12	-6	1	50	—	72	144	—	560	65	80	8.2	U-MOSVI		
	SSM3J356R	*	+10/-20	-2	1	360	400	—	—	—	330	25	40	8.3	U-MOSVI		
	SSM3J351R	*	+10/-20	-3.5	1	164	184	—	—	—	660	50	70	15.1	U-MOSVI		
 (mm)	SSM3J325F	—	±8	-2	0.6	150	—	179	231	311	270	32	40	4.6	U-MOSVI	(3b_S)	
	SSM3J352F	*	±12	-2	0.6	136	—	199	443	—	210	31	39	5.1	U-MOSVI		
	SSM3J353F	*	+20/-25	-2	0.6	232	274	—	—	—	159	23	30	3.4	U-MOSVI		
 (mm)	SSM6J801R	*	-20	+6/-8	-6	1.5	32.5	—	39.7	56	840	99	118	12.8	U-MOSVI	(6b)	
	SSM6J808R	**	-40	+10/-20	-7	1.5	54	—	—	—	1105	133	166	24.2	U-MOSVI	(6a)	

*: New Product / 新製品

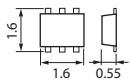
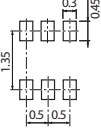
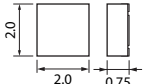
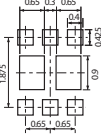
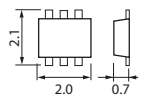
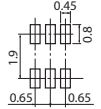
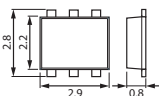
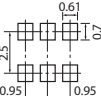
**: Under Development / 開発中



• The internal connection diagrams only show the general configurations of the circuits.

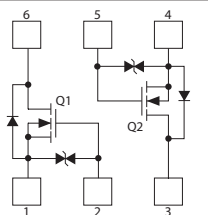
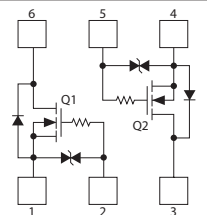
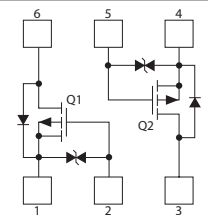
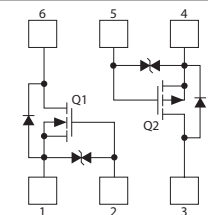
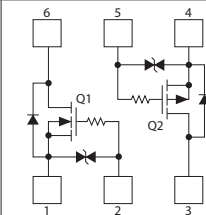
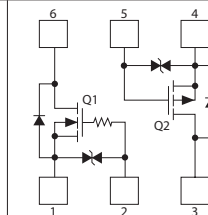
• 内部接続図はイメージ図です。

(Semi-Power Type: Dual Channel/Complementary) / (セミパワータイプ:デュアルチャネル/コンプリメンタリ)

Package	Polarity	Part Number	Absolute Maximum Ratings				R _{DS(ON)} max (mΩ)					C _{iss} typ. (pF)	C _{rss} typ. (pF)	C _{oss} typ. (pF)	Q _g typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)	
			V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)	V _{GS1} = 4.5 V	V _{GS1} = 4 V	V _{GS1} = 2.5 V	V _{GS1} = 1.8 V	V _{GS1} = 1.5 V								
ES6 SOT-563  (mm)	N-ch x 2	SSM6N56FE	20	±8	0.8	0.25	235	—	300	480	840	55	6	16	1	U-MOSVII-H	(6BB)		
	P-ch x 2	SSM6P41FE	−20	±8	−0.72	0.15	300	—	440	670	1040	110	20	28	1.76	U-MOSV	(6bb)		
	N-ch + P-ch	SSM6L14FE	20	±10	0.8	0.15	240	—	330	450	600	90	15	21	2	U-MOSIII	(6Cb)		
			−20	±8	−0.72	0.15	300	—	440	670	1040	110	20	28	1.76	U-MOSV			
UDFN6 SOT-1118  (mm)	N-ch x 2	SSM6N61NU	*	20	±8	4	1	33	—	45	74	108	410	40	85	3.6	U-MOSVII-H	(6BB)	
		SSM6N55NU			±20	4	1	64	—	—	—	—	280	20	53	2.5	U-MOSVII-H		
		SSM6N57NU	30		±12	4	1	39.1	—	53	82	—	310	20	52	3.2	U-MOSVII-H		
		SSM6N58NU		±12	4	1	84	—	117	180	—	129	13	34	1.8	U-MOSVII-H			
	P-ch x 2	SSM6P47NU		−20	±8	−4	1	95	—	125	170	242	290	32	44	4.6	U-MOSVI	(6bb)	
		SSM6P49NU		±12	−4	1	56	—	76	157	—	480	76	90	6.74	U-MOSVI			
	N-ch + P-ch	SSM6L61NU	20	±8	4	1	—	33	45	74	108	410	40	85	3.6	U-MOSVII-H	(6Bb)		
			−20	±12	−4	1	56	—	76	157	—	480	76	90	6.74	U-MOSVI			
		SSM6L63NU	30	±20	4	1	48 (typ.)	—	—	—	—	280	20	53	2.5	U-MOSVII-H	(6Cc)		
			−30	±20	−4	1	80 (typ.)	—	—	—	—	280	40	55	5.9	U-MOSVII-H			
UF6  (mm)	N-ch x 2	SSM6N62TU		20	±8	0.8	0.5	85	—	98	120	173	177	17	52	2	U-MOSVII-H	(6BB)	
		SSM6N39TU		±10	1.6	0.5	—	119	139	190	247	260	37	45	7.5	U-MOSIII			
		SSM6N40TU	30	±20	1.6	0.5	—	182	—	—	—	180	27	34	5.1	U-MOSIII			
	P-ch x 2	SSM6P54TU		−20	±8	−1.2	0.5	—	—	228	350	555	331	39	48	7.7	U-MOSIV	(6bb)	
		SSM6P39TU		±8	−1.5	0.5	—	213	294	430	—	250	35	43	6.4	U-MOSIII			
		SSM6P40TU	−30	±20	−1.4	0.5	—	403	—	—	—	120	21	32	2.9	U-MOSIII			
	N-ch + P-ch	SSM6L39TU	20	±10	1.6	0.5	—	119	139	190	247	260	37	45	7.5	U-MOSIII	(6Bb)		
			−20	±8	−1.5	0.5	—	213	294	430	—	250	35	43	6.4	U-MOSIII			
		SSM6L12TU	30	±12	0.5	0.5	145	—	180	—	—	245	33	41	—	U-MOSIII	(6Cc)		
			−20	±12	−0.5	0.5	—	260	430	—	—	218	42	52	—	U-MOSIII			
		SSM6L40TU	30	±20	1.6	0.5	—	182	—	—	—	180	27	34	5.1	U-MOSIII	(6Bb)		
			−30	±20	−1.4	0.5	—	403	—	—	—	120	21	32	2.9	U-MOSIII			
TSOP6F  (mm)	N-ch x 2	SSM6N813R	*	100	±20	3.5	1.5	154	—	—	—	—	242	7	106	3.6	U-MOSVIII-H	(6CC)	
		SSM6N815R	*		±20	2	1.4	142	180	—	—	—	290	16	108	3.1	U-MOSVIII-H	(6BB)	

*: New Product / 新製品

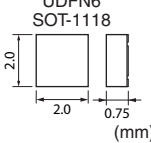
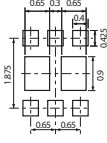
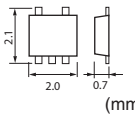
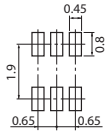
**: Under Development / 開発中

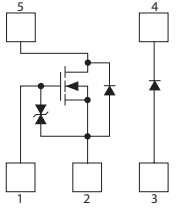
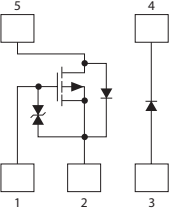
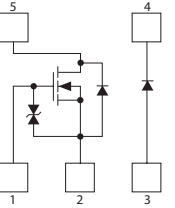
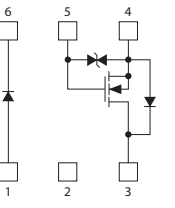
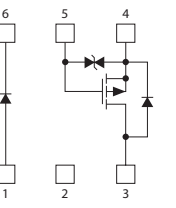
Internal Connections 内部接続図 (Top View)					
(6BB)	(6CC)	(6bb)	(6Bb)	(6Cc)	(6Cb)
 Nch x 2	 Nch x 2	 Pch x 2	 Nch + Pch	 Nch + Pch	 Nch + Pch

• The internal connection diagrams only show the general configurations of the circuits.

• 内部接続図はイメージ図です。

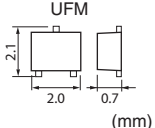
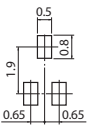
(Semi-Power Type: Built-in Diode) / (セミパワータイプ: ダイオード混載品)

Package	Polarity	Part Number	Absolute Maximum Ratings				R _{DS(ON)} max (mΩ)					C _{iss} typ. (pF)	C _{rss} typ. (pF)	C _{oss} typ. (pF)	Q _g typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)	
			V _{DS} (V)	V _{GS} (V)	I _D (A)	P _D (W)	V _{GS} = 4.5 V	V _{GS} = 4 V	V _{GS} = 2.5 V	V _{GS} = 1.8 V	V _{GS} = 1.5 V								
 UDFN6 SOT-1118 (mm)	N-ch + SBD	SSM6H19NU	40	±12	2	1	198	—	238	390	—	130	7.5	26	1.1	U-MOSVII-H	(6SB)		
	P-ch + SBD	SSM6G18NU	−20	±8	−2	1	112	—	143	185	261	270	32	40	4.6	U-MOSVI	(6Sb)		
 UFV (mm)	N-ch + SBD	SSM5H08TU	20	±12	1.5	0.5	—	160	220	—	—	125	17	42	—	U-MOSIII	(5BS)		
		SSM5H01TU		±20	1.4	0.5	—	450	—	—	—	106	15	28	—	U-MOSIII			
		SSM5H11TU	30	±20	1.6	0.5	—	182	—	—	—	180	27	34	5.1	U-MOSIII			
		SSM5H16TU		±12	1.9	0.5	—	133	177	296	—	123	18	43	1.9	U-MOSIII			
	P-ch + SBD	SSM5G02TU	−12	±12	−1	0.5	—	160	240	—	—	310	70	110	—	U-MOSII	(5bS)		
		SSM5G09TU		±8	−1.5	0.5	—	130	200	—	—	550	155	170	—	U-MOSIII			
		SSM5G11TU	−30	±20	−1.4	0.5	—	403	—	—	—	120	21	32	2.9	U-MOSIII			
	N-ch + Switching Diode	SSM5H90ATU	20	±10	2.4	0.5	—	65	89	—	—	200	13	40	2.2	U-MOSVII-H	(5BW)		

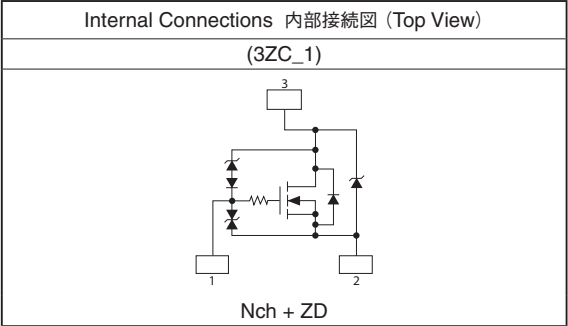
Internal Connections 内部接続図 (Top View)				
(5BS)	(5bS)	(5BW)	(6SB)	(6Sb)
 Nch + SBD	 Pch + SBD	 Nch + Switching Diode	 Nch + SBD	 Pch + SBD

- The internal connection diagrams only show the general configurations of the circuits.
- 内部接続図はイメージ図です。

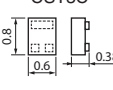
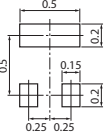
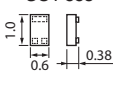
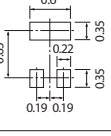
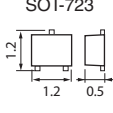
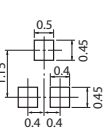
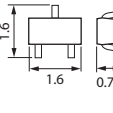
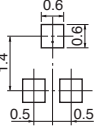
(Semi-Power Type: Built-in Zener Diode) / (セミパワータイプ: ZD 混載品)

Package	Polarity	Part Number	Absolute Maximum Ratings				R _{DS(ON)} max (mΩ)					C _{iss} typ. (pF)	C _{rss} typ. (pF)	C _{oss} typ. (pF)	Q _g typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)
			V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)	V _{GS1} = 4.5 V	V _{GS1} = 4 V	V _{GS1} = 2.5 V	V _{GS1} = 1.8 V	V _{GS1} = 1.5 V							
 (mm)	N-ch + Zener	SSM3H137TU	34	±20	2	0.8	280	295	—	—	—	119	8	40	3	U-MOSIV	(3ZC_1)	

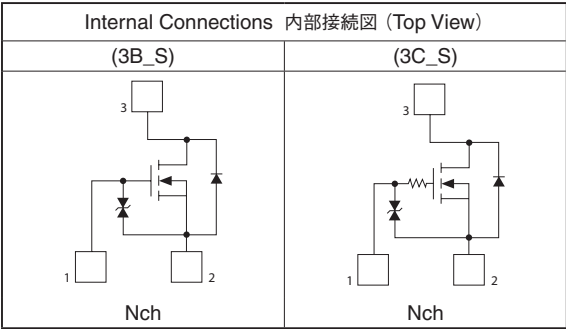
*: New Product / 新製品



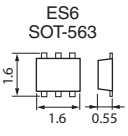
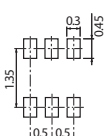
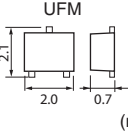
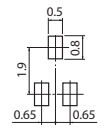
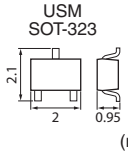
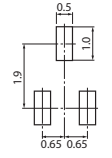
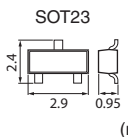
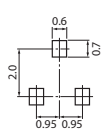
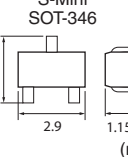
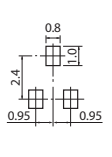
- The internal connection diagrams only show the general configurations of the circuits.
- 内部接続図はイメージ図です。

Package	Part Number	Absolute Maximum Ratings				R _{DS(ON)} max (Ω)					C _{iss} typ. (pF)	C _{rss} typ. (pF)	C _{oss} typ. (pF)	Q _g typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)	
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)	V _{GS} = 4.5 V	V _{GS} = 4 V	V _{GS} = 2.5 V	V _{GS} = 1.8 V	V _{GS} = 1.5 V								
CST3C  (mm)	SSM3K16CTC *	20	±10	0.2	0.5	2.2	—	3	4	5.6	12	4.1	5.5	—	U-MOSIII	(3C_S)		
	SSM3K35CTC		±10	0.25	0.5	1.1	—	1.6	2.4	3.1	18	5	6	0.34	U-MOSIII			
	SSM3K15ACTC *	30	±20	0.1	0.5	—	3.6	6	—	—	13.5	6.5	8	—	U-MOSIII			
	SSM3K72CTC *	60	±20	0.15	0.5	4.7	—	—	—	—	11	0.7	3	0.27	U-MOSVII-H			
CST3 SOT-883  (mm)	SSM3K16CT	20	±10	0.1	0.1	—	3	4	—	15	9.3	4.5	9.8	—	π-MOSVI	(3C_S)		
	SSM3K35CT		±10	0.18	0.1	—	3	4	—	8	9.5	4.1	9.5	—	π-MOSVI			
	SSM3K37CT		±10	0.2	0.1	2.2	—	3.02	4.05	5.6	12	4.1	5.5	—	U-MOSIII			
	SSM3K15ACT	30	±20	0.1	0.1	—	3.6	6	—	—	13.5	6.5	8	—	U-MOSIII			
	SSM3K72KCT *	60	±20	0.4	0.5	1.75	—	—	—	—	26	1.3	5.5	0.39	U-MOSVII-H			
VESM SOT-723  (mm)	SSM3K16FV	20	±10	0.1	0.15	—	3	4	—	15	9.3	4.5	9.8	—	π-MOSVI	(3C_S)		
	SSM3K35MFV		±10	0.18	0.15	—	3	4	—	8	9.5	4.1	9.5	—	π-MOSVI			
	SSM3K35AMFV *		±10	0.25	0.15	1.1	—	1.6	2.4	3.1	18	5	6	0.34	U-MOSIII			
	SSM3K37MFV		±10	0.25	0.15	2.2	—	3.02	4.05	5.6	12	4.1	5.5	—	U-MOSIII			
	SSM3K36MFV		±10	0.5	0.15	0.66	—	0.85	1.14	1.52	46	7.3	10.8	1.23	U-MOSIII			
	SSM3K56MFV	30	±8	0.8	0.15	0.235	—	0.3	0.48	0.84	55	6	16	1	U-MOSVII-H	(3B_S)		
	SSM3K15AMFV		±20	0.1	0.15	—	3.6	6	—	—	13.5	6.5	8	—	U-MOSIII	(3C_S)		
	SSM3K44MFV		±20	0.1	0.15	—	4	7	—	—	8.5	5.3	9.4	—	π-MOSVI	(3C_S)		
SSM SOT-416  (mm)	SSM3K16FS	20	±10	0.1	0.1	—	3	4	—	15	9.3	4.5	9.8	—	π-MOSVI	(3C_S)		
	SSM3K35FS		±10	0.18	0.1	—	3	4	—	8	9.5	4.1	9.5	—	π-MOSVI			
	SSM3K37FS		±10	0.2	0.1	2.2	—	3.02	4.05	5.6	12	4.1	5.5	—	U-MOSIII			
	SSM3K35AFS *		±10	0.25	0.15	1.1	—	1.6	2.4	3.1	18	5	6	0.34	U-MOSIII			
	SSM3K36FS		±10	0.5	0.15	0.66	—	0.85	1.14	1.52	46	7.3	10.8	1.23	U-MOSIII			
	SSM3K56FS	30	±8	0.8	0.15	0.235	—	0.3	0.48	0.84	55	6	16	1	U-MOSVII-H	(3B_S)		
	SSM3K15AFS		±20	0.1	0.1	—	3.6	6	—	—	13.5	6.5	8	—	U-MOSIII	(3C_S)		
	SSM3K44FS		±20	0.1	0.15	—	4	7	—	—	8.5	5.3	9.4	—	π-MOSVI			
	SSM3K72CFs *	60	±20	0.17	0.15	4.7	—	—	—	—	11	0.7	3	0.27	U-MOSVII-H	(3C_S)		
	SSM3K72KFs *		±20	0.3	0.15	1.75	—	—	—	—	26	1.3	5.5	0.39	U-MOSVII-H			

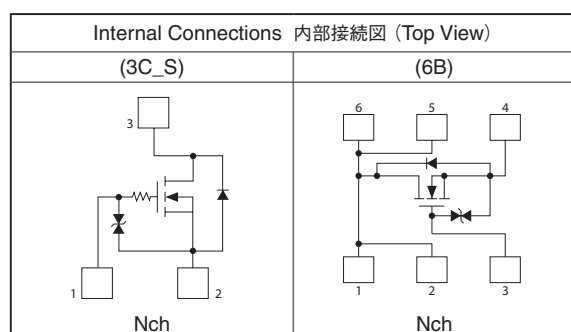
*: New Product / 新製品



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- 内部接続図はイメージ図です。

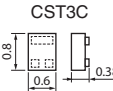
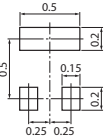
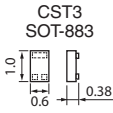
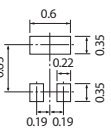
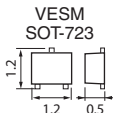
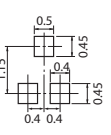
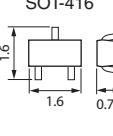
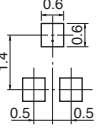
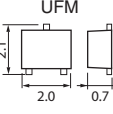
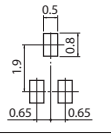
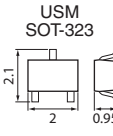
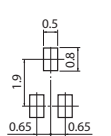
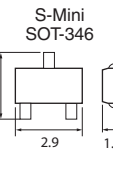
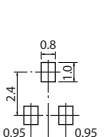
Package	Part Number	Absolute Maximum Ratings				R _{DS(ON)} max (Ω)					C _{iss} typ. (pF)	C _{rss} typ. (pF)	C _{oss} typ. (pF)	Q _g typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)	V _{GS1} = 4.5 V	V _{GS1} = 4 V	V _{GS1} = 2.5 V	V _{GS1} = 1.8 V	V _{GS1} = 1.5 V							
 ES6 SOT-563 (mm)	SSM6K24FE	30	±12	0.5	0.5	0.145	—	0.18	—	—	245	33	41	—	U-MOSIII	(6B)	
 UFM (mm)	SSM3K36TU	20	±10	0.5	0.5	0.66	—	0.85	1.14	1.52	46	7.3	10.8	1.23	U-MOSIII	(3C_S)	
 USM SOT-323 (mm)	SSM3K16FU	20	±10	0.1	0.15	—	3	4	—	15	9.3	4.5	9.8	—	π-MOSVI	(3C_S)	
	SSM3K15AFU	30	±20	0.1	0.15	—	3.6	6	—	—	13.5	6.5	8	—	U-MOSIII		
	SSM3K48FU	30	±20	0.1	0.15	—	3.2	5.4	—	—	15.1	7.8	12.4	—	U-MOSIII		
	SSM3K09FU	30	±20	0.4	0.15	—	1.2	—	—	—	20	7	16	—	π-MOSVI		
	SSM3K17FU	50	±7	0.1	0.15	—	20	40	—	—	7	3	7	—	π-MOSV		
	SSM3K7002CFU	60	±20	0.17	0.15	4.7	—	—	—	—	11	0.7	3	0.27	U-MOSVII-H		
 SOT23 (mm)	T2N7002AK	60	±20	0.2	0.32	4.7	—	—	—	—	11	0.7	3	0.27	U-MOSVII-H	(3C_S)	
	T2N7002BK	60	±20	0.4	0.32	1.75	—	—	—	—	26	1.3	5.5	0.39	U-MOSVII-H		
 S-Mini SOT-346 (mm)	SSM3K15F	30	±20	0.1	0.2	—	4	7	—	—	7.8	3.6	8.8	—	π-MOSVI	(3C_S)	
	SSM3K7002KF	60	±20	0.4	0.27	1.75	—	—	—	—	26	1.3	5.5	0.39	U-MOSVII-H		

*: New Product / 新製品

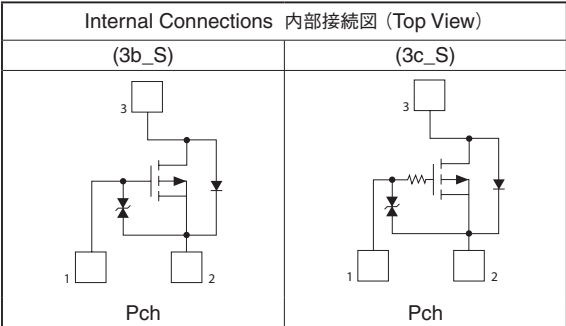


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- 内部接続図はイメージ図です。

(Small-Signal Type: Single P-Channel) / (小信号スタンダードタイプ: シングルPチャネル)

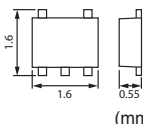
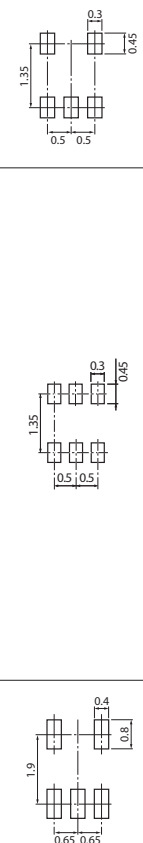
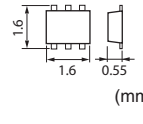
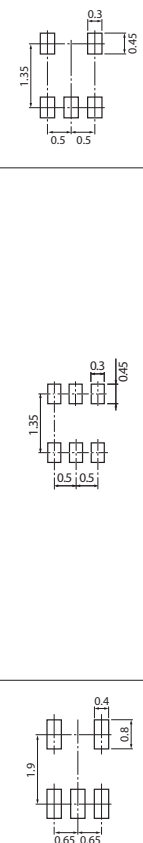
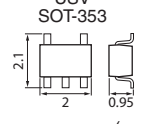
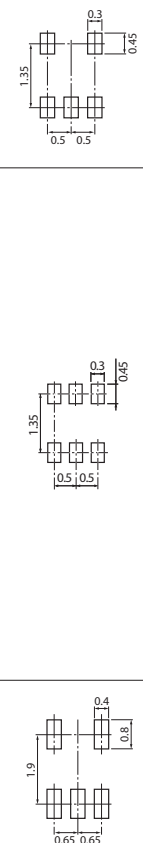
Package	Part Number	Absolute Maximum Ratings				R _{DS(ON)} max (Ω)					C _{iss} typ. (pF)	C _{rss} typ. (pF)	C _{oss} typ. (pF)	Q _g typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)	V _{GS} = 4.5 V	V _{GS} = 4 V	V _{GS} = 2.5 V	V _{GS} = 1.8 V	V _{GS} = 1.5 V							
CST3C  (mm)	SSM3J35CTC *	-20	±10	-0.25	0.5	1.4	—	2.1	2.9	4	21	2	6	—	U-MOSVII	(3c_S)	
CST3 SOT-883  (mm)	SSM3J35CT	-20	±10	-0.1	0.1	—	8	11	—	22	12.2	6.5	10.4	—	π-MOSVI	(3c_S)	
	SSM3J15CT	-30	±20	-0.1	0.1	—	12	32	—	—	9.1	3.5	8.6	—	π-MOSVI		
VESM SOT-723  (mm)	SSM3J16FV	-20	±10	-0.1	0.15	—	8	12	—	45	11	3.7	10	—	π-MOSVI	(3c_S)	
	SSM3J35MFV		±10	-0.1	0.15	—	8	11	—	22	12.2	6.5	10.4	—	π-MOSVI		
	SSM3J35AMFV *		±10	-0.25	0.5	1.4	—	2.1	2.9	4	21	2	6	—	U-MOSVII		
	SSM3J56MFV		±8	-0.8	0.15	0.39	—	0.48	0.66	0.9	100	10	16	1.6	U-MOSVI	(3b_S)	
	SSM3J15FV	-30	±20	-0.1	0.15	—	12	32	—	—	9.1	3.5	8.6	—	π-MOSVI	(3c_S)	
SSM SOT-416  (mm)	SSM3J35FS	-20	±10	-0.1	0.1	—	8	11	—	22	12.2	6.5	10.4	—	π-MOSVI	(3c_S)	
	SSM3J35AFS *		±10	-0.25	0.15	1.4	—	2.1	2.9	4	21	2	6	—	U-MOSVII		
	SSM3J36FS		±8	-0.33	0.15	1.31	—	—	2.7	3.6	43	6.1	10.3	1.2	U-MOSIII		
	SSM3J15FS	-30	±20	-0.1	0.1	—	12	32	—	—	9.1	3.5	8.6	—	π-MOSVI		
UFM  (mm)	SSM3J36TU	-20	±8	-0.33	0.5	1.31	—	—	2.7	3.6	43	6.1	10.3	1.2	U-MOSIII	(3c_S)	
USM SOT-323  (mm)	SSM3J16FU	-20	±10	-0.1	0.15	—	8	12	—	45	11	3.7	10	—	π-MOSVI	(3c_S)	
	SSM3J15FU	-30	±20	-0.1	0.15	—	12	32	—	—	9.1	3.5	8.6	—	π-MOSVI		
	SSM3J09FU		±20	-0.2	0.15	—	4.2	—	—	—	22	5	14	—	π-MOSVI		
S-Mini SOT-346  (mm)	SSM3J15F	-30	±20	-0.1	0.2	—	12	32	—	—	9.1	3.5	8.6	—	π-MOSVI	(3c_S)	
	2SJ168	-60	±20	-0.2	0.2	—	—	—	—	—	73	15	48	—	U-MOSVI	(3b_S)	
	SSM3J168F *		+10/-20	-0.4	0.6	1.9	2	—	—	—	82	5.5	13	3			

*: New Product / 新製品

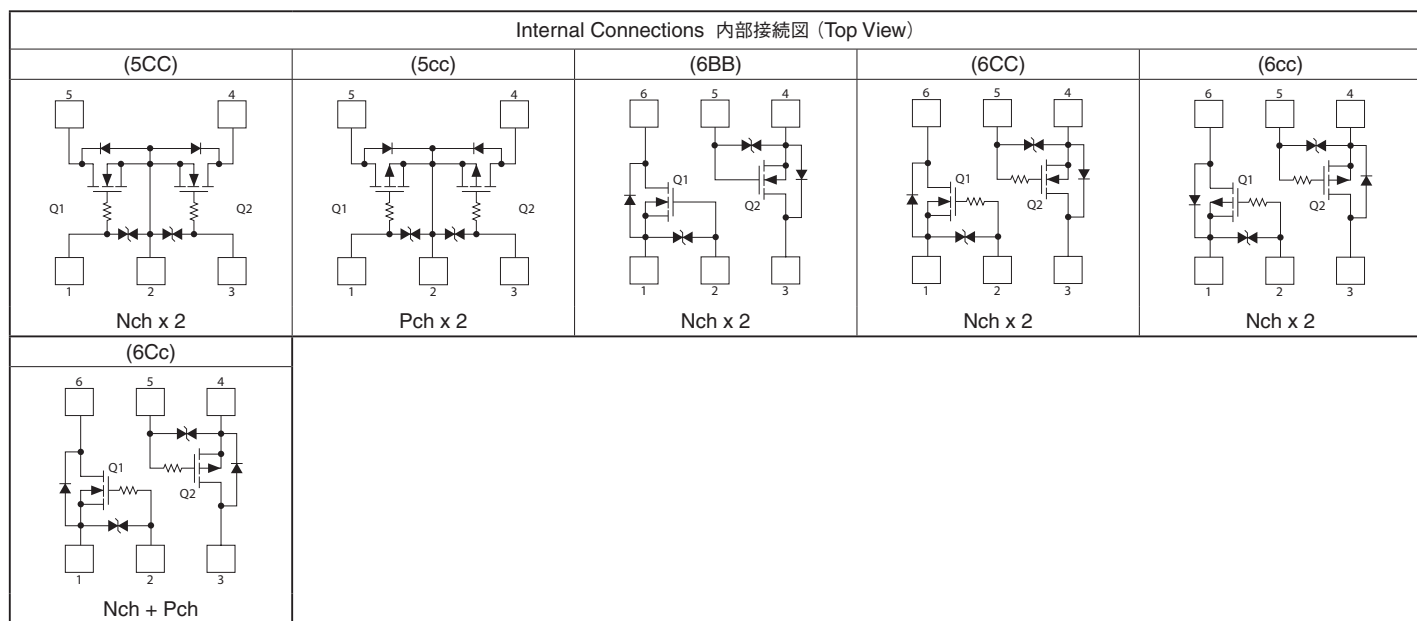


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(Small-Signal Type: Dual Channel/Complementary) / (小信号スタンダードタイプ: デュアルチャネル/コンプリメンタリ) (1/2)

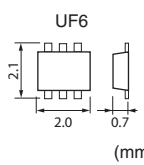
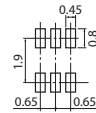
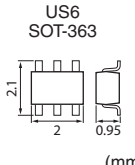
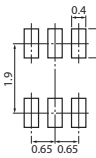
Package	Polarity	Part Number	Absolute Maximum Ratings				R _{DS(ON)} max (Ω)					C _{iss} typ. (pF)	C _{rss} typ. (pF)	C _{oss} typ. (pF)	Q _g typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)	
			V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)	V _{GS} = 4.5 V	V _{GS} = 4 V	V _{GS} = 2.5 V	V _{GS} = 1.8 V	V _{GS} = 1.5 V								
ESV SOT-553  (mm)	N-ch x 2	SSM5N16FE	20	±10	0.1	0.15	—	3	4	—	15	9.3	4.5	9.8	—	π-MOSVI	(5CC)		
		SSM5N15FE	30	±20	0.1	0.15	—	4	7	—	—	7.8	3.6	8.8	—	π-MOSVI			
	P-ch x 2	SSM5P16FE	−20	±10	−0.1	0.15	—	8	12	—	45	11	3.7	10	—	π-MOSVI	(5cc)		
ES6 SOT-563  (mm)	N-ch x 2	SSM6N16FE	20	±10	0.1	0.15	—	3	4	—	15	9.3	4.5	9.8	—	π-MOSVI	(6CC)		
		SSM6N35FE		±10	0.18	0.15	—	3	4	—	8	9.5	4.1	9.5	—	π-MOSVI			
		SSM6N35AFE *		±10	0.25	0.15	1.1	—	1.6	2.4	3.1	18	5	6	0.34	U-MOSIII			
		SSM6N37FE		±10	0.25	0.15	2.2	—	3.02	4.05	5.6	12	4.1	5.5	—	U-MOSIII			
		SSM6N36FE	30	±10	0.5	0.15	0.66	—	0.85	1.14	1.52	46	7.3	10.8	1.23	U-MOSIII	(6BB)		
		SSM6N56FE *		±8	0.8	0.15	0.235	—	0.3	0.48	0.84	55	6	16	1	U-MOSVII-H			
		SSM6N15AFE		±20	0.1	0.15	—	3.6	6	—	—	13.5	6.5	8	—	U-MOSIII	(6CC)		
		SSM6N44FE		±20	0.1	0.15	—	4	7	—	—	8.5	5.3	9.4	—	π-MOSVI			
	P-ch x 2	SSM6N7002BFE	60	±20	0.2	0.15	3.3	—	—	—	—	17	1.9	3.6	—	U-MOSIV	(6cc)		
		SSM6P35FE	−20	±10	−0.1	0.15	—	8	11	—	22	12.2	6.5	10.4	—	π-MOSVI			
		SSM6P35AFE *		±10	−0.25	0.15	1.4	—	2.1	2.9	4	21	2	6	—	U-MOSVII			
		SSM6P36FE		±8	−0.33	0.15	1.31	—	—	2.7	3.6	43	6.1	10.3	1.2	U-MOSIII			
	N-ch + P-ch	SSM6P15FE	−30	±20	−0.1	0.15	—	12	32	—	—	9.1	3.5	8.6	—	π-MOSVI	(6Cc)		
		SSM6L35FE	20	±10	0.18	0.15	—	3	4	—	8	9.5	4.1	9.5	—	π-MOSVI			
		SSM6L36FE	−20	±10	−0.1	0.15	—	8	11	—	22	12.2	6.5	10.4	—	π-MOSVI			
		SSM6L36FE	20	±10	0.5	0.15	0.66	—	0.85	1.14	1.52	46	7.3	10.8	1.23	U-MOSIII			
			SSM6L36FE	−20	±8	−0.33	0.15	1.31	—	—	2.7	3.6	43	6.1	10.3	1.2	U-MOSIII		
USV SOT-353  (mm)	N-ch x 2	SSM5N16FU	20	±10	0.1	0.2	—	3	4	—	15	9.3	4.5	9.8	—	π-MOSVI	(5CC)		
		SSM5N15FU	30	±20	0.1	0.2	—	4	7	—	—	7.8	3.6	8.8	—	π-MOSVI			
	P-ch x 2	SSM5P15FU	−30	±20	−0.1	0.2	—	12	32	—	—	9.1	3.5	8.6	—	π-MOSVI	(5cc)		

*: New Product / 新製品

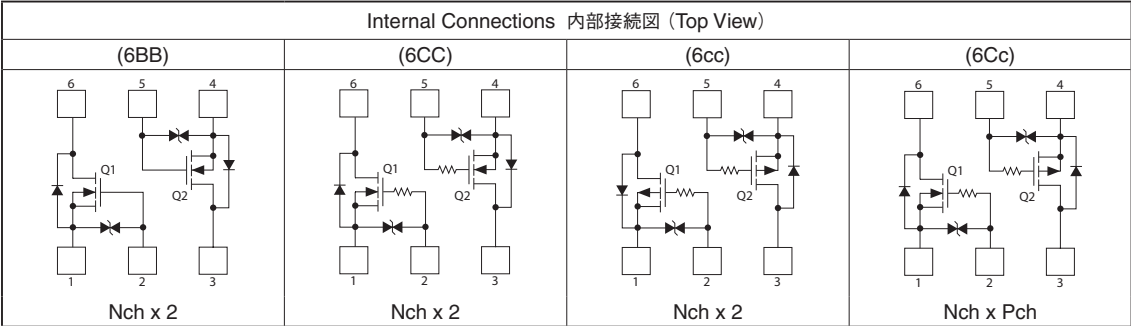


- The internal connection diagrams only show the general configurations of the circuits.
- 内部接続図はイメージ図です。

(Small-Signal Type: Dual Channel/Complementary) / (小信号スタンダードタイプ:デュアルチャネル/コンプリメンタリ) (2/2)

Package	Polarity	Part Number	Absolute Maximum Ratings				R _{DS(ON)} max (Ω)					C _{iss} typ. (pF)	C _{rss} typ. (pF)	C _{oss} typ. (pF)	Q _g typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)	
			V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)	V _{GS} = 4.5 V	V _{GS} = 4 V	V _{GS} = 2.5 V	V _{GS} = 1.8 V	V _{GS} = 1.5 V								
 (mm)	N-ch x 2	SSM6N36TU	20	±10	0.5	0.5	0.66	—	0.85	1.14	1.52	46	7.3	10.8	1.23	U-MOSIII	(6CC)		
		SSM6N62TU		±8	0.8	0.5	0.085	—	0.098	0.12	0.173	177	17	52	2	U-MOSVII-H			
		SSM6N24TU	30	±12	0.5	0.5	0.145	—	0.18	—	—	245	33	41	—	U-MOSIII	(6BB)		
	P-ch x 2	SSM6P36TU	−20	±8	−0.33	0.5	1.31	—	—	2.7	3.6	43	6.1	10.3	1.2	U-MOSIII	(6cc)		
		N-ch + P-ch	SSM6L12TU	30	±12	0.5	0.5	0.145	—	0.18	—	—	245	33	41	—	U-MOSIII		(6Cc)
	SSM6L12TU		−20	±12	−0.5	0.5	—	0.26	0.43	—	—	218	42	52	—	U-MOSIII			
	SSM6L36TU		20	±10	0.5	0.5	0.66	—	0.85	1.14	1.52	46	7.3	10.8	1.23	U-MOSIII			
SSM6L36TU	−20		±8	−0.33	0.5	1.31	—	—	2.7	3.6	43	6.1	10.3	1.2	U-MOSIII				
 (mm)	N-ch x 2	SSM6N16FU	20	±10	0.1	0.2	—	3	4	—	15	9.3	4.5	9.8	—	π-MOSVI	(6CC)		
		SSM6N35FU		±10	0.18	0.2	—	3	4	—	8	9.5	4.1	9.5	—	π-MOSVI			
		SSM6N35AFU *		±10	0.25	0.285	1.1	—	1.6	2.4	3.1	18	5	6	0.34	U-MOSIII			
		SSM6N37FU		±10	0.25	0.3	2.2	—	3.02	4.05	5.6	12	4.1	5.5	—	U-MOSIII			
		SSM6N43FU		±10	0.5	0.2	0.66	—	0.85	1.14	1.52	46	7.3	10.8	1.23	π-MOSVI			
		SSM6N15AFU	30	±20	0.1	0.3	—	3.6	6	—	—	13.5	6.5	8	—	U-MOSIII			
		SSM6N44FU		±20	0.1	0.2	—	4	7	—	—	8.5	5.3	9.4	—	π-MOSVI			
		SSM6N48FU		±20	0.1	0.3	—	3.2	5.4	—	—	15.1	7.8	12.4	—	U-MOSIII			
		SSM6N09FU		±20	0.4	0.3	—	1.2	—	—	—	20	7	16	—	π-MOSVI			
		SSM6N17FU	50	±7	0.1	0.2	—	20	40	—	—	7	3	7	—	π-MOSV			
	P-ch x 2	SSM6N7002CFU *	60	±20	0.17	0.285	4.7	—	—	—	—	11	0.7	3	0.27	U-MOSVII-H	(6CC)		
		SSM6N7002KFU *		±20	0.3	0.285	1.75	—	—	—	—	26	1.3	5.5	0.39	U-MOSVII-H			
		SSM6P35FU	−20	±10	−0.1	0.2	—	8	11	—	22	12.2	6.5	10.4	—	π-MOSVI			(6cc)
	P-ch x 2	SSM6P35AFU *	−30	±10	−0.25	0.285	1.4	—	2.1	2.9	4	21	2	6	—	U-MOSVII			
		SSM6P15FU		±20	−0.1	0.2	—	12	32	—	—	9.1	3.5	8.6	—	π-MOSVI			
	N-ch + P-ch	SSM6L09FU	30	±20	0.4	0.3	—	1.2	—	—	—	20	7	16	—	π-MOSVI	(6Cc)		
			−30	±20	−0.2	0.3	—	4.2	—	—	—	22	5	14	—	π-MOSVI			
		SSM6L35FU	20	±10	0.18	0.2	—	3	4	—	8	9.5	4.1	9.5	—	π-MOSVI			
			−20	±10	−0.1	0.2	—	8	11	—	22	12.2	6.5	10.4	—	π-MOSVI			

*: New Product / 新製品



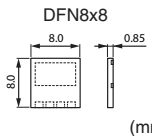
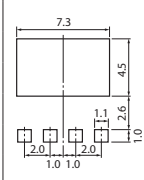
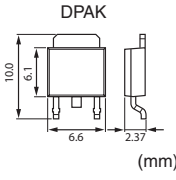
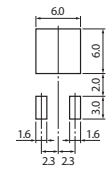
- The internal connection diagrams only show the general configurations of the circuits.
- 内部接続図はイメージ図です。

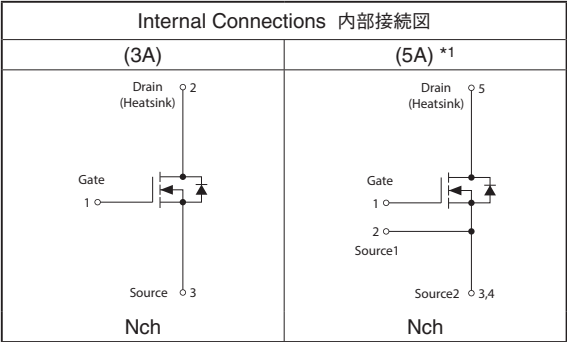
Mid-High Voltage MOSFETs / 中高耐压 MOSFET

DTMOS Series / DTMOS シリーズ

(Single N-Channel) / (シングルNチャネル)

(1/5)

Package	Part Number	Absolute Maximum Ratings				R _{DS(ON)} max (Ω) V _{GS} = 10 V	C _{iss} typ. (pF)	C _{rss} typ. (pF)	C _{oss} typ. (pF)	Q _g typ. (nC)	Series	Internal Con- nec- tions	Land Pattern Examples (mm)
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)								
 (mm)	TK10V60W	600	±30	9.7	83.3	0.38	700	2.3	20	20	DTMOSIV	(5A)	
	TK12V60W		±30	11.5	104	0.3	890	2.8	23	25	DTMOSIV		
	TK16V60W		±30	15.8	139	0.19	1350	4	35	38	DTMOSIV		
	TK16V60W5		±30	15.8	139	0.245	1350	4	35	43	DTMOSIV(HSD)		
	TK20V60W		±30	20	156	0.17	1680	7	40	48	DTMOSIV		
	TK20V60W5		±30	20	156	0.19	1800	5.5	45	55	DTMOSIV(HSD)		
	TK25V60X		±30	25	180	0.135	2400	6	60	40	DTMOSIV-H		
	TK25V60X5		±30	25	180	0.15	2400	6	60	60	DTMOSIV-H(HSD)		
	TK31V60W		±30	30.8	240	0.098	3000	9.5	70	86	DTMOSIV		
	TK31V60W5		±30	30.8	240	0.109	3000	9.5	70	105	DTMOSIV(HSD)		
	TK31V60X		±30	30.8	240	0.098	3000	7	70	65	DTMOSIV-H		
	TK14V65W	650	±30	13.7	139	0.28	1300	4	35	35	DTMOSIV		
	TK17V65W		±30	17.3	156	0.21	1800	7	40	45	DTMOSIV		
	TK22V65X5		±30	22	180	0.17	2400	6	60	50	DTMOSIV-H(HSD)		
	TK28V65W		±30	27.6	240	0.12	3000	8	70	75	DTMOSIV		
	TK28V65W5		±30	27.6	240	0.14	3000	8	70	90	DTMOSIV(HSD)		
 (mm)	TK10P50W	500	±30	9.7	80	0.43	700	2.3	20	20	DTMOSIV	(3A)	
	TK12P50W		±30	11.5	100	0.34	890	2.8	23	25	DTMOSIV		
	TK5P60W5	600	±30	4.5	60	0.99	370	1	11	11.5	DTMOSIV(HSD)		
	TK5P60W		±30	5.4	60	0.9	380	1.5	10	10.5	DTMOSIV		
	TK6P60W		±30	6.2	60	0.82	390	1.7	12	12	DTMOSIV		
	TK560P60Y		±30	7	60	0.56	380	2.5	18	14.5	DTMOSV		
	TK7P60W		±30	7	60	0.6	490	1.7	13	15	DTMOSIV		
	TK7P60W5		±30	7	60	0.67	490	1.7	13	16	DTMOSIV(HSD)		
	TK8P60W		±30	8	80	0.5	570	2.5	16	18.5	DTMOSIV		
	TK8P60W5		±30	8	80	0.56	590	1.7	16	22	DTMOSIV(HSD)		
	TK10P60W	650	±30	9.7	80	0.43	700	2.3	20	20	DTMOSIV		
	TK380P60Y		±30	9.7	80	0.38	590	2.5	23	20	DTMOSV		
	TK12P60W		±30	11.5	100	0.34	890	2.8	23	25	DTMOSIV		
	TK290P60Y		±30	11.5	100	0.29	730	2.5	26	25	DTMOSV		
	TK5P65W		±30	5.2	60	1.22	380	1.5	10	10.5	DTMOSIV		
	TK6P65W		±30	5.8	60	1.05	390	1.7	12	11	DTMOSIV		
	TK7P65W		±30	6.8	60	0.8	490	1.7	13	15	DTMOSIV		
	TK560P65Y		±30	7	60	0.56	380	2.5	18	14.5	DTMOSV		
	TK8P65W		±30	7.8	80	0.67	570	2.5	16	16	DTMOSIV		
	TK9P65W		±30	9.3	80	0.56	700	2.3	20	20	DTMOSIV		
	TK380P65Y		±30	9.7	80	0.38	590	2.5	23	20	DTMOSV		
	TK11P65W		±30	11.1	100	0.44	890	2.8	23	25	DTMOSIV		
	TK290P65Y		±30	11.5	100	0.29	730	2.5	26	25	DTMOSV		

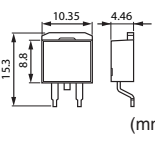
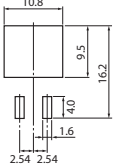
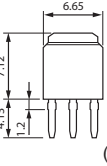
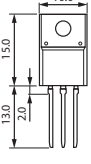


(*1) Notice : Please use the source1 pin for gate input signal return. Make sure that the main current flows into the source2 pins.

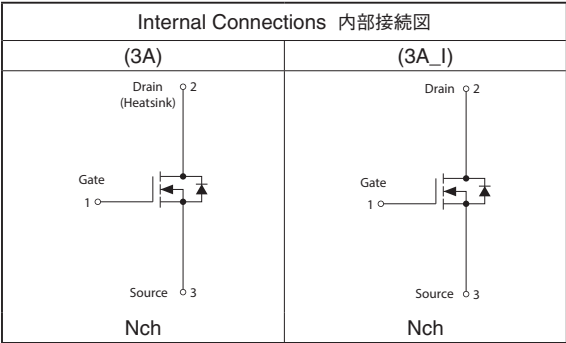
(*1) ご注意：ソース1はゲート入力信号のリターン用として使用してください。主電流はソース2を流すように配線パターンを設計してください。

・ The internal connection diagrams only show the general configurations of the circuits.

・ 内部接続図はイメージ図です。

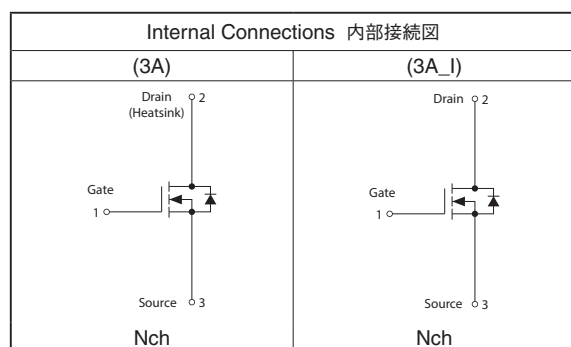
Package	Part Number	Absolute Maximum Ratings				R _{DS(ON)} max (Ω) V _{GS} = 10 V	C _{iss} typ. (pF)	C _{rss} typ. (pF)	C _{oss} typ. (pF)	Q _g typ. (nC)	Series	Internal Conne- ctions	Land Pattern Examples (mm)
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)								
D2PAK  (mm)	TK16G60W	600	±30	15.8	130	0.19	1350	4	35	38	DTMOSIV	(3A)	
	TK16G60W5		±30	15.8	130	0.23	1350	4	35	43	DTMOSIV(HSD)		
	TK20G60W		±30	20	165	0.155	1680	7	40	48	DTMOSIV		
	TK14G65W	650	±30	13.7	130	0.25	1300	4	35	35	DTMOSIV		
	TK14G65W5		±30	13.7	130	0.3	1300	4	35	40	DTMOSIV(HSD)		
IPAK  (mm)	TK5Q60W	600	±30	5.4	60	0.9	380	1.5	10	10.5	DTMOSIV	(3A)	
	TK6Q60W		±30	6.2	60	0.82	390	1.7	12	12	DTMOSIV		
	TK7Q60W		±30	7	60	0.6	490	1.7	13	15	DTMOSIV		
	TK8Q60W		±30	8	80	0.5	570	2.5	16	18.5	DTMOSIV		
	TK10Q60W		±30	9.7	80	0.43	700	2.3	20	20	DTMOSIV		
	TK12Q60W		±30	11.5	100	0.34	890	2.8	23	25	DTMOSIV		
	TK5Q65W	650	±30	5.2	60	1.22	380	1.5	10	10.5	DTMOSIV		
	TK6Q65W		±30	5.8	60	1.05	390	1.7	12	11	DTMOSIV		
	TK7Q65W		±30	6.8	60	0.8	490	1.7	13	15	DTMOSIV		
	TK8Q65W		±30	7.8	80	0.67	570	2.5	16	16	DTMOSIV		
	TK9Q65W		±30	9.3	80	0.56	700	2.3	20	20	DTMOSIV		
	TK11Q65W		±30	11.1	100	0.44	890	2.8	23	25	DTMOSIV		
TO-220SIS  (mm)	TK10A50W	500	±30	9.7	30	0.38	700	2.3	20	20	DTMOSIV	(3A_I)	
	TK12A50W		±30	11.5	35	0.3	890	2.8	23	25	DTMOSIV		
	TK19A50W		±30	18.5	40	0.19	1350	4	35	38	DTMOSIV		
	TK5A60W5	600	±30	4.5	30	0.95	370	1	11	11.5	DTMOSIV(HSD)		
	TK5A60W		±30	5.4	30	0.9	380	1.5	10	10.5	DTMOSIV		
	TK6A60W		±30	6.2	30	0.75	390	1.7	12	12	DTMOSIV		
	TK560A60Y		±30	7	30	0.56	380	2.5	18	14.5	DTMOSV		
	TK7A60W		±30	7	30	0.6	490	1.7	13	15	DTMOSIV		
	TK7A60W5		±30	7	30	0.65	490	1.7	13	16	DTMOSIV(HSD)		
	TK8A60W		±30	8	30	0.5	570	2.5	16	18.5	DTMOSIV		
	TK8A60W5		±30	8	30	0.54	590	1.7	16	22	DTMOSIV(HSD)		
	TK10A60W		±30	9.7	30	0.38	700	2.3	20	20	DTMOSIV		
	TK10A60W5		±30	9.7	30	0.45	720	2	20	25	DTMOSIV(HSD)		
	TK380A60Y		±30	9.7	30	0.38	590	2.5	23	20	DTMOSV		
	TK12A60W		±30	11.5	35	0.3	890	2.8	23	25	DTMOSIV		
	TK290A60Y		±30	11.5	35	0.29	730	2.5	26	25	DTMOSV		
	TK16A60W		±30	15.8	40	0.19	1350	4	35	38	DTMOSIV		
	TK16A60W5		±30	15.8	40	0.23	1350	4	35	43	DTMOSIV(HSD)		
	TK20A60W		±30	20	45	0.155	1680	7	40	48	DTMOSIV		
	TK20A60W5		±30	20	45	0.175	1800	5.5	45	55	DTMOSIV(HSD)		
	TK25A60X		±30	25	45	0.125	2400	6	60	40	DTMOSIV-H		
	TK25A60X5		±30	25	45	0.14	2400	6	60	60	DTMOSIV-H(HSD)		
	TK31A60W		±30	30.8	45	0.088	3000	9.5	70	86	DTMOSIV		
	TK39A60W		±30	38.8	50	0.065	4100	10	90	110	DTMOSIV		

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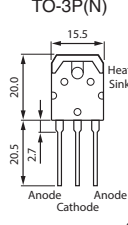
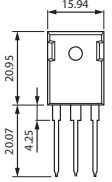


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- 内部接続図はイメージ図です。

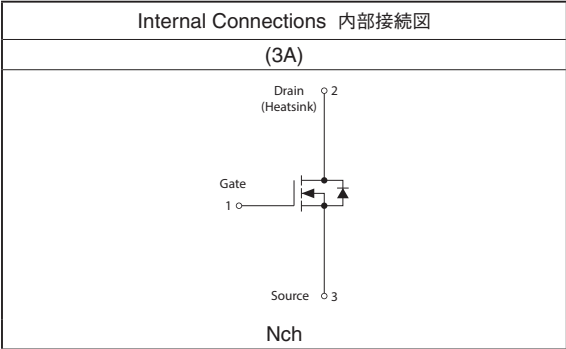
Package	Part Number	Absolute Maximum Ratings				$R_{DS(ON)}$ max (Ω) $ V_{GS} = 10\text{ V}$	C_{iss} typ. (pF)	C_{rss} typ. (pF)	C_{oss} typ. (pF)	Q_g typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)
		V_{DSS} (V)	V_{GSS} (V)	I_D (A)	P_D (W)								
(Continued from previous page)	TK5A65W	650	± 30	5.2	30	1.2	380	1.5	10	10.5	DTMOSIV	(3A_I)	
	TK6A65W		± 30	5.8	30	1	390	1.7	12	11	DTMOSIV		
	TK7A65W		± 30	6.8	30	0.78	490	1.7	13	15	DTMOSIV		
	TK560A65Y		± 30	7	30	0.56	380	2.5	18	14.5	DTMOSV		
	TK8A65W		± 30	7.8	30	0.65	570	2.5	16	16	DTMOSIV		
	TK9A65W		± 30	9.3	30	0.5	700	2.3	20	20	DTMOSIV		
	TK380A65Y		± 30	9.7	30	0.38	590	2.5	23	20	DTMOSV		
	TK11A65W		± 30	11.1	35	0.39	890	2.8	23	25	DTMOSIV		
	TK290A65Y		± 30	11.5	35	0.29	730	2.5	26	25	DTMOSV		
	TK14A65W		± 30	13.7	40	0.25	1300	4	35	35	DTMOSIV		
	TK14A65W5		± 30	13.7	40	0.3	1300	4	35	40	DTMOSIV(HSD)		
	TK17A65W		± 30	17.3	45	0.2	1800	7	40	45	DTMOSIV		
	TK17A65W5		± 30	17.3	45	0.23	1800	5.5	45	50	DTMOSIV(HSD)		
	TK22A65X		± 30	22	45	0.15	2400	6	60	50	DTMOSIV-H		
	TK22A65X5		± 30	22	45	0.16	2400	6	60	50	DTMOSIV-H(HSD)		
	TK28A65W		± 30	27.6	45	0.11	3000	8	70	75	DTMOSIV		
	TK35A65W		± 30	35	50	0.08	4100	9	90	100	DTMOSIV		
	TK35A65W5		± 30	35	50	0.095	4100	9	90	115	DTMOSIV(HSD)		
	TK7A80W	800	± 20	6.5	35	0.95	700	1.2	20	13	DTMOSIV		
	TK10A80W		± 20	9.5	40	0.55	1150	2	27	19	DTMOSIV		
	TK12A80W		± 20	11.5	45	0.45	1400	3	29	23	DTMOSIV		
	TK17A80W		± 20	17	45	0.29	2050	2	42	32	DTMOSIV		
	TK10E60W		± 30	9.7	100	0.38	700	2.3	20	20	DTMOSIV		
	TK12E60W	600	± 30	11.5	110	0.3	890	2.8	23	25	DTMOSIV	(3A)	
	TK16E60W		± 30	15.8	130	0.19	1350	4	35	38	DTMOSIV		
	TK16E60W5		± 30	15.8	130	0.23	1350	4	35	43	DTMOSIV(HSD)		
	TK20E60W		± 30	20	165	0.155	1680	7	40	48	DTMOSIV		
	TK20E60W5		± 30	20	165	0.175	1800	5.5	45	55	DTMOSIV(HSD)		
	TK25E60X		± 30	25	180	0.125	2400	6	60	40	DTMOSIV-H		
	TK25E60X5		± 30	25	180	0.14	2400	6	60	60	DTMOSIV-H(HSD)		
	TK31E60W		± 30	30.8	230	0.088	3000	9.5	70	86	DTMOSIV		
	TK31E60X		± 30	30.8	230	0.088	3000	7	70	65	DTMOSIV-H		
	TK14E65W	650	± 30	13.7	130	0.25	1300	4	35	35	DTMOSIV		
	TK14E65W5		± 30	13.7	130	0.3	1300	4	35	40	DTMOSIV(HSD)		
	TK17E65W		± 30	17.3	165	0.2	1800	7	40	45	DTMOSIV		
	TK28E65W		± 30	27.6	230	0.11	3000	8	70	75	DTMOSIV		
	TK7E80W	800	± 20	6.5	110	0.95	700	1.2	20	13	DTMOSIV		
	TK10E80W		± 20	9.5	130	0.55	1150	2	27	19	DTMOSIV		
	TK12E80W		± 20	11.5	165	0.45	1400	3	29	23	DTMOSIV		
	TK17E80W		± 20	17	180	0.29	2050	2	42	32	DTMOSIV		



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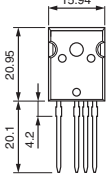
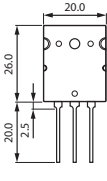
Package	Part Number	Absolute Maximum Ratings				R _{DS(ON)} max (Ω) V _{GS} = 10 V	C _{iss} typ. (pF)	C _{rss} typ. (pF)	C _{oss} typ. (pF)	Q _g typ. (nC)	Series	Internal Con- nec- tions	Land Pattern Examples (mm)
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)								
TO-3P(N)  (mm)	TK12J60W	600	±30	11.5	110	0.3	890	2.8	23	25	DTMOSIV	(3A)	
	TK16J60W		±30	15.8	130	0.19	1350	4	35	38	DTMOSIV		
	TK16J60W5		±30	15.8	130	0.23	1350	4	35	43	DTMOSIV(HSD)		
	TK20J60W		±30	20	165	0.155	1680	7	40	48	DTMOSIV		
	TK20J60W5		±30	20	165	0.175	1800	5.5	45	55	DTMOSIV(HSD)		
	TK31J60W		±30	30.8	230	0.088	3000	9.5	70	86	DTMOSIV		
	TK31J60W5		±30	30.8	230	0.099	3000	9.5	70	105	DTMOSIV(HSD)		
	TK39J60W		±30	38.8	270	0.065	4100	10	90	110	DTMOSIV		
	TK39J60W5		±30	38.8	270	0.074	4100	10	90	135	DTMOSIV(HSD)		
	TK62J60W		±30	61.8	400	0.04	6500	20	140	180	DTMOSIV		
	TK62J60W5		±30	61.8	400	0.045	6500	16	140	205	DTMOSIV(HSD)		
TO-247  (mm)	TK16N60W	600	±30	15.8	130	0.19	1350	4	35	38	DTMOSIV	(3A)	
	TK16N60W5		±30	15.8	130	0.23	1350	4	35	43	DTMOSIV(HSD)		
	TK20N60W		±30	20	165	0.155	1680	7	40	48	DTMOSIV		
	TK20N60W5		±30	20	165	0.175	1800	5.5	45	55	DTMOSIV(HSD)		
	TK25N60X		±30	25	180	0.125	2400	6	60	40	DTMOSIV-H		
	TK25N60X5		±30	25	180	0.14	2400	6	60	60	DTMOSIV-H(HSD)		
	TK31N60W		±30	30.8	230	0.088	3000	9.5	70	86	DTMOSIV		
	TK31N60W5		±30	30.8	230	0.099	3000	9.5	70	105	DTMOSIV(HSD)		
	TK31N60X		±30	30.8	230	0.088	3000	7	70	65	DTMOSIV-H		
	TK39N60W		±30	38.8	270	0.065	4100	10	90	110	DTMOSIV		
	TK39N60W5		±30	38.8	270	0.074	4100	10	90	135	DTMOSIV(HSD)		
	TK39N60X		±30	38.8	270	0.065	4100	8	90	85	DTMOSIV-H		
	TK62N60W		±30	61.8	400	0.04	6500	20	140	180	DTMOSIV		
	TK62N60W5		±30	61.8	400	0.045	6500	16	140	205	DTMOSIV(HSD)		
	TK62N60X		±30	61.8	400	0.04	6500	15	140	135	DTMOSIV-H		
	TK14N65W	650	±30	13.7	130	0.25	1300	4	35	35	DTMOSIV		
	TK14N65W5		±30	13.7	130	0.3	1300	4	35	40	DTMOSIV(HSD)		
	TK17N65W		±30	17.3	165	0.2	1800	7	40	45	DTMOSIV		
	TK28N65W		±30	27.6	230	0.11	3000	8	70	75	DTMOSIV		
	TK28N65W5		±30	27.6	230	0.13	3000	8	70	90	DTMOSIV(HSD)		
	TK35N65W		±30	35	270	0.08	4100	9	90	100	DTMOSIV		
	TK35N65W5		±30	35	270	0.095	4100	9	90	115	DTMOSIV(HSD)		
	TK49N65W		±30	49.2	400	0.055	6500	15	140	160	DTMOSIV		
	TK49N65W5		±30	49.2	400	0.057	6500	15	140	185	DTMOSIV(HSD)		
	TK040N65Z		±30	57	360	0.04	6250	4	140	105	DTMOSVI		
		*											

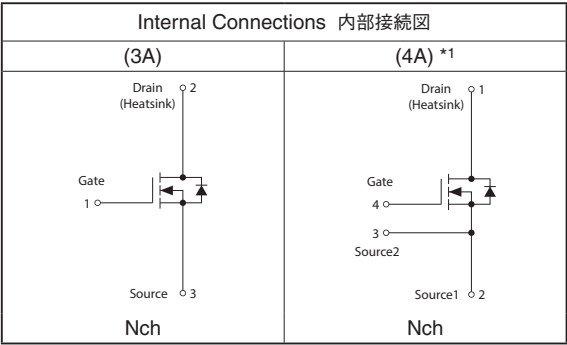
*: New Product / 新製品



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• 内部接続図はイメージ図です。

Package	Part Number	Absolute Maximum Ratings				$R_{DS(ON)}$ max (Ω) $ V_{GS} = 10\text{ V}$	C_{iss} typ. (pF)	C_{rss} typ. (pF)	C_{oss} typ. (pF)	Q_g typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)
		V_{DSS} (V)	V_{GSS} (V)	I_D (A)	P_D (W)								
TO-247-4L  (mm)	TK25Z60X	600	± 30	25	180	0.125	2400	6	60	40	DTMOSIV-H	(4A)	
	TK31Z60X		± 30	30.8	230	0.088	3000	7	70	65	DTMOSIV-H		
	TK39Z60X		± 30	38.8	270	0.065	4100	8	90	85	DTMOSIV-H		
	TK62Z60X		± 30	61.8	400	0.04	6500	15	140	135	DTMOSIV-H		
TO-3P(L)  (mm)	TK100L60W	600	± 30	100	797	0.018	15000	50	320	360	DTMOSIV	(3A)	



(*1) Notice : Please use the source1 pin for gate input signal return. Make sure that the main current flows into the source2 pins.

(*1) ご注意：ソース1はゲート入力信号のリターン用として使用してください。主電流はソース2を流すように配線パターンを設計してください。

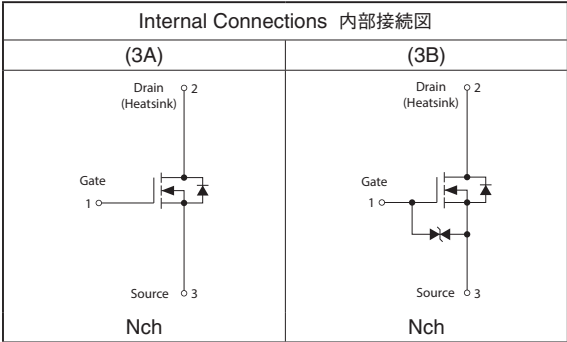
・ The internal connection diagrams only show the general configurations of the circuits.

・ 内部接続図はイメージ図です。

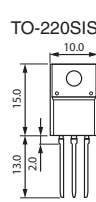
π-MOS Series / π-MOSシリーズ
 (Single N-Channel) / (シングルNチャネル)

(1/4)

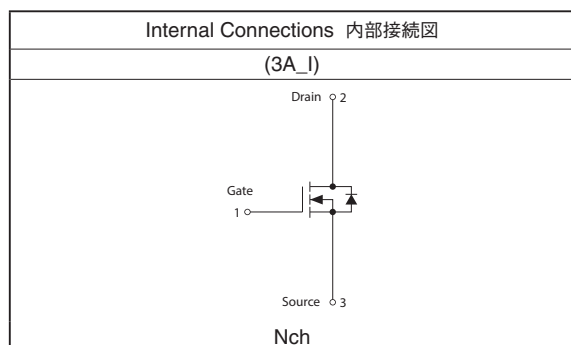
Package	Part Number	Absolute Maximum Ratings				R _{DS(ON)} max (Ω) V _{GS} = 10 V	C _{iss} typ. (pF)	C _{rss} typ. (pF)	C _{oss} typ. (pF)	Q _g typ. (nC)	Series	Internal Con- nec- tions	Land Pattern Examples (mm)
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)								
New PW-Mold (mm)	TK5P50D5	500	±30	5	80	1.85	490	3	55	12	π-MOSVII (HSD)	(3A)	
	TK2P60D	600	±30	2	60	4.3	280	1.5	30	7	π-MOSVII		
	TK1P90A	900	±30	1	20	9	320	10	35	13	π-MOSIV	(3B)	
DPAK (mm)	TK3P50D	500	±30	3	60	3	280	1.5	30	7	π-MOSVII	(3A)	
	TK4P50D		±30	4	80	2	380	3	45	9	π-MOSVII		
	TK5P50D		±30	5	80	1.5	490	3	55	11	π-MOSVII		
	TK7P50D		±30	7	100	1.22	600	4	70	12	π-MOSVII		
	TK5P53D	525	±30	5	80	1.5	540	3	60	11	π-MOSVII		
	TK6P53D		±30	6	100	1.3	600	4	70	12	π-MOSVII		
	TK4P55DA	550	±30	3.5	80	2.45	380	2.5	45	9	π-MOSVII		
	TK4P55D		±30	4	80	1.88	490	3	55	11	π-MOSVII		
	TK4P60DA	600	±30	3.5	80	2.2	490	3	55	11	π-MOSVII		
	TK4P60DB		±30	3.7	80	2	540	3	60	11	π-MOSVII		
	TK4P60D		±30	4	100	1.7	600	4	70	12	π-MOSVII		
	TK3P80E	800	±30	3	80	4.9	500	4	40	12	π-MOSVIII		
	TK2P90E	900	±30	2	80	5.9	500	4	40	12	π-MOSVIII		
New PW-Mold2 (mm)	TK2Q60D	600	±30	2	60	4.3	280	1.5	30	7	π-MOSVII	(3A)	
	TK4Q60DA		±30	3.5	80	2.2	490	3	55	11	π-MOSVII		
	TK1Q90A	900	±30	1	20	9	320	10	35	13	π-MOSIV	(3B)	



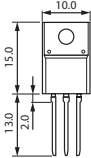
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Package	Part Number	Absolute Maximum Ratings				R _{DS(ON)} max (Ω) V _{GS} = 10 V	C _{iss} typ. (pF)	C _{rss} typ. (pF)	C _{oss} typ. (pF)	Q _g typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)								
TO-220SIS  (mm) (Continued on next page)	TK5A45DA	450	±30	4.5	30	1.75	380	2.5	45	9	π-MOSVII	(3A_I)	
	TK6A45DA		±30	5.5	35	1.35	490	3	55	11	π-MOSVII		
	TK7A45DA		±30	6.5	35	1.2	540	3	60	11	π-MOSVII		
	TK8A45D		±30	8	35	0.9	700	4	80	16	π-MOSVII		
	TK9A45D		±30	9	40	0.77	800	4	100	16	π-MOSVII		
	TK11A45D		±30	11	40	0.62	1050	5	100	20	π-MOSVII		
	TK12A45D		±30	12	45	0.52	1200	6	120	24	π-MOSVII		
	TK13A45D		±30	13	45	0.46	1350	6	135	25	π-MOSVII		
	TK19A45D		±30	19	50	0.25	2600	11	280	45	π-MOSVII		
	TK4A50D	500	±30	4	30	2	380	2.5	45	9	π-MOSVII		
	TK5A50D		±30	5	35	1.5	490	3	55	11	π-MOSVII		
	TK5A50D5		±30	5	35	2.1	490	3	55	11	π-MOSVII (HSD)		
	TK6A50D		±30	6	35	1.4	540	3	60	11	π-MOSVII		
	TK7A50D		±30	7	35	1.22	600	4	70	12	π-MOSVII		
	TK7A50D5		±30	7	35	1.68	600	4	70	12	π-MOSVII (HSD)		
	TK8A50DA		±30	7.5	35	1.04	700	4	80	16	π-MOSVII		
	TK8A50D		±30	8	40	0.85	800	4	100	16	π-MOSVII		
	TK10A50D		±30	10	45	0.72	1050	5	100	20	π-MOSVII		
	TK11A50D		±30	11	45	0.6	1200	6	120	24	π-MOSVII		
	TK12A50D		±30	12	45	0.52	1350	6	135	25	π-MOSVII		
	TK12A50D5		±30	12	45	0.78	1200	12	160	30	π-MOSVII (HSD)		
	TK13A50DA		±30	12.5	45	0.47	1550	7	165	28	π-MOSVII		
	TK13A50D		±30	13	45	0.4	1800	9	190	38	π-MOSVII		
	TK15A50D		±30	15	50	0.3	2300	10	250	40	π-MOSVII		
	TK18A50D		±30	18	50	0.27	2600	11	280	45	π-MOSVII		
	TK4A53D	525	±30	4	35	1.7	490	3	55	11	π-MOSVII		
	TK5A53D		±30	5	35	1.5	540	3	60	11	π-MOSVII		
	TK6A53D		±30	6	35	1.3	600	4	70	12	π-MOSVII		
	TK12A53D		±30	12	45	0.58	1350	6	135	25	π-MOSVII		
	TK4A55DA	550	±30	3.5	30	2.45	380	2.5	45	9	π-MOSVII		
	TK4A55D		±30	4	35	1.88	490	3	55	11	π-MOSVII		
	TK5A55D		±30	5	35	1.7	540	3	60	11	π-MOSVII		
	TK6A55DA		±30	5.5	35	1.48	600	4	70	12	π-MOSVII		
	TK7A55D		±30	7	35	1.25	700	4	80	16	π-MOSVII		
	TK8A55DA		±30	7.5	40	1.07	800	4	100	16	π-MOSVII		
	TK9A55DA		±30	8.5	40	0.86	1050	5	100	20	π-MOSVII		
	TK10A55D		±30	10	45	0.72	1200	6	120	24	π-MOSVII		
	TK11A55D		±30	11	45	0.63	1350	6	135	25	π-MOSVII		
	TK12A55D		±30	12	45	0.57	1550	7	165	28	π-MOSVII		
	TK13A55DA		±30	12.5	45	0.48	1800	9	190	38	π-MOSVII		
	TK14A55D		±30	14	50	0.37	2300	10	250	40	π-MOSVII		
	TK16A55D		±30	16	50	0.33	2600	11	280	45	π-MOSVII		

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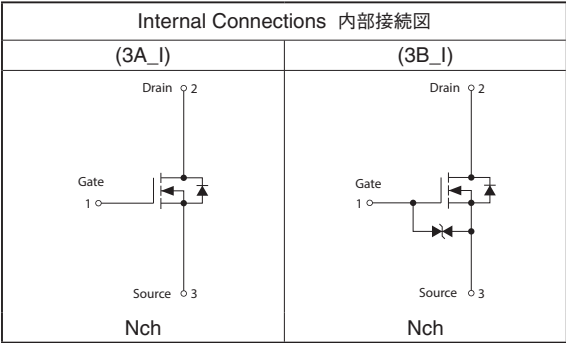


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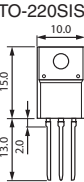
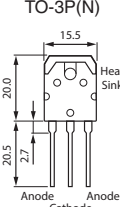
Package	Part Number	Absolute Maximum Ratings				R _{DS(ON)} max (Ω) V _{GS} = 10 V	C _{iss} typ. (pF)	C _{rss} typ. (pF)	C _{oss} typ. (pF)	Q _g typ. (nC)	Series	Internal Con- nec- tions	Land Pattern Examples (mm)		
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)										
(Continued from previous page)  (mm)	TK4K1A60F **	600	±30	2	30	4.1	270	2.5	11	8	π-MOSIX	(3A_I)			
	TK3A60DA		±30	2.5	30	2.8	380	2.5	45	9	π-MOSVII				
	TK4A60DA		±30	3.5	35	2.2	490	3	55	11	π-MOSVII				
	TK2K2A60F **		±30	3.5	30	2.2	450	3.6	16	13	π-MOSIX				
	TK4A60DB		±30	3.7	35	2	540	3	60	11	π-MOSVII				
	TK1K9A60F *		±30	3.7	30	1.9	490	5.2	20	14	π-MOSIX				
	TK4A60D		±30	4	35	1.7	600	4	70	12	π-MOSVII				
	TK1K7A60F **		±30	4	35	1.7	560	5	20	16	π-MOSIX				
	TK5A60D		±30	5	35	1.43	700	4	80	16	π-MOSVII				
	TK6A60D		±30	6	40	1.25	800	4	100	16	π-MOSVII				
	TK1K2A60F *		±30	6	35	1.2	740	6.8	29	20.5	π-MOSIX				
	TK8A60DA		±30	7.5	45	1	1050	5	100	20	π-MOSVII				
	TK1K0A60F **		±30	7.5	40	1	890	8.3	33	24	π-MOSIX				
	TK9A60D		±30	9	45	0.83	1200	6	120	24	π-MOSVII				
	TK10A60D		±30	10	45	0.75	1350	6	135	25	π-MOSVII				
	TK10A60D5		±30	10	45	1.05	1350	15	135	25	π-MOSVII (HSD)				
	TK750A60F *		±30	10	40	0.75	1130	8.5	40	30	π-MOSIX				
	TK11A60D		±30	11	45	0.65	1550	7	165	28	π-MOSVII				
	TK650A60F *		±30	11	45	0.65	1320	10	47	34	π-MOSIX				
	TK12A60D		±30	12	45	0.55	1800	9	190	38	π-MOSVII				
	TK13A60D	±30	13	50	0.43	2300	10	250	40	π-MOSVII					
	TK15A60D	±30	15	50	0.37	2600	11	280	45	π-MOSVII					
	TK2A65D	650	±30	2	30	3.26	380	2.5	45	9	π-MOSVII				
	TK3A65DA		±30	2.5	35	2.51	490	3	55	11	π-MOSVII				
	TK3A65D		±30	3	35	2.25	540	3	60	11	π-MOSVII				
	TK4A65DA		±30	3.5	35	1.9	600	4	70	12	π-MOSVII				
	TK5A65DA		±30	4.5	35	1.67	700	4	70	16	π-MOSVII				
	TK5A65D		±30	5	40	1.43	800	4	100	16	π-MOSVII				
	TK6A65D		±30	6	45	1.11	1050	5	100	20	π-MOSVII				
	TK7A65D		±30	7	45	0.98	1200	6	120	24	π-MOSVII				
	TK8A65D		±30	8	45	0.84	1350	6	135	25	π-MOSVII				
	TK11A65D		±30	11	45	0.7	1700	8	157	30	π-MOSVII				
	TK12A65D		±30	12	50	0.54	2300	10	200	40	π-MOSVII				
	TK13A65D		±30	13	50	0.47	2600	11	280	45	π-MOSVII				
	TK4A80E	800	±30	4	35	3.5	650	6	55	15	π-MOSVIII				
	TK5A80E		±30	5	40	2.4	950	8	75	20	π-MOSVIII				
	2SK4013		±30	6	45	1.7	1400	30	130	45	π-MOSIV			(3B_I)	
	TK6A80E		±30	6	45	1.7	1350	10	110	32	π-MOSVIII			(3A_I)	
	(Continued on next page)	TK10A80E		±30	10	50	1	2000	15	150	46			π-MOSVIII	

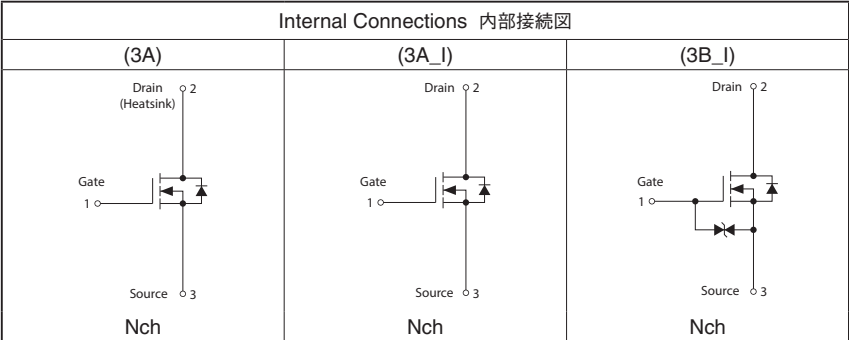
*: New Product / 新製品

***: Under Development / 開発中



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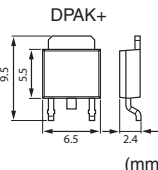
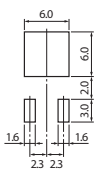
Package	Part Number	Absolute Maximum Ratings				R _{DS(ON)} max (Ω) V _{GS} = 10 V	C _{iss} typ. (pF)	C _{rss} typ. (pF)	C _{oss} typ. (pF)	Q _g typ. (nC)	Series	Internal Con- nec- tions	Land Pattern Examples (mm)
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)								
(Continued from previous page)  (mm)	2SK3566	900	±30	2.5	40	6.4	470	10	50	12	π-MOSIV	(3B_I)	
	TK3A90E		±30	2.5	35	4.6	650	6	55	15	π-MOSVIII	(3A_I)	
	2SK3564		±30	3	40	4.3	700	15	75	17	π-MOSIV	(3B_I)	
	2SK3798		±30	4	40	3.5	800	20	85	26	π-MOSIV	(3B_I)	
	TK5A90E		±30	4.5	40	3.1	950	8	75	20	π-MOSVIII	(3A_I)	
	2SK3565		±30	5	45	2.5	1150	20	100	28	π-MOSIV	(3B_I)	
	2SK3742		±30	5	45	2.5	1150	20	110	25	π-MOSIV		
	2SK4014		±30	6	45	2	1400	30	130	45	π-MOSIV		
	TK7A90E		±30	7	45	2	1350	10	110	32	π-MOSVIII	(3A_I)	
	2SK3799		±30	8	50	1.3	2200	45	190	60	π-MOSIV	(3B_I)	
	TK9A90E		±30	9	50	1.3	2000	15	150	46	π-MOSVIII	(3A_I)	
 (mm)	TK15J50D	500	±30	15	210	0.4	1800	9	190	38	π-MOSVII	(3A)	
	TK20J50D		±30	20	280	0.27	2600	11	280	45	π-MOSVII		
	TK12J55D	550	±30	12	190	0.57	1550	7	165	28	π-MOSVII		
	TK16J55D		±30	16	250	0.37	2300	10	250	40	π-MOSVII		
	TK19J55D		±30	19	280	0.33	2600	11	280	45	π-MOSVII		
	2SK3633	800	±30	7	150	1.7	1500	25	140	35	π-MOSIV	(3B_I)	
	TK10J80E		±30	10	250	1	2000	15	150	46	π-MOSVIII	(3A)	
	2SK3700	900	±30	5	150	2.5	1150	20	100	28	π-MOSIV	(3B_I)	
	2SK4115		±30	7	150	2	1650	30	140	45	π-MOSIV		
	TK7J90E		±30	7	200	2	1350	10	110	32	π-MOSVIII	(3A)	
	TK9J90E		±30	9	250	1.3	2000	15	150	46	π-MOSVIII		
	2SK4207		±30	13	150	0.95	2790	25	300	45	π-MOSIV	(3B_I)	



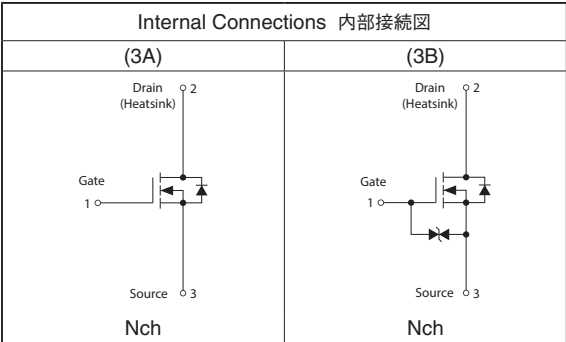
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Automotive MOSFETs / 車載 MOSFET

Automotive Power MOSFETs / 車載パワー MOSFET
(Single N-Channel) / (シングルNチャネル)

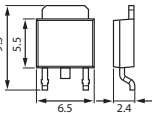
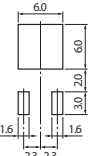
Package	Part Number	Absolute Maximum Ratings					R _{DS(ON)} max (mΩ)			Ciss typ. (pF)	Crss typ. (pF)	Coss typ. (pF)	Qg typ. (nC)	Series	Internal Conne- ctions	Land Pattern Examples (mm)	
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)	T _{ch} (°C)	V _{GS} = 10 V	V _{GS} = 6 V	V _{GS} = 4.5 V								
 (mm)	TK15S04N1L	40	±20	15	46	175	17.8	—	37	610	50	390	10	U-MOSVIII-H	(3B)		
	TK35S04K3L		±20	35	58	175	10.3	15	—	1370	180	320	28	U-MOSIV			
	TK65S04N1L		±20	65	107	175	4.3	—	7.8	2550	130	1430	39	U-MOSVIII-H			
	TK100S04N1L		±20	100	180	175	2.3	—	4.5	5490	220	3000	76	U-MOSVIII-H	(3A)		
	TK1R4S04PB		±20	120	180	175	1.35	1.9	—	5500	490	3400	103	U-MOSIX-H			
	TK8S06K3L	60	±20	8	25	175	54	80	—	400	40	80	10	U-MOSIV	(3B)		
	TK20S06K3L		±20	20	38	175	29	40	—	780	75	136	18	U-MOSIV			
	TK25S06N1L		±20	25	57	175	18.5	—	36.8	855	69	490	15	U-MOSVIII-H			
	TK30S06K3L		±20	30	58	175	18	30	—	1350	130	230	28	U-MOSIV			
	TK40S06N1L		±20	40	88.2	175	10.5	—	18	1650	107	835	26	U-MOSVIII-H			
	TK60S06K3L		±20	60	88	175	8	12.3	—	2900	280	460	60	U-MOSIV			
	TK90S06N1L		±20	90	157	175	3.3	—	5.2	5400	350	2630	81	U-MOSVIII-H	(3A)		
	TK7S10N1Z	100	±20	7	50	175	48	—	—	470	36	260	7.1	U-MOSVIII-H	(3B)		
	TK11S10N1L *		±20	11	65	175	28	—	50	850	67	370	15	U-MOSVIII-H			
	TK33S10N1L		±20	33	125	175	9.7	—	16.2	2250	145	1010	33	U-MOSVIII-H			
	TK33S10N1Z		±20	33	125	175	9.7	—	—	2050	140	1070	28	U-MOSVIII-H			
	TK55S10N1		±20	55	157	175	6.5	—	—	3280	210	1520	49	U-MOSVIII-H	(3A)		
	TK60S10N1L		±20	60	180	175	6.11	9.25	—	4320	220	1480	60	U-MOSVIII-H			

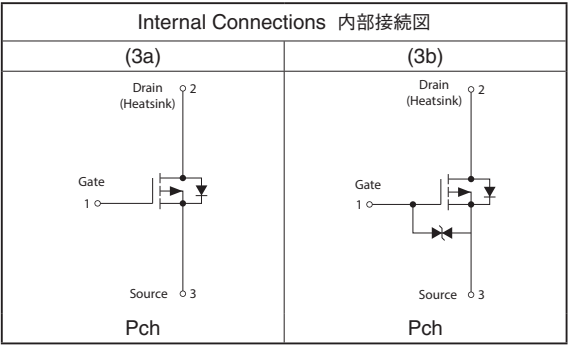
*: New Product / 新製品



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(Single P-Channel) / (シングルPチャンネル)

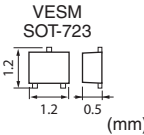
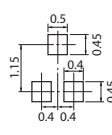
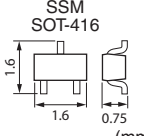
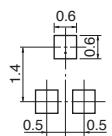
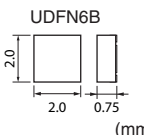
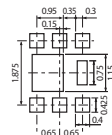
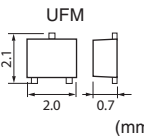
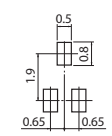
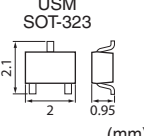
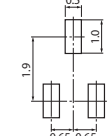
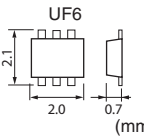
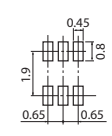
Package	Part Number	Absolute Maximum Ratings					R _{DS(ON)} max (mΩ)			C _{iss} typ. (pF)	C _{rss} typ. (pF)	C _{oss} typ. (pF)	Q _g typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)	T _{ch} (°C)	V _{GS} = 10 V	V _{GS} = 6 V	V _{GS} = 4.5 V							
 (mm)	TJ10S04M3L	-40	+10/-20	-10	27	175	44	62	—	930	90	140	19	U-MOSVI	(3b)	
	TJ20S04M3L		+10/-20	-20	41	175	22.2	32	—	1850	180	250	37	U-MOSVI		
	TJ40S04M3L		+10/-20	-40	68	175	9.1	13	—	4140	410	510	83	U-MOSVI		
	TJ60S04M3L		+10/-20	-60	90	175	6.3	9.4	—	6510	570	780	125	U-MOSVI		
	TJ80S04M3L		+10/-20	-80	100	175	5.2	7.9	—	7770	740	970	158	U-MOSVI		
	TJ90S04M3L		+10/-20	-90	180	175	4.3	—	6.0	7700	825	990	172	U-MOSVI		
	TJ8S06M3L	-60	+10/-20	-8	27	175	104	130	—	890	60	100	19	U-MOSVI	(3b)	
	TJ15S06M3L		+10/-20	-15	41	175	50	63	—	1770	130	180	36	U-MOSVI		
	TJ30S06M3L		+10/-20	-30	68	175	21.8	28	—	3950	270	360	80	U-MOSVI		
	TJ50S06M3L		+10/-20	-50	90	175	13.8	17.4	—	6290	410	560	124	U-MOSVI		
	TJ60S06M3L		+10/-20	-60	100	175	11.2	14.5	—	7760	530	690	156	U-MOSVI		
	TJ15S10M3		-100	+10/-20	-15	75	175	130	—	—	3200	135	190	69		



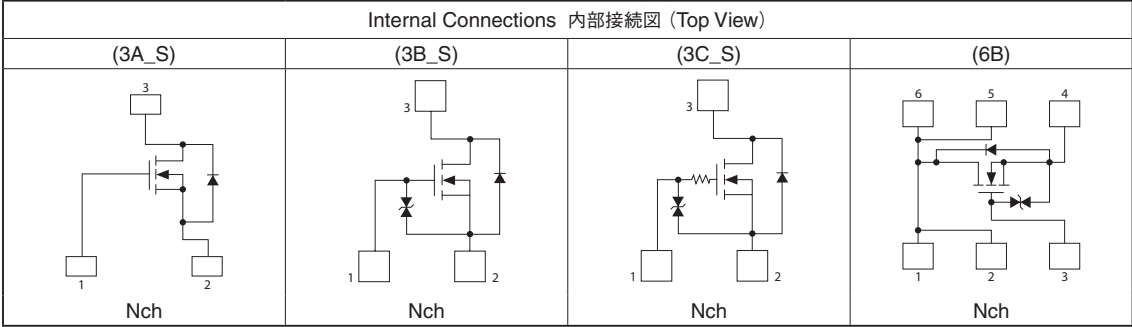
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Automotive Small-Package Series / 車載小型パッケージシリーズ
(Single N-Channel) / (シングルNチャンネル)

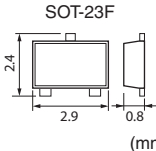
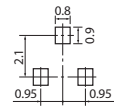
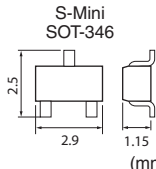
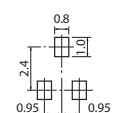
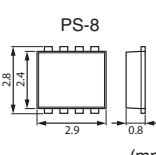
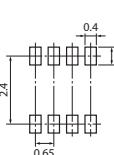
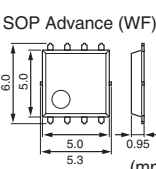
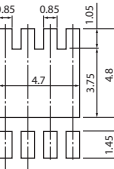
(1/2)

Package	Part Number	Absolute Maximum Ratings					R _{DS(ON)} max (mΩ)						Ciss typ. (pF)	Crss typ. (pF)	Coss typ. (pF)	Qg typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)		
		V _{DSS} (V)	V _{GSS} (V)	I _B (A)	P _D (W)	T _{ch} (°C)	I _V gsl = 10 V	I _V gsl = 6 V	I _V gsl = 4.5 V	I _V gsl = 4 V	I _V gsl = 2.5 V	I _V gsl = 1.8 V								I _V gsl = 1.5 V	
 (mm)	SSM3K35MFV	20	±10	0.18	0.15	150	—	—	—	3000	4000	—	8000	9.5	4.1	9.5	—	π-MOSVI	(3C_S)		
	SSM3K56MFV		±8	0.8	0.15	150	—	—	235	—	300	480	840	55	6	16	1	U-MOSVII-H	(3B_S)		
	SSM3K44MFV	30	±20	0.1	0.15	150	—	—	—	4000	7000	—	—	8.5	5.3	9.4	—	π-MOSVI	(3C_S)		
 (mm)	SSM3K35FS	20	±10	0.18	0.1	150	—	—	—	3000	4000	—	8000	9.5	4.1	9.5	—	π-MOSVI	(3C_S)		
	SSM3K56FS		±8	0.8	0.15	150	—	—	235	—	300	480	840	55	6	16	1	U-MOSVII-H	(3B_S)		
	SSM3K44FS	30	±20	0.1	0.15	150	—	—	—	4000	7000	—	—	8.5	5.3	9.4	—	π-MOSVI	(3C_S)		
	SSM3K72KFS *	60	±20	0.3	0.15	150	1500	—	1750	—	—	—	—	26	1.3	5.5	0.39	U-MOSVII-H			
 (mm)	SSM6K504NU	30	±20	9	1.25	150	19.5	—	26	—	—	—	—	620	42	110	4.8	U-MOSVII-H	(6B)		
 (mm)	SSM3K62TU *	20	±8	0.8	0.5	150	—	—	57	—	68	89	139	177	17	52	2	U-MOSVII-H	(3C_S)		
	SSM3K122TU		±10	2	0.5	150	—	—	—	123	161	211	304	195	29	35	3.4	U-MOSIII	(3B_S)		
	SSM3K121TU		±10	3.2	0.5	150	—	—	—	48	63	93	140	400	60	68	5.9	U-MOSIII			
	SSM3K123TU		±10	4.2	0.5	150	—	—	—	28	32	43	66	1010	150	162	13.6	U-MOSIII			
	SSM3K127TU	30	±12	2	0.5	150	—	—	—	123	167	286	—	123	18	43	1.5	U-MOSIII	(3A_S)		
	SSM3K116TU		±12	2.2	0.5	150	—	—	100	—	135	—	—	245	33	41	—	U-MOSIII			
	SSM3K131TU		±20	6	0.5	150	27.6	—	41.5	—	—	—	—	450	77	120	10.1	U-MOSIV			
	SSM3K2615TU *	60	±20	2	0.8	150	300	—	—	440	—	—	—	150	25	70	6	π-MOSV	(3C_S)		(3B_S)
	SSM3K341TU *		±20	6	1	175	36	—	51	69	—	—	—	550	35	300	9.3	U-MOSVIII-H			
SSM3K361TU *	100	±20	3.5	1	175	69	—	92	—	—	—	—	430	22	160	3.2	U-MOSVIII-H				
 (mm)	SSM3K15FU	30	±20	0.1	0.15	150	—	—	—	4000	7000	—	—	7.8	3.6	8.8	—	π-MOSVI	(3C_S)		
	SSM3K7002KFU *	60	±20	0.4	0.15	150	1500	—	1750	—	—	—	—	26	1.3	5.5	0.39	U-MOSVII-H			
 (mm)	SSM6K404TU	20	±10	3	0.5	150	—	—	—	55	70	100	147	400	60	68	5.9	U-MOSIII	(6B)		
	SSM6K403TU		±10	4.2	0.5	150	—	—	—	28	32	43	66	1050	160	175	16.8	U-MOSIII			
	SSM6K406TU	30	±20	4.4	0.5	150	25	—	38.5	—	—	—	—	490	105	143	12.4	U-MOSIV			
	SSM6K407TU	60	±20	2	0.5	150	300	—	—	440	—	—	—	150	25	70	6	π-MOSV			

*: New Product / 新製品

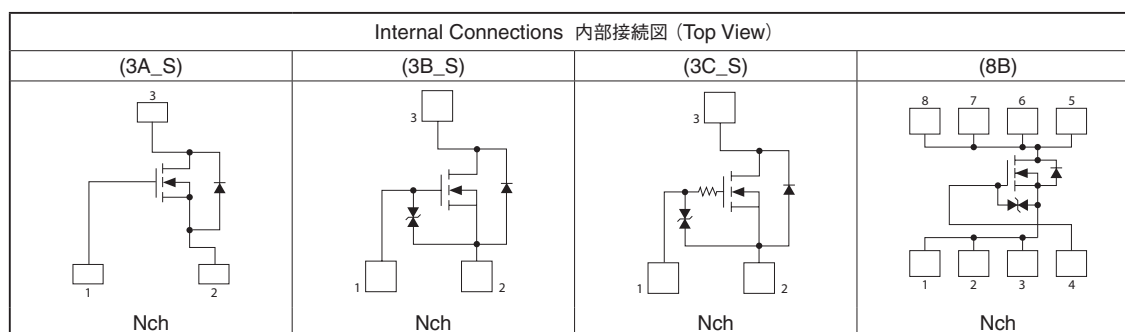


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Package	Part Number	Absolute Maximum Ratings					R _{DS(ON)} max (mΩ)						C _{iss} typ. (pF)	C _{rss} typ. (pF)	C _{oss} typ. (pF)	Q _g typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)	
		V _{BSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)	T _{ch} (°C)	V _{GS} = 10 V	V _{GS} = 6 V	V _{GS} = 4.5 V	V _{GS} = 4 V	V _{GS} = 2.5 V	V _{GS} = 1.8 V								V _{GS} = 1.5 V
 SOT-23F (mm)	SSM3K336R *	30	±20	3	1	150	95	—	140	—	—	—	126	8	26	1.7	U-MOSVII-H	(3B_S)		
	SSM3K329R		±12	3.5	1	150	—	—	—	126	170	289	—	123	18	43	1.5			U-MOSIII
	SSM3K376R		+12/-8	4	1	150	—	—	56	—	72	109	—	200	13	40	2.2			U-MOSVII-H
	SSM3K333R		±20	6	1	150	28	—	42	—	—	—	—	436	28	77	3.4			U-MOSVII-H
	SSM3K335R	60	±20	6	1	150	38	—	56	—	—	—	—	340	20	60	2.7	U-MOSVII-H		(3B_S)
	SSM3K2615R		±20	2	1	150	300	—	—	440	—	—	—	150	25	70	6	π-MOSV		(3C_S)
	SSM3K318R		±20	2.5	1	150	107	—	145	—	—	—	—	235	23	31	7	U-MOSIV		(3B_S)
	SSM3K341R *		±20	6	1.2	175	36	—	51	69	—	—	—	550	35	300	9.3	U-MOSVIII-H		
SSM3K361R *	100	±20	3.5	1.2	175	69	—	92	—	—	—	—	430	22	160	3.2	U-MOSVIII-H	(3C_S)		
 S-Mini SOT-346 (mm)	SSM3K15F	30	±20	0.1	0.2	150	—	—	—	4000	7000	—	—	7.8	3.6	8.8	—	π-MOSVI	(3C_S)	
	SSM3K7002KF *	60	±20	0.4	0.27	150	1500	—	1750	—	—	—	—	26	1.3	5.5	0.39	U-MOSVII-H		
 PS-8 (mm)	TPCP8011	40	±20	5	1.96 (1)	175	31.8	51.2	—	—	—	—	—	505	66	115	11.8	U-MOSIV	(8B)	
	TPCP8010		±20	6	1.96 (1)	175	23.8	38.4	—	—	—	—	—	600	75	132	13.1	U-MOSIV		
	TPCP8009		±20	10	2.01 (1)	175	11.8	19.5	—	—	—	—	—	1250	165	265	25.1	U-MOSIV		
	TPCP8013	60	±20	4	1.96 (1)	175	51.8	77.9	—	—	—	—	—	515	48	86	12	U-MOSIV		
	TPCP8012		±20	8	2.01 (1)	175	20.2	29.1	—	—	—	—	—	1160	120	200	26.6	U-MOSIV		
 SOP Advance (WF) (mm)	TPH4R304NC	40	±20	40	55	175	4.3	—	8.8	—	—	—	—	2450	145	1380	35	U-MOSVIII-H	(8B)	
	TPH1R104PB *		±20	120	132	175	1.14	1.95	—	—	—	—	—	4560	320	2940	55	U-MOSIX-H		
	TPHR7904PB *		±20	150	170	175	0.79	1.3	—	—	—	—	—	—	6340	490	4300	85		

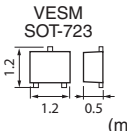
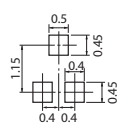
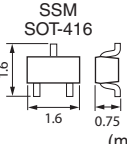
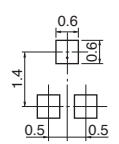
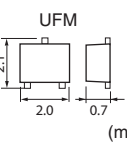
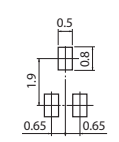
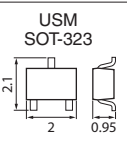
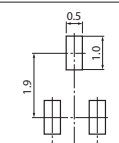
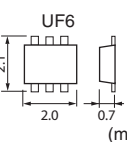
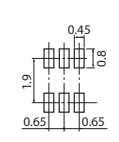
Note (1): Device mounted on a glass board. t = 5 seconds. / ガラスエポキシ基板。t = 5 秒。

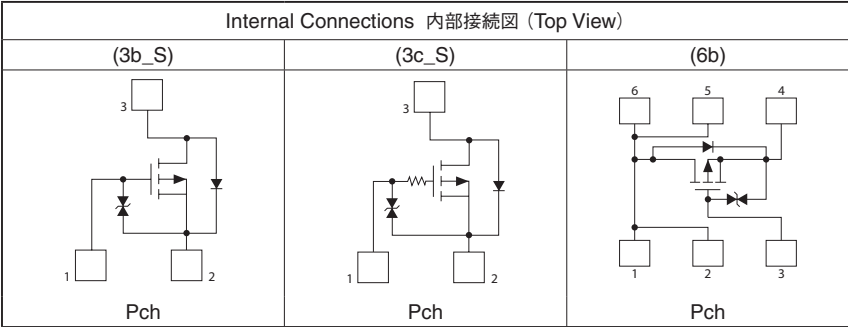
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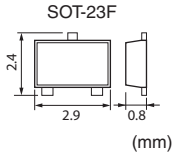
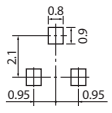
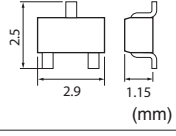
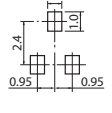
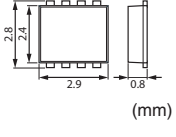
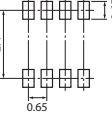
• The internal connection diagrams only show the general configurations of the circuits.

• 内部接続図はイメージ図です。

Package	Part Number	Absolute Maximum Ratings					R _{DS(ON)} max (mΩ)						C _{iss} typ. (pF)	C _{rss} typ. (pF)	C _{oss} typ. (pF)	Q _g typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)	
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)	T _{ch} (°C)	I _{VGSL} = 10 V	I _{VGSL} = 6 V	I _{VGSL} = 4.5 V	I _{VGSL} = 4 V	I _{VGSL} = 2.5 V	I _{VGSL} = 1.8 V								I _{VGSL} = 1.5 V
 (mm)	SSM3J35MFV	-20	±10	-0.1	0.15	150	—	—	—	8000	11000	—	22000	12.2	6.5	10.4	—	π-MOSVI	(3c_S)	
	SSM3J66MFV		+6/-8	-0.8	0.5	150	—	—	390	—	480	660	900	100	10	16	1.6	U-MOSVI	(3b_S)	
	SSM3J36MFV		±8	-0.33	0.15	150	—	—	1310	—	—	2700	3600	43	6.1	10.3	1.2	U-MOSIII	(3c_S)	
	SSM3J15FV	-30	±20	-0.1	0.15	150	—	—	—	12000	32000	—	—	9.1	3.5	8.6	—	π-MOSVI	(3c_S)	
 (mm)	SSM3J35FS	-20	±10	-0.1	0.1	150	—	—	—	8000	11000	—	22000	12.2	6.5	10.4	—	π-MOSVI	(3c_S)	
	SSM3J36FS		±8	-0.33	0.15	150	—	—	1310	—	—	2700	3600	43	6.1	10.3	1.2	U-MOSIII		
	SSM3J15FS	-30	±20	-0.1	0.1	150	—	—	—	12000	32000	—	—	9.1	3.5	8.6	—	π-MOSVI		
 (mm)	SSM3J145TU	-20	+6/-8	-3.0	0.5	150	—	—	103	—	132	180	260	270	32	40	4.6	U-MOSVI	(3b_S)	
	SSM3J144TU		+6/-8	-3.2	0.5	150	—	—	93	—	123	168	240	290	32	44	4.7	U-MOSVI		
	SSM3J140TU		+6/-8	-4.4	0.5	150	—	—	25.8	—	31	41.1	63.2	1800	190	205	24.8	U-MOSVI		
	SSM3J143TU		+6/-8	-5.5	0.5	150	—	—	29.8	—	39.7	56	88.4	840	99	118	12.8	U-MOSVI		
	SSM3J112TU	-30	±20	-1.1	0.5	150	390	—	—	790	—	—	—	86	14	25	—	U-MOSII		
	SSM3J118TU		±20	-1.4	0.5	150	240	—	—	480	—	—	—	137	20	39	—	U-MOSII		
	SSM3J117TU		±20	-2	0.5	150	117	—	—	225	—	—	—	280	45	80	—	U-MOSII		
 (mm)	SSM3J36TU	-20	±8	-0.33	0.5	150	—	—	1310	—	—	2700	3600	43	6.1	10.3	1.2	U-MOSIII	(3c_S)	
	SSM3J15FU	-30	±20	-0.1	0.15	150	—	—	—	12000	32000	—	—	9.1	3.5	8.6	—	π-MOSVI		
 (mm)	SSM6J50TU	-20	±10	-2.5	0.5	150	—	—	64	—	100	—	—	800	120	160	—	U-MOSIV	(6b)	
	SSM6J424TU		+6/-8	-6.0	1	150	—	—	22.5	—	26	36	54	1650	90	220	23.1	U-MOSVI		
	SSM6J422TU		+6/-8	-4.0	1	150	—	—	42.7	—	51.4	67.8	99.6	840	99	118	12.8	U-MOSVI		
	SSM6J402TU	-30	±20	-2	0.5	150	117	—	—	225	—	—	—	280	45	80	5.3	U-MOSII		
	SSM6J410TU		±20	-2.1	0.5	150	216	—	—	393	—	—	—	120	21	32	2.9	U-MOSIII		
	SSM6J401TU		±20	-2.5	0.5	150	73	—	—	145	—	—	—	730	90	110	16	U-MOSIII		

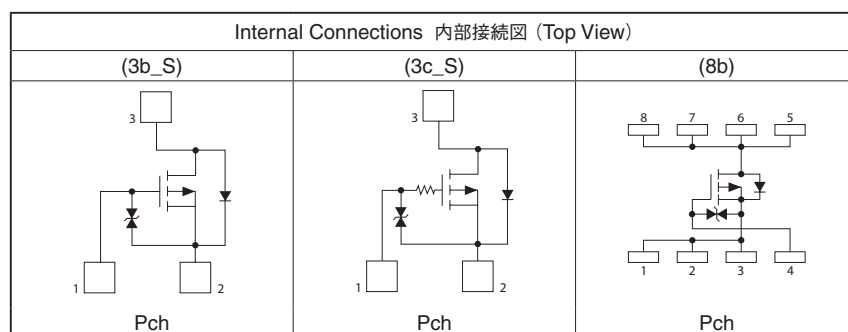


- The internal connection diagrams only show the general configurations of the circuits.
- 内部接続図はイメージ図です。

Package	Part Number	Absolute Maximum Ratings					R _{DS(ON)} max (mΩ)							C _{iss} typ. (pF)	C _{rss} typ. (pF)	C _{oss} typ. (pF)	Q _g typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)
		V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)	T _{ch} (°C)	V _{GSL} = 10 V	V _{GSL} = 6 V	V _{GSL} = 4.5 V	V _{GSL} = 4 V	V _{GSL} = 2.5 V	V _{GSL} = 1.8 V	V _{GSL} = 1.5 V							
 SOT-23F (mm)	SSM3J377R	-20	+6/-8	-3.9	1	150	—	—	93	—	123	168	240	290	32	44	4.6	U-MOSVI	(3b_S)	
	SSM3J371R		+6/-8	-4.0	1	150	—	—	55	—	75	100	150	630	60	75	10.4	U-MOSVI		
	SSM3J378R		+6/-8	-6.0	1	150	—	—	29.8	—	39.7	56	88.4	840	99	118	12.8	U-MOSVI		
	SSM3J374R	-30	+10/-20	-4.0	1	150	71	—	105	136	—	—	—	280	40	55	5.9	U-MOSVI		
	SSM3J372R		+6/-12	-6.0	1	150	42	—	50	—	72	144	—	560	65	80	8.2	U-MOSVI		
	SSM3J356R *		+10/-20	-2	1	150	300	—	360	400	—	—	—	330	25	40	8.3	U-MOSVI		
	SSM3J351R *	-60	+10/-20	-3.5	1	150	134	—	164	184	—	—	—	660	50	70	15.1	U-MOSVI		
 S-Mini SOT-346 (mm)	SSM3J375F	-20	+6/-8	-2	0.6	150	—	—	150	—	179	231	311	270	32	40	4.6	U-MOSVI	(3b_S)	
	SSM3J15F	-30	±20	-0.1	0.2	150	—	—	—	12000	32000	—	—	9.1	3.5	8.6	—	π-MOSVI	(3c_S)	
	SSM3J168F *	-60	+10/-20	-0.4	0.6	150	1550	—	1900	2000	—	—	—	82	5.5	13	3	U-MOSVI	(3b_S)	
 PS-8 (mm)	TPCP8109	-40	+10/-20	-4.5	1.96 ⁽¹⁾	175	52.3	76.8	—	—	—	—	—	810	85	130	18	U-MOSVI	(8b)	
	TPCP8107		+10/-20	-8	2.01 ⁽¹⁾	175	18	26.8	—	—	—	—	—	2160	238	292	44.6	U-MOSVI		
	TPCP8111	-60	+10/-20	-3	1.96 ⁽¹⁾	175	117	158.4	—	—	—	—	—	760	60	90	17	U-MOSVI		
	TPCP8110		+10/-20	-5	2.01 ⁽¹⁾	175	39.5	53.2	—	—	—	—	—	2075	150	205	45	U-MOSVI		

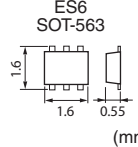
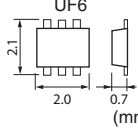
Note (1): Device mounted on a glass board. t = 5 seconds. / ガラスエポキシ基板。t = 5 秒。

*: New Product / 新製品



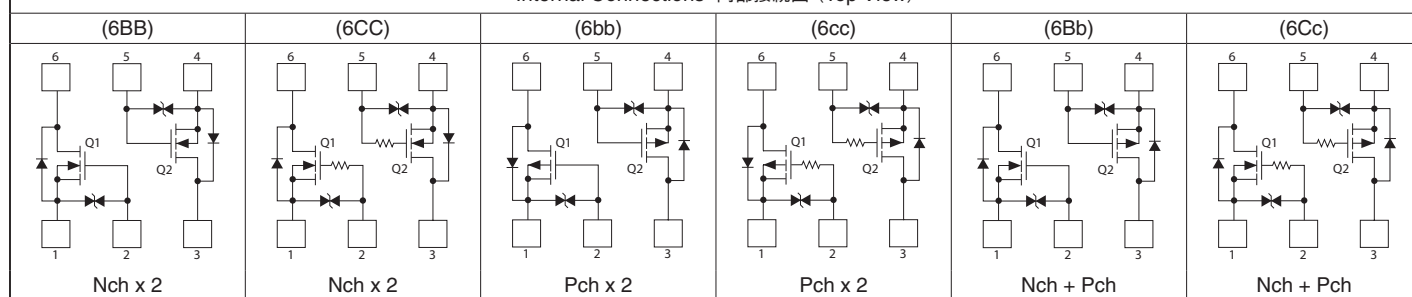
• The internal connection diagrams only show the general configurations of the circuits.

• 内部接続図はイメージ図です。

Package	Polarity	Part Number	Absolute Maximum Ratings					R _{DS(ON)} max (mΩ)						Ciss typ. (pF)	Crss typ. (pF)	Coss typ. (pF)	Qg typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)	
			V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)	T _{ch} (°C)	I _V gs1 = 10 V	I _V gs1 = 6 V	I _V gs1 = 4.5 V	I _V gs1 = 4 V	I _V gs1 = 2.5 V	I _V gs1 = 1.8 V								I _V gs1 = 1.5 V
 (mm)	N-ch x 2	SSM6N35FE	20	±10	0.18	0.15	150	—	—	—	3000	4000	—	8000	9.5	4.1	9.5	—	π-MOSVI	(6CC)	
		SSM6N56FE		±8	0.8	0.25	150	—	—	235	—	300	480	840	55	6	16	1	U-MOSVII-H	(6BB)	
		SSM6N44FE	30	±20	0.1	0.15	150	—	—	—	4000	7000	—	—	8.5	5.3	9.4	—	π-MOSVI	(6CC)	
	P-ch x 2	SSM6P35FE	−20	±10	−0.1	0.15	150	—	—	—	8000	11000	—	22000	12.2	6.5	10.4	—	π-MOSVI	(6cc)	
		SSM6P36FE		±8	−0.33	0.15	150	—	—	1310	—	—	2700	3600	43	6.1	10.3	1.2	U-MOSIII		
		SSM6P15FE	−30	±20	−0.1	0.15	150	—	—	—	12000	32000	—	—	9.1	3.5	8.6	—	π-MOSVI		
	N-ch + P-ch	SSM6L35FE	20	±10	0.18	0.15	150	—	—	—	3000	4000	—	8000	9.5	4.1	9.5	—	π-MOSVI	(6Cc)	
		SSM6L36FE	−20	±10	−0.1	0.15	150	—	—	—	8000	11000	—	22000	12.2	6.5	10.4	—	π-MOSVI		
		SSM6L36FE	20	±10	0.5	0.15	150	—	—	660	—	850	1140	1520	46	7.3	10.8	1.23	U-MOSIII		
		SSM6L36FE	−20	±8	−0.33	0.15	150	—	—	1310	—	—	2700	3600	43	6.1	10.3	1.2	U-MOSIII		
 (mm)	N-ch x 2	SSM6N61NU *	20	±8	4	1	150	—	—	33	—	45	74	108	410	40	85	3.6	U-MOSVII-H	(6BB)	
		SSM6N55NU	30	±20	4	1	150	46	—	64	—	—	—	—	280	20	53	2.5	U-MOSVII-H		
		SSM6N67NU		+12/−8	4	1	150	—	—	39.1	—	53	82	—	310	20	52	3.2	U-MOSVII-H		
		SSM6N68NU		+12/−8	4	1	150	—	—	84	—	117	180	—	129	13	34	1.8	U-MOSVII-H		
	P-ch x 2	SSM6P69NU	−20	+6/−12	−4	1	150	45	—	56	—	76	157	—	480	76	90	6.74	U-MOSVI	(6bb)	
 (mm)	N-ch x 2	SSM6N62TU	20	±8	0.8	0.5	150	—	—	85	—	98	120	173	177	17	52	2	U-MOSVII-H	(6BB)	
		SSM6N39TU		±10	1.6	0.5	150	—	—	—	119	139	190	247	260	37	45	7.5	U-MOSIII		
		SSM6N24TU	30	±12	0.5	0.5	150	—	—	145	—	180	—	—	245	33	41	—	U-MOSIII		
		SSM6N40TU		±20	1.6	0.5	150	122	—	—	182	—	—	—	180	27	34	5.1	U-MOSIII		
	P-ch x 2	SSM6P54TU	−20	±8	−1.2	0.5	150	—	—	—	—	228	350	555	331	39	48	7.7	U-MOSIV	(6bb)	
		SSM6P39TU		±8	−1.5	0.5	150	—	—	—	213	294	430	—	250	35	43	6.4	U-MOSIII		
		SSM6P40TU	−30	±20	−1.4	0.5	150	226	—	—	403	—	—	—	120	21	32	2.9	U-MOSIII		
	N-ch + P-ch	SSM6L12TU	30	±12	0.5	0.5	150	—	—	145	—	180	—	—	245	33	41	—	U-MOSIII	(6Cc)	
		SSM6L12TU	−20	±12	−0.5	0.5	150	—	—	—	260	430	—	—	218	42	52	—	U-MOSIII		
		SSM6L39TU	20	±10	1.6	0.5	150	—	—	—	119	139	190	247	260	37	45	7.5	U-MOSIII	(6Bb)	
		SSM6L39TU	−20	±8	−1.5	0.5	150	—	—	—	213	294	430	—	250	35	43	6.4	U-MOSIII		
		SSM6L40TU	30	±20	1.6	0.5	150	122	—	—	182	—	—	—	180	27	34	5.1	U-MOSIII		
		SSM6L40TU	−30	±20	−1.4	0.5	150	226	—	—	403	—	—	—	120	21	32	2.9	U-MOSIII		

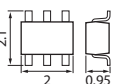
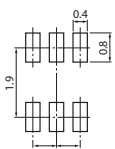
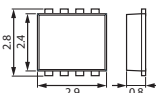
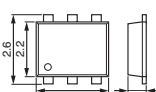
*: New Product / 新製品

Internal Connections 内部接続図 (Top View)



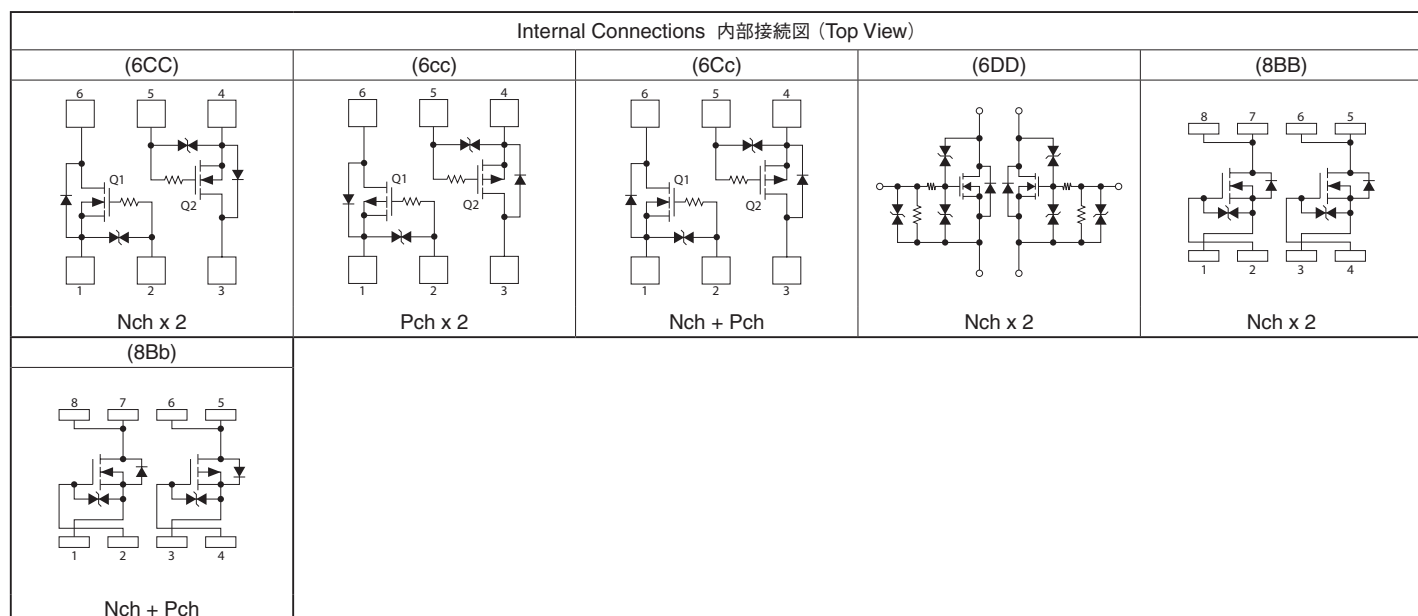
• The internal connection diagrams only show the general configurations of the circuits.

• 内部接続図はイメージ図です。

Package	Polarity	Part Number	Absolute Maximum Ratings					R _{DS(ON)} max (mΩ)						Ciss typ. (pF)	Crss typ. (pF)	Coss typ. (pF)	Qg typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)	
			V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)	T _{ch} (°C)	I _{V_{GS}} = 10 V	I _{V_{GS}} = 6 V	I _{V_{GS}} = 4.5 V	I _{V_{GS}} = 4 V	I _{V_{GS}} = 2.5 V	I _{V_{GS}} = 1.8 V								I _{V_{GS}} = 1.5 V
US6 SOT-363  (mm)	N-ch x 2	SSM6N35FU	20	±10	0.18	0.2	150	—	—	—	3000	4000	—	8000	9.5	4.1	9.5	—	π-MOSVI	(6CC)	
		SSM6N43FU	20	±10	0.5	0.2	150	—	—	660	—	850	1140	1520	46	7.3	10.8	1.23	π-MOSVI		
		SSM6N44FU	30	±20	0.1	0.2	150	—	—	—	4000	7000	—	—	8.5	5.3	9.4	—	π-MOSVI		
		SSM6N7002KFU *	60	±20	0.3	0.5	150	1500	—	1750	—	—	—	—	26	1.3	5.5	0.39	U-MOSVII-H		
	P-ch x 2	SSM6P35FU	-20	±10	-0.1	0.2	150	—	—	—	8000	11000	—	22000	12.2	6.5	10.4	—	π-MOSVI	(6cc)	
		SSM6P36TU	-20	±8	-0.33	0.5	150	—	—	1310	—	—	2700	3600	43	6.1	10.3	1.2	U-MOSIII		
		SSM6P15FU	-30	±20	-0.1	0.2	150	—	—	—	12000	32000	—	—	9.1	3.5	8.6	—	π-MOSVI		
	N-ch + P-ch	SSM6L35FU	20	±10	0.18	0.2	150	—	—	—	3000	4000	—	8000	9.5	4.1	9.5	—	π-MOSVI	(6Cc)	
		SSM6L35FU	-20	±10	-0.1	0.2	150	—	—	—	8000	11000	—	22000	12.2	6.5	10.4	—	π-MOSVI		
		SSM6L36TU	20	±10	0.5	0.5	150	—	—	660	—	850	1140	1520	46	7.3	10.8	1.23	U-MOSIII		
SSM6L36TU		-20	±8	-0.33	0.5	150	—	—	660	—	850	1140	1520	46	7.3	10.8	1.23	U-MOSIII			
PS-8  (mm)	N-ch x 2	TPCP8207	40	±20	5	1.77 (1)	175	36.3	62.8	—	—	—	—	505	66	115	11.8	U-MOSIV	(8BB)		
	N-ch + P-ch	TPCP8407	40	±20	5	1.77 (1)	175	36.3	62.8	—	—	—	—	—	505	66	115	11.8	U-MOSIV	(8Bb)	
			-40	+10/-20	-4	1.77 (1)	175	56.8	82.2	—	—	—	—	—	810	85	130	18	U-MOSVI		
TSOP6F  (mm)	N-ch x 2	SSM6N357R *	60	±12	0.65	1	150	—	—	—	—	—	—	43	2.5	20	1.5	π-MOSV	(6DD)		
		SSM6N813R	100	±20	3.5	1.5	175	112	—	154	—	—	—	—	242	7	106	3.6	U-MOSVIII-H	(6CC)	

Note (1): Device mounted on a glass board. t = 5 seconds. / ガラスエポキシ基板。t = 5 秒。

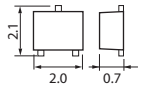
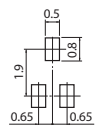
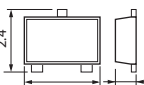
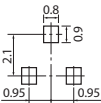
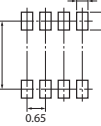
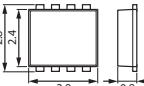
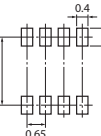
*: New Product / 新製品



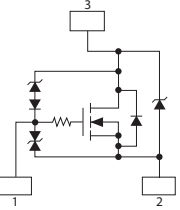
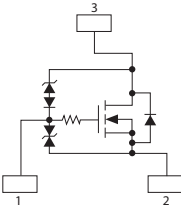
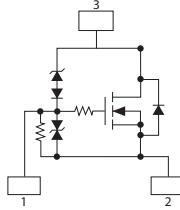
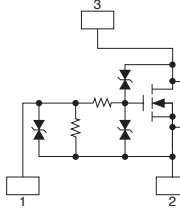
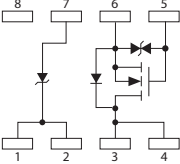
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(Semi-Power Type: Built-in Zener Diode) / (セミパワータイプ: ZD混載品)

Package	Polarity	Part Number	Absolute Maximum Ratings					R _{DS(ON)} max (mΩ)						Ciss typ. (pF)	Crss typ. (pF)	Coss typ. (pF)	Qg typ. (nC)	Series	Internal Connections	Land Pattern Examples (mm)	
			V _{DSS} (V)	V _{GSS} (V)	I _D (A)	P _D (W)	T _{ch} (°C)	I _{VGSL} = 10 V	I _{VGSL} = 6 V	I _{VGSL} = 4.5 V	I _{VGSL} = 4 V	I _{VGSL} = 2.5 V	I _{VGSL} = 1.8 V								I _{VGSL} = 1.5 V
UFM  (mm)	N-ch + Zener	SSM3H137TU *	34	±20	2	0.8	150	240	—	280	295	—	—	—	119	8	40	3	U-MOSIV	(3ZC_1)	
SOT-23F  (mm)	N-ch + Zener	SSM3K337R *	38	±20	2	1	150	150	—	176	200	—	—	—	120	7.2	33	3	U-MOSIV	(3ZC_2)	
		SSM3K347R *		±20	2	1	150	340	—	410	480	—	—	—	86	13	27	2.5	U-MOSIV	(3ZC_3)	
		SSM3K357R	60	±12	0.65	1	150	—	—	—	—	—	—	—	43	2.5	20	1.5	π-MOSV	(3ZC_4)	
PS-8  (mm)	N-ch + Zener	TPCP8R01	60	±20	2	0.5	150	300	—	—	440	—	—	—	140	20	65	5	π-MOSV	(8ZB)	

*: New Product / 新製品

Internal Connections 内部接続図 (Top View)				
(3ZC_1)	(3ZC_2)	(3ZC_3)	(3ZC_4)	(8ZB)
 Nch + ZD	 Nch + ZD	 Nch + ZD	 Nch + ZD	 Nch + ZD

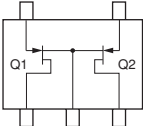
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Junction FETs / 接合形FET

(Single Type) / (シングルタイプ)

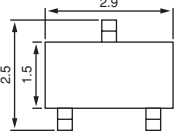
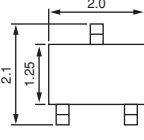
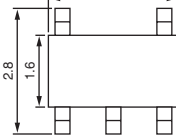
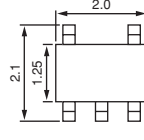
Classification	V _{GDS} (V) Max	I _G (mA) Max	I _{DSS} (mA)	Y _{fs} (mS) Min	S-MINI (SC-59)		USM (SC-70)	
					Nch	Pch	Nch	Pch
General-purpose	-50	10	0.3 to 6.5	1.2	2SK208		2SK879	
	-50	10	1.2 to 14	4	2SK209	—	2SK880	—

(Dual Type) / (デュアルタイプ)

Classification	V _{GDS} (V)	I _G (mA)	I _{DSS} (mA)	Y _{fs} (mS) Min	SMV		USV		Internal Connections
					Nch x 2	Pch x 2	Nch x 2	Pch x 2	
General-purpose	-50	10	1.2 to 14	4	2SK2145	—	2SK3320	—	

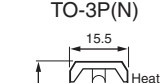
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Package Lineup / パッケージラインアップ

S-MINI (SC-59)	USM (SC-70)	SMV	USV
 (mm)	 (mm)	 (mm)	 (mm)

SiC MOSFETs / SiC MOSFET

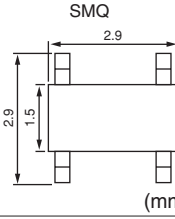
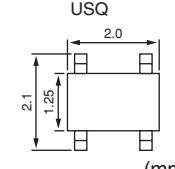
SiC MOSFETs / SiC MOSFET

Circuit Configuration		Absolute Maximum ratings		Electrical Characteristics (Ta = 25°C)				TO-3P(N)  (mm)
		VDS (V)	ID (A)	RDS(ON) (mΩ)			Qg (nC)	
				Typ.	VGS (V)	ID (A)		
Nch	Single	1200	(36)	70	(20)	(36)	(50)	TW070J120B **

**: Under development / 開発中

Radio-Frequency MOSFETs / 高周波 MOSFET

Radio-Frequency Small-Signal MOSFETs / 高周波小信号 MOSFET

Part Number	Package	Applications	Electrical Characteristics (Ta = 25°C)					Marking	Equivalent Product (Leaded Type)
			V _{DS} (V)	I _D (mA)	P _D (mW)	I _{DSS} (mA)	Y _{fs} (mS) Typ.		
3SK291	 (mm)	UHF-band radio-frequency amps	12.5	30	150	0 to 0.1	26	UF	—
3SK292		VHF/UHF-band radio-frequency amps	12.5	30	150	0 to 0.1	23.5	UV	—
3SK293	 (mm)	UHF-band radio-frequency amps	12.5	30	100	0 to 0.1	26	UF	—
3SK294		VHF/UHF-band radio-frequency amps	12.5	30	100	0 to 0.1	23.5	UV	—

Radio-Frequency Power MOSFETs / 高周波パワー MOSFET

Part Number	Package	Applications	Absolute Maximum Ratings (Ta = 25°C)			Min	Po (W)		
			V _{DSS} (V)	P _D (W)	I _D (A)		Test Conditions		
							V _{DS} (V)	f (MHz)	P _i (W)
RFM08U9X	PW-X	UHF/VHF Professional radios	36	20	5	7.5	9.6	520	0.5
2SK3075	PW-X		30	20	5	7.5	9.6	520	0.5
2SK3074	PW-MINI		30	3	1	0.63	9.6	520	0.02
RFM12U7X	PW-X		20	20	4	11.5	7.2	520	1.0
RFM07U7X	PW-X		16	20	3	7.0	7.2	450 to 530	0.5
RFM06U3X *	PW-X		16	20	5	5.0	3.6	520	0.5
RFM01U7P	PW-MINI		20	3	1	1.0	7.2	520	0.1
2SK3476	PW-X		20	20	3	7.0	7.2	520	0.5
2SK3475	PW-MINI		20	3	1	0.63	7.2	520	0.02
RFM04U6P	PW-MINI	GMRS	16	7	2	3.5	6.0	470	0.2
2SK4037	PW-X		12	20	3	3.55	6.0	470	0.3
2SK2854	PW-MINI	UHF and VHF radio	10	0.5	0.5	0.2	6.0	849	0.02
2SK3079A	PW-X	FRS/GMRS	10	20	3	2.24	4.5	470	0.1
2SK3756	PW-MINI		7.5	3	1	1.26	4.5	470	0.1
2SK3078A	PW-MINI		10	3	0.5	0.63	4.5	470	0.1
2SK3078	PW-MINI		10	3	0.5	0.5	4.8	915	0.02
2SK3077	USQ	Driver	10	0.25	0.1	0.032	4.8	915	0.001
RFM03U3P	PW-MINI	GMRS	16	7	2.5	2.3	3.6	470	0.1
RFM00U7U	USQ	Driver	20	0.25	0.1	0.1	7.2	520	0.01

*: New product / 新製品

SEMICONDUCTOR GENERAL CATALOG

半導体製品総覧表

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